

RA6M3 Group R01DS0358EJ0120 Rev.1.20

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Leading performance 120-MHz Arm[®] Cortex[®]-M4 core, up to 2-MB code flash memory, 640-KB SRAM, Graphics LCD Controller, 2D Drawing Engine, Capacitive Touch Sensing Unit, Ethernet MAC Controller with IEEE 1588 PTP, USB 2.0 High-Speed, USB 2.0 Full-Speed, SDHI, Quad SPI, security and safety features, and advanced analog.

Features

■ Arm Cortex-M4 Core with Floating Point Unit (FPU)

- · Armv7E-M architecture with DSP instruction set
- Maximum operating frequency: 120 MHz
- Support for 4-GB address space
- On-chip debugging system: JTAG, SWD, and ETM
- Boundary scan and Arm Memory Protection Unit (Arm MPU)

■ Memory

- Up to 2-MB code flash memory (40 MHz zero wait states)
- 64-KB data flash memory (125,000 erase/write cycles)
- Up to 640-KB SRAM
- Flash Cache (FCACHE)
- Memory Protection Units (MPU)
- Memory Mirror Function (MMF)
- 128-bit unique ID

■ Connectivity

- Ethernet MAC Controller (ETHERC)
- Ethernet DMA Controller (EDMAC)
- Ethernet PTP Controller (EPTPC)
- USB 2.0 High-Speed (USBHS) module
- On-chip transceiver with voltage regulator
- Compliant with USB Battery Charging Specification 1.2
- USB 2.0 Full-Speed (USBFS) module
 - On-chip transceiver with voltage regulator
- Serial Communications Interface (SCI) with FIFO × 10
- Serial Peripheral Interface (SPI) × 2
- I²C bus interface (IIC) × 3
- Controller Area Network (CAN) × 2
- Serial Sound Interface Enhanced (SSIE) × 2
- SD/MMC Host Interface (SDHI) × 2
- Quad Serial Peripheral Interface (QSPI)
- IrDA interface
- Sampling Rate Converter (SRC)
- External address space
 - 8-bit or 16-bit bus space is selectable per area
 - SDRAM support

■ Analog

- 12-bit A/D Converter (ADC12) with 3 sample-and-hold circuits each × 2
- 12-bit D/A Converter (DAC12) × 2
- High-Speed Analog Comparator (ACMPHS) × 6
- Programmable Gain Amplifier (PGA) × 6
- Temperature Sensor (TSN)

■ Timers

- General PWM Timer 32-bit Enhanced High Resolution (GPT32EH) × 4
- General PWM Timer 32-bit Enhanced (GPT32E) × 4
- General PWM Timer 32-bit (GPT32) × 6
- Low Power Asynchronous General-Purpose Timer (AGT) × 2
- Watchdog Timer (WDT)

■ Safetv

- Error Correction Code (ECC) in SRAM
- · SRAM parity error check
- · Flash area protection
- ADC self-diagnosis function
- Clock Frequency Accuracy Measurement Circuit (CAC)
- Cyclic Redundancy Check (CRC) calculator
- Data Operation Circuit (DOC)
- Port Output Enable for GPT (POEG)
- Independent Watchdog Timer (IWDT)
- GPIO readback level detection
- · Register write protection
- Main oscillator stop detection
- Illegal memory access

■ System and Power Management

- Low power modes
- Realtime Clock (RTC) with calendar and VBATT support
- Event Link Controller (ELC)
- DMA Controller (DMAC) × 8
- Data Transfer Controller (DTC)
- Key Interrupt Function (KINT)
- · Power-on reset
- Low Voltage Detection (LVD) with voltage settings

■ Security and Encryption

- AES128/192/256
- 3DES/ARC4
- SHA1/SHA224/SHA256/MD5
- GHASH
- RSA/DSA/ECC
- True Random Number Generator (TRNG)

■ Human Machine Interface (HMI)

- Graphics LCD Controller (GLCDC)
- JPEG codec
- 2D Drawing Engine (DRW)
- Capacitive Touch Sensing Unit (CTSU)
- Parallel Data Capture Unit (PDC)

■ Multiple Clock Sources

- Main clock oscillator (MOSC) (8 to 24 MHz)
- Sub-clock oscillator (SOSC) (32.768 kHz)
- High-speed on-chip oscillator (HOCO) (16/18/20 MHz)
- Middle-speed on-chip oscillator (MOCO) (8 MHz)
- Low-speed on-chip oscillator (LOCO) (32.768 kHz)
- IWDT-dedicated on-chip oscillator (15 kHz)
- Clock trim function for HOCO/MOCO/LOCO
 Clock out support

■ General-Purpose I/O Ports

- Up to 133 input/output pins
 - Up to 9 CMOS input
 - Up to 124 CMOS input/output
 - Up to 21 input/output 5 V tolerant
 - Up to 18 high current (20 mA)

■ Operating Voltage

• VCC: 2.7 to 3.6 V

■ Operating Temperature and Packages

- $Ta = -40^{\circ}C \text{ to } +105^{\circ}C$
 - 176-pin BGA (13 mm × 13 mm, 0.8 mm pitch)
 - 176-pin LQFP (24 mm × 24 mm, 0.5 mm pitch)
 - 145-pin LGA (7 mm × 7 mm, 0.5 mm pitch) - 144-pin LQFP (20 mm × 20 mm, 0.5 mm pitch)
- 100-pin LQFP (14 mm × 14 mm, 0.5 mm pitch)

Overview

The MCU integrates multiple series of software- and pin-compatible Arm®-based 32-bit cores that share the same set of Renesas peripherals to facilitate design scalability and efficient platform-based product development.

The MCU in this series incorporates a high-performance Arm Cortex®-M4 core running up to 120 MHz, with the following features:

- Up to 2-MB code flash memory
- 640-KB SRAM
- Graphics LCD Controller (GLCDC)
- 2D Drawing Engine (DRW)
- Capacitive Touch Sensing Unit (CTSU)
- Ethernet MAC Controller (ETHERC) with IEEE 1588 PTP, USBFS, USBHS, SD/MMC Host Interface
- Quad Serial Peripheral Interface (QSPI)
- Security and safety features
- Analog peripherals.

1.1 Function Outline

Table 1.1 Arm core

Feature	Functional description
Arm Cortex-M4 core	Maximum operating frequency: up to 120 MHz Arm Cortex-M4 core: Revision: r0p1-01rel0 ARMv7E-M architecture profile Single precision floating-point unit compliant with the ANSI/IEEE Std 754-2008. Arm Memory Protection Unit (Arm MPU): ARMv7 Protected Memory System Architecture 8 protect regions. SysTick timer: Driven by SYSTICCLK (LOCO) or ICLK.

Table 1.2 Memory

Feature	Functional description
Code flash memory	Maximum 2-MB code flash memory. See section 55, Flash Memory in User's Manual.
Data flash memory	64-KB data flash memory. See section 55, Flash Memory in User's Manual.
Memory Mirror Function (MMF)	The Memory Mirror Function (MMF) can be configured to mirror the target application image load address in code flash memory to the application image link address in the 23-bit unused memory space (memory mirror space addresses). Your application code is developed and linked to run from this MMF destination address. The application code does not need to know the load location where it is stored in code flash memory. See section 5, Memory Mirror Function (MMF) in User's Manual.
Option-setting memory	The option-setting memory determines the state of the MCU after a reset. See section 7, Option-Setting Memory in User's Manual.
SRAM	On-chip high-speed SRAM with either parity-bit or Error Correction Code (ECC). The first 32 KB in SRAM0 provides error correction capability using ECC. Parity check is performed for other areas. See section 53, SRAM in User's Manual.
Standby SRAM	On-chip SRAM that can retain data in Deep Software Standby mode. See section 54, Standby SRAM in User's Manual.

Table 1.3 System (1 of 2)

Feature	Functional description
Operating modes	Two operating modes: - Single-chip mode - SCI or USB boot mode. See section 3, Operating Modes in User's Manual.
Resets	14 resets: RES pin reset Power-on reset Voltage monitor 0 reset Voltage monitor 1 reset Voltage monitor 2 reset Independent watchdog timer reset Watchdog timer reset Deep software standby reset SRAM parity error reset SRAM ECC error reset Bus master MPU error reset Bus slave MPU error reset Stack pointer error reset Software reset. See section 6, Resets in User's Manual.
Low Voltage Detection (LVD)	The Low Voltage Detection (LVD) function monitors the voltage level input to the VCC pin, and the detection level can be selected using a software program. See section 8, Low Voltage Detection (LVD) in User's Manual.
Clocks	Main clock oscillator (MOSC) Sub-clock oscillator (SOSC) High-speed on-chip oscillator (HOCO) Middle-speed on-chip oscillator (MOCO) Low-speed on-chip oscillator (LOCO) PLL frequency synthesizer IWDT-dedicated on-chip oscillator Clock out support. See section 9, Clock Generation Circuit in User's Manual.
Clock Frequency Accuracy Measurement Circuit (CAC)	The Clock Frequency Accuracy Measurement Circuit (CAC) counts pulses of the clock to be measured (measurement target clock) within the time generated by the clock to be used as a measurement reference (measurement reference clock), and determines the accuracy depending on whether the number of pulses is within the allowable range. When measurement is complete or the number of pulses within the time generated by the measurement reference clock is not within the allowable range, an interrupt request is generated. See section 10, Clock Frequency Accuracy Measurement Circuit (CAC) in User's Manual.
Interrupt Controller Unit (ICU)	The Interrupt Controller Unit (ICU) controls which event signals are linked to the NVIC/DTC module and DMAC module. The ICU also controls NMI interrupts. See section 14, Interrupt Controller Unit (ICU) in User's Manual.
Key Interrupt Function (KINT)	A key interrupt can be generated by setting the Key Return Mode Register (KRM) and inputting a rising or falling edge to the key interrupt input pins. See section 21, Key Interrupt Function (KINT) in User's Manual.
Low power modes	Power consumption can be reduced in multiple ways, such as by setting clock dividers, controlling EBCLK output, controlling SDCLK output, stopping modules, selecting power control mode in normal operation, and transitioning to low power modes. See section 11, Low Power Modes in User's Manual.
Battery backup function	A battery backup function is provided for partial powering by a battery. The battery-powered area includes the RTC, SOSC, backup memory, and switch between VCC and VBATT. See section 12, Battery Backup Function in User's Manual.
Register write protection	The register write protection function protects important registers from being overwritten because of software errors. See section 13, Register Write Protection in User's Manual.
Memory Protection Unit (MPU)	Four Memory Protection Units (MPUs) and a CPU stack pointer monitor function are provided for memory protection. See section 16, Memory Protection Unit (MPU) in User's Manual.

Table 1.3 System (2 of 2)

Feature	Functional description
Watchdog Timer (WDT)	The Watchdog Timer (WDT) is a 14-bit down-counter that can be used to reset the MCU when the counter underflows because the system has run out of control and is unable to refresh the WDT. In addition, a non-maskable interrupt or interrupt can be generated by an underflow. A refresh-permitted period can be set to refresh the counter and be used as the condition for detecting when the system runs out of control. See section 27, Watchdog Timer (WDT) in User's Manual.
Independent Watchdog Timer (IWDT)	The Independent Watchdog Timer (IWDT) consists of a 14-bit down-counter that must be serviced periodically to prevent counter underflow. It can be used to reset the MCU or to generate a non-maskable interrupt or interrupt for a timer underflow. Because the timer operates with an independent, dedicated clock source, it is particularly useful in returning the MCU to a known state as a fail safe mechanism when the system runs out of control. The IWDT can be triggered automatically on a reset, underflow, refresh error, or by a refresh of the count value in the registers. See section 28, Independent Watchdog Timer (IWDT) in User's Manual.

Table 1.4 Event link

Feature	Functional description
Event Link Controller (ELC)	The Event Link Controller (ELC) uses the interrupt requests generated by various peripheral modules as event signals to connect them to different modules, enabling direct interaction between the modules without CPU intervention. See section 19, Event Link Controller (ELC) in User's Manual.

Table 1.5 Direct memory access

Feature	Functional description
Data Transfer Controller (DTC)	A Data Transfer Controller (DTC) module is provided for transferring data when activated by an interrupt request. See section 18, Data Transfer Controller (DTC) in User's Manual.
DMA Controller (DMAC)	An 8-channel DMA Controller (DMAC) module is provided for transferring data without the CPU. When a DMA transfer request is generated, the DMAC transfers data stored at the transfer source address to the transfer destination address. See section 17, DMA Controller (DMAC) in User's Manual.

Table 1.6 External bus interface

Feature	Functional description
External buses	CS area (EXBIU): Connected to the external devices (external memory interface) SDRAM area (EXBIU): Connected to the SDRAM (external memory interface) QSPI area (EXBIUT2): Connected to the QSPI (external device interface).

Table 1.7 Timers (1 of 2)

Feature	Functional description
General PWM Timer (GPT)	The General PWM Timer (GPT) is a 32-bit timer with 14 channels. PWM waveforms can be generated by controlling the up-counter, down-counter, or the up- and down-counter. In addition, PWM waveforms can be generated for controlling brushless DC motors. The GPT can also be used as a general-purpose timer. See section 23, General PWM Timer (GPT) in User's Manual.
Port Output Enable for GPT (POEG)	Use the Port Output Enable for GPT (POEG) function to place the General PWM Timer (GPT) output pins in the output disable state. See section 22, Port Output Enable for GPT (POEG) in User's Manual.
Low Power Asynchronous General- Purpose Timer (AGT)	The Low Power Asynchronous General-Purpose Timer (AGT) is a 16-bit timer that can be used for pulse output, external pulse width or period measurement, and counting of external events. This 16-bit timer consists of a reload register and a down-counter. The reload register and the down-counter are allocated to the same address, and can be accessed with the AGT register. See section 25, Low Power Asynchronous General-Purpose Timer (AGT) in User's Manual.

Table 1.7 Timers (2 of 2)

Feature	Functional description
Realtime Clock (RTC)	The Realtime Clock (RTC) has two counting modes, calendar count mode and binary count mode, that are controlled by the register settings. For calendar count mode, the RTC has a 100-year calendar from 2000 to 2099 and automatically adjusts dates for leap years. For binary count mode, the RTC counts seconds and retains the information as a serial value. Binary count mode can be used for calendars other than the Gregorian (Western) calendar. See section 26, Realtime Clock (RTC) in User's Manual.

Table 1.8 Communication interfaces (1 of 2)

Feature	Functional description
Serial Communications Interface (SCI)	The Serial Communications Interface (SCI) is configurable to five asynchronous and synchronous serial interfaces: • Asynchronous interfaces (UART and Asynchronous Communications Interface Adapter (ACIA)) • 8-bit clock synchronous interface • Simple IIC (master-only) • Simple SPI • Smart card interface. The smart card interface complies with the ISO/IEC 7816-3 standard for electronic signals and transmission protocol. Each SCI has FIFO buffers to enable continuous and full-duplex communication, and the data transfer speed can be configured independently using an on-chip baud rate generator. See section 34, Serial Communications Interface (SCI) in User's Manual.
IrDA interface	The IrDA interface sends and receives IrDA data communication waveforms in cooperation with the SCI1 based on the IrDA (Infrared Data Association) standard 1.0. See section 35, IrDA Interface in User's Manual.
I ² C bus interface (IIC)	The 3-channel I ² C bus interface (IIC) conforms with and provides a subset of the NXP I ² C (Inter-Integrated Circuit) bus interface functions. See section 36, I ² C Bus Interface (IIC) in User's Manual.
Serial Peripheral Interface (SPI)	Two independent Serial Peripheral Interface (SPI) channels are capable of high-speed, full-duplex synchronous serial communications with multiple processors and peripheral devices. See section 38, Serial Peripheral Interface (SPI) in User's Manual.
Serial Sound Interface Enhanced (SSIE)	The Serial Sound Interface Enhanced (SSIE) peripheral provides functionality to interface with digital audio devices for transmitting I ² S 2ch, 4ch, 6ch, 8ch, WS Continue/Monaural/TDM audio data over a serial bus. The SSIE supports an audio clock frequency of up to 50 MHz, and can be operated as a slave or master receiver, transmitter, or transceiver to suit various applications. The SSIE includes 32-stage FIFO buffers in the receiver and transmitter, and supports interrupts and DMA-driven data reception and transmission. See section 41, Serial Sound Interface Enhanced (SSIE) in User's Manual.
Quad Serial Peripheral Interface (QSPI)	The Quad Serial Peripheral Interface (QSPI) is a memory controller for connecting a serial ROM (nonvolatile memory such as a serial flash memory, serial EEPROM, or serial FeRAM) that has an SPI-compatible interface. See section 39, Quad Serial Peripheral Interface (QSPI) in User's Manual.
Controller Area Network (CAN) module	The Controller Area Network (CAN) module provides functionality to receive and transmit data using a message-based protocol between multiple slaves and masters in electromagnetically-noisy applications. The CAN module complies with the ISO 11898-1 (CAN 2.0A/CAN 2.0B) standard and supports up to 32 mailboxes, which can be configured for transmission or reception in normal mailbox and FIFO modes. Both standard (11-bit) and extended (29-bit) messaging formats are supported. See section 37, Controller Area Network (CAN) Module in User's Manual.
USB 2.0 Full-Speed (USBFS) module	The USB 2.0 Full-Speed (USBFS) module can operate as a host controller or device controller. The module supports full-speed and low-speed (host controller only) transfer as defined in Universal Serial Bus Specification 2.0. The module has an internal USB transceiver and supports all of the transfer types defined in the Universal Serial Bus Specification 2.0. The USB has buffer memory for data transfer, providing a maximum of 10 pipes. Pipes 1 to 9 can be assigned any endpoint number based on the peripheral devices used for communication or based on your system. See section 32, USB 2.0 Full-Speed Module (USBFS) in User's Manual.

Table 1.8 Communication interfaces (2 of 2)

Feature	Functional description
USB 2.0 High-Speed (USBHS) module	The USB 2.0 High-Speed (USBHS) module can operate as a host controller or a device controller. As a host controller, the USBHS supports high-speed transfer, full-speed transfer, and low-speed transfer as defined in the Universal Serial Bus Specification 2.0. As a device controller, the USBHS supports high-speed transfer and full-speed transfer as defined in the Universal Serial Bus Specification 2.0. The USBHS has an internal USB transceiver and supports all of the transfer types defined in the Universal Serial Bus Specification 2.0. The USBHS has FIFO buffers for data transfer, providing a maximum of 10 pipes. Any endpoint number can be assigned to pipes 1 to 9, based on the peripheral devices or your system for communication. See section 33, USB 2.0 High-Speed Module (USBHS) in User's Manual.
Ethernet MAC with IEEE 1588 PTP (ETHERC)	One-channel Ethernet MAC Controller (ETHERC) compliant with the Ethernet/IEEE802.3 Media Access Control (MAC) layer protocol. An ETHERC channel provides one channel of the MAC layer interface, connecting the MCU to the physical layer LSI (PHY-LSI) that allows transmission and reception of frames compliant with the Ethernet and IEEE802.3 standards. The ETHERC is connected to the Ethernet DMA Controller (EDMAC) so data can be transferred without using the CPU. To handle timing and synchronization between devices, an on-chip Precision Time Protocol (PTP) module for the Ethernet PTP Controller (EPTPC) applies the PTP defined in the IEEE 1588-2008 version 2.0 standard. The EPTPC is composed of: Synchronization Frame Processing unit (SYNFP0) A Statistical Time Correction Algorithm unit (STCA). Use the EPTPC in combination with the on-chip Ethernet MAC Controller (ETHERC) and the DMA Controller for the PTP Ethernet Controller (PTPEDMAC). See section 29, Ethernet MAC Controller (ETHERC) in User's Manual.
SD/MMC Host Interface (SDHI)	The SDHI and MultiMediaCard (MMC) interface module provides the functionality required to connect a variety of external memory cards to the MCU. The SDHI supports both 1-bit and 4-bit buses for connecting memory cards that support SD, SDHC, and SDXC formats. When developing host devices that are compliant with the SD Specifications, you must comply with the SD Host/Ancillary Product License Agreement (SD HALA). The MMC interface supports 1-bit, 4-bit, and 8-bit MMC buses that provide eMMC 4.51 (JEDEC Standard JESD 84-B451) device access. This interface also provides backward compatibility and supports high-speed SDR transfer modes. See section 43, SD/MMC Host Interface (SDHI) in User's Manual.

Table 1.9 Analog

Feature	Functional description
12-bit A/D Converter (ADC12)	Two units of successive approximation 12-bit A/D Converter (ADC12) are provided. Analog input channels are selectable up to 13 in unit 0 and up to 11 in unit 1. Each 2 analog inputs of unit 0 and 1 are assigned to same port (AN005/AN105, AN006/AN106), up to 22 ports are available as analog input. The temperature sensor output and an internal reference voltage are selectable for conversion of each unit 0 and 1. The A/D conversion accuracy is selectable from 12-bit, 10-bit, and 8-bit conversion, making it possible to optimize the tradeoff between speed and resolution in generating a digital value. See section 47, 12-Bit A/D Converter (ADC12) in User's Manual.
12-bit D/A Converter (DAC12)	The 12-bit D/A Converter (DAC12) converts data and includes an output amplifier. See section 48, 12-Bit D/A Converter (DAC12) in User's Manual.
Temperature Sensor (TSN)	The on-chip Temperature Sensor (TSN) determines and monitors the die temperature for reliable operation of the device. The sensor outputs a voltage directly proportional to the die temperature, and the relationship between the die temperature and the output voltage is linear. The output voltage is provided to the ADC12 for conversion and can also be used by the end application. See section 49, Temperature Sensor (TSN) in User's Manual.
High-Speed Analog Comparator (ACMPHS)	The High-Speed Analog Comparator (ACMPHS) compares a test voltage with a reference voltage and provides a digital output based on the conversion result. Both the test and reference voltages can be provided to the comparator from internal sources such as the DAC12 output and internal reference voltage, and an external source with or without an internal PGA. Such flexibility is useful in applications that require go/no-go comparisons to be performed between analog signals without necessarily requiring A/D conversion. See section 50, High-Speed Analog Comparator (ACMPHS) in User's Manual.

Table 1.10 Human machine interfaces

Feature	Functional description
Capacitive Touch Sensing Unit (CTSU)	The Capacitive Touch Sensing Unit (CTSU) measures the electrostatic capacitance of the touch sensor. Changes in the electrostatic capacitance are determined by software, which enables the CTSU to detect whether a finger is in contact with the touch sensor. The electrode surface of the touch sensor is usually enclosed with an electrical insulator so that fingers do not come into direct contact with the electrodes. See section 51, Capacitive Touch Sensing Unit (CTSU) in User's Manual.

Table 1.11 Graphics

Feature	Functional description
Graphics LCD Controller (GLCDC)	 The Graphics LCD Controller (GLCDC) provides multiple functions and supports various data formats and panels. Key GLCDC features include: GPX bus master function for accessing graphics data Superimposition of three planes (single-color background plane, graphic 1-plane, and graphic 2-plane) Support for many types of 32-bit or 16-bit per pixel graphics data and 8-bit, 4-bit, or 1-bit LUT data format Digital interface signal output supporting a video image size of WVGA or greater. See section 58, Graphics LCD Controller (GLCDC) in User's Manual.
2D Drawing Engine (DRW)	The 2D Drawing Engine (DRW) provides flexible functions that can support almost any object geometry rather than being bound to only a few specific geometries such as lines, triangles, or circles. The edges of every object can be independently blurred or antialiased. Rasterization is executed at one pixel per clock on the bounding box of the object from left to right and top to bottom. The DRW can also raster from bottom to top to optimize the performance in certain cases. In addition, optimization methods are available to avoid rasterization of many empty pixels of the bounding box. The distances to the edges of the object are calculated by a set of edge equations for every pixel of the bounding box. These edge equations can be combined to describe the entire object. If a pixel is inside the object, it is selected for rendering. If it is outside, it is discarded. If it is on the edge, an alpha value can be chosen proportional to the distance of the pixel to the nearest edge for antialiasing. Every pixel that is selected for rendering can be textured. The resulting aRGB quadruple can be modified by a general raster operation approach independently for each of the four channels. The aRGB quadruples can then be blended with one of the multiple blend modes of the DRW. The DRW provides two inputs (texture read and framebuffer read), and one output (framebuffer write). The internal color format is always aRGB (8888). The color formats from the inputs are converted to the internal format on read and a conversion back is made on write. See section 56, 2D Drawing Engine (DRW) in User's Manual.
JPEG codec	The JPEG incorporates a JPEG codec that conforms to the JPEG baseline compression and decompression standard. This provides high-speed compression of image data and high-speed decoding of JPEG data. See section 57, JPEG Codec (JPEG) in User's Manual.
Parallel Data Capture (PDC) unit	One Parallel Data Capture (PDC) unit is provided for communicating with external I/O devices, including image sensors, and transferring parallel data, such as an image output from the external I/O device through the DTC or DMAC to the on-chip SRAM and external address spaces (the CS and SDRAM areas). See section 44, Parallel Data Capture Unit (PDC) in User's Manual.

Table 1.12 Data processing (1 of 2)

Feature	Functional description
Cyclic Redundancy Check (CRC) calculator	The Cyclic Redundancy Check (CRC) calculator generates CRC codes to detect errors in the data. The bit order of CRC calculation results can be switched for LSB-first or MSB-first communication. Additionally, various CRC-generating polynomials are available. The snoop function allows monitoring reads from and writes to specific addresses. This function is useful in applications that require CRC code to be generated automatically in certain events, such as monitoring writes to the serial transmit buffer and reads from the serial receive buffer. See section 40, Cyclic Redundancy Check (CRC) Calculator in User's Manual.

Table 1.12 Data processing (2 of 2)

Feature	Functional description
Data Operation Circuit (DOC)	The Data Operation Circuit (DOC) compares, adds, and subtracts 16-bit data. See section 52, Data Operation Circuit (DOC) in User's Manual.
Sampling Rate Converter (SRC)	The Sampling Rate Converter (SRC) converts the sampling rate of data produced by various audio decoders, such as the WMA, MP3, and AAC. Both 16-bit stereo and monaural data are supported. See section 42, Sampling Rate Converter (SRC) in User's Manual.

Table 1.13 Security

Feature	Functional description
Secure Crypto Engine 7 (SCE7)	Security algorithms: Symmetric algorithms: AES, 3DES, and ARC4 Asymmetric algorithms: RSA, DSA, and ECC. Other support features: TRNG (True Random Number Generator) Hash-value generation: SHA1, SHA224, SHA256, GHASH, and MD5 128-bit unique ID. See section 46, Secure Cryptographic Engine (SCE7) in User's Manual.

Table 1.14 I/O ports

Feature	Functional description	
I/O ports	 I/O ports for the 176-pin BGA, 176-pin LQFP - I/O pins: 124 - Input pins: 9 - Pull-up resistors: 125 - N-ch open-drain outputs: 124 - 5-V tolerance: 17 I/O ports for the 145-pin LGA, 144-pin LQFP - I/O pins: 101 - Input pins: 9 - Pull-up resistors: 102 - N-ch open-drain outputs: 101 - 5-V tolerance: 21 I/O ports for the 100-pin LQFP - I/O pins: 67 - Input pins: 9 - Pull-up resistors: 68 - N-ch open-drain outputs: 67 - 5-V tolerance: 14 	

1.2 Block Diagram

Figure 1.1 shows a block diagram of the MCU superset, some individual devices within the group have a subset of the features.

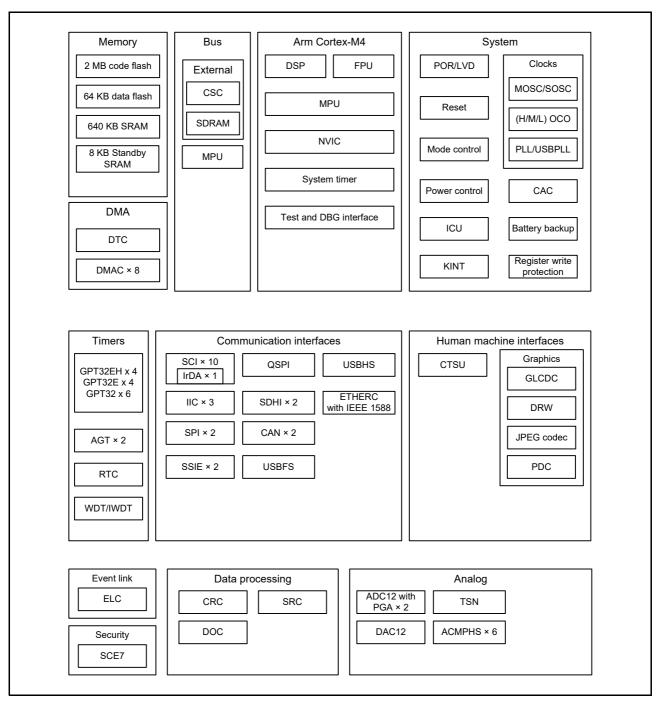


Figure 1.1 Block diagram

1.3 Part Numbering



Figure 1.2 Part numbering scheme

Table 1.15 Product list

Product part number	Package code	Code flash	Data flash	SRAM	Operating temperature
R7FA6M3AH2CBG	PLBG0176GE-A	2 MB	64 KB	640 KB	-40 to +85°C
R7FA6M3AH3CBG					-40 to +105°C
R7FA6M3AH3CFC	PLQP0176KB-A				-40 to +105°C
R7FA6M3AH2CLK	PTLG0145KA-A				-40 to +85°C
R7FA6M3AH3CLK					-40 to +105°C
R7FA6M3AH3CFB	PLQP0144KA-B				-40 to +105°C
R7FA6M3AH3CFP	PLQP0100KB-B				-40 to +105°C
R7FA6M3AF2CBG	PLBG0176GE-A	1 MB			-40 to +85°C
R7FA6M3AF3CBG					-40 to +105°C
R7FA6M3AF3CFC	PLQP0176KB-A				-40 to +105°C
R7FA6M3AF2CLK	PTLG0145KA-A				-40 to +85°C
R7FA6M3AF3CLK					-40 to +105°C
R7FA6M3AF3CFB	PLQP0144KA-B				-40 to +105°C
R7FA6M3AF3CFP	PLQP0100KB-B				-40 to +105°C

1.4 Function Comparison

Table 1.16 Functional comparison (1 of 2)

		Part numbers							
Function		R7FA6M3AH2CBG/ R7FA6M3AF2CBG/ R7FA6M3AH3CBG/ R7FA6M3AF3CBG	R7FA6M3AH3CFC/ R7FA6M3AF3CFC	R7FA6M3AH2CLK/ R7FA6M3AF2CLK/ R7FA6M3AH3CLK/ R7FA6M3AF3CLK	R7FA6M3AH3CFB/ R7FA6M3AF3CFB	R7FA6M3AH3CFP/ R7FA6M3AF3CFP			
Pin count		176	176	145	144	100			
Package		BGA	LQFP	LGA	LQFP	LQFP			
Code flash memory				2/1 MB					
Data flash memory				64 KB					
SRAM				640 KB					
o. u	Parity	608 KB							
	ECC								
Standby SRAM	200	32 KB 8 KB							
System	CPU clock			120 MHz					
System			512 B						
	Backup registers								
	ICU			Yes					
	KINT			8					
Event link	ELC			Yes					
DMA	DTC			Yes					
	DMAC			8		_			
BUS	External bus		16	bit bus		8-bit bus			
	SDRAM			Yes		No			
Timers	GPT32EH	4	4	4	4	4			
	GPT32E	4	4	4	4	4			
	GPT32	6	6	6	6	5			
	AGT	2	2	2	2	2			
	RTC	Yes							
	WDT/IWDT		Yes						
Communication	SCI	10							
	IIC	3 2							
	SPI		2						
	SSIE			2		1			
	QSPI			1		·			
	SDHI			2					
	CAN			2					
	USBFS		.,	Yes					
	USBHS		Yes	1	No				
	ETHERC			1		Unit0: 11			
Analog	ADC12	Un	Unit0: 13 Unit0: 13 Unit1: 11 Unit1: 9 Shared channel pin: 2*1 Shared channel pin: 2*1						
	3ch-S/H			Unit0: 1 (3ch) Unit1: 1 (3ch)					
	PGA			Unit0: 3 Unit1: 3					
	DAC12			2					
	ACMPHS			6					
	TSN			Yes		_			
нмі	CTSU		13		18	12			
Graphics	GLCDC			RGB888					
	DRW			Yes					
	JPEG			Yes					
	PDC			Yes					
Data processing	CRC			Yes					
	DOC			Yes					
	SRC			Yes					
	1	1							

Table 1.16 Functional comparison (2 of 2)

		Part numbers						
Function		R7FA6M3AH2CBG/ R7FA6M3AF2CBG/ R7FA6M3AH3CBG/ R7FA6M3AF3CBG	R7FA6M3AH3CFC/ R7FA6M3AF3CFC	R7FA6M3AH2CLK/ R7FA6M3AF2CLK/ R7FA6M3AH3CLK/ R7FA6M3AF3CLK	R7FA6M3AH3CFB/ R7FA6M3AF3CFB	R7FA6M3AH3CFP/ R7FA6M3AF3CFP		
I/O ports	I/O pins	124 9 125 124 17		101		67		
	Input pins			9		9		
	Pull-up resistors			102		68		
	N-ch open-drain outputs				101			
	5-V tolerance				21			

Note 1. Some input channels of the ADC units are sharing same port pin.

1.5 Pin Functions

Table 1.17 Pin functions (1 of 6)

Function	Signal	I/O	Description
Power supply	VCC	Input	Digital voltage supply pin. This is used as the digital power supply for the respective modules and internal voltage regulator, and used to monitor the voltage of the POR/LVD. Connect to the system power supply. Connect to VSS through a 0.1-µF smoothing capacitor close to each VCC pin.
	VCL0	-	Connect to VSS through a 0.1-µF smoothing capacitor close to each VCL
	VCL	-	pin. Stabilize the internal power supply.
	VSS	Input	Ground pin. Connect to the system power supply (0 V).
	VBATT	Input	Backup power pin
Clock	XTAL	Output	Pins for a crystal resonator. An external clock signal can be input through the
	EXTAL	Input	EXTAL pin.
	XCIN	Input	Input/output pins for the sub-clock oscillator. Connect a crystal resonator
	XCOUT	Output	between XCOUT and XCIN.
	EBCLK	Output	Outputs the external bus clock for external devices
	SDCLK	Output	Outputs the SDRAM-dedicated clock
	CLKOUT	Output	Clock output pin
Operating mode control	MD	Input	Pin for setting the operating mode. The signal level on this pin must not be changed during operation mode transition on release from the reset state.
System control	RES	Input	Reset signal input pin. The MCU enters the reset state when this signal goes low.
CAC	CACREF	Input	Measurement reference clock input pin
Interrupt	NMI	Input	Non-maskable interrupt request pin
	IRQ0 to IRQ15	Input	Maskable interrupt request pins
KINT	KR00 to KR07	Input	A key interrupt can be generated by inputting a falling edge to the key interrupt input pins
On-chip emulator	TMS	I/O	On-chip emulator or boundary scan pins
	TDI	Input	-
	TCK	Input	-
	TDO	Output	-
	TCLK	Output	This pin outputs the clock for synchronization with the trace data
	TDATA0 to TDATA3	Output	Trace data output
	SWDIO	I/O	Serial wire debug data input/output pin
	SWCLK	Input	Serial wire clock pin
	SWO	Output	Serial wire trace output pin

Table 1.17 Pin functions (2 of 6)

Function	Signal	I/O	Description
External bus interface	RD	Output	Strobe signal indicating that reading from the external bus interface space i in progress, active low
	WR	Output	Strobe signal indicating that writing to the external bus interface space is in progress, in 1-write strobe mode, active low
	WR0 to WR1	Output	Strobe signals indicating that either group of data bus pins (D07 to D00 or D15 to D08) is valid in writing to the external bus interface space, in byte strobe mode, active low
	BC0 to BC1	Output	Strobe signals indicating that either group of data bus pins (D07 to D00 or D15 to D08) is valid in access to the external bus interface space, in 1-write strobe mode, active low
	ALE	Output	Address latch signal when address/data multiplexed bus is selected
	WAIT	Input	Input pin for wait request signals in access to the external space, active lov
	CS0 to CS7	Output	Select signals for CS areas, active low
	A00 to A23	Output	Address bus
	D00 to D15	I/O	Data bus
	A00/D00 to A15/D15	I/O	Address/data multiplexed bus
SDRAM interface	CKE	Output	SDRAM clock enable signal
	SDCS	Output	SDRAM chip select signal, active low
	RAS	Output	SDRAM low address strobe signal, active low
	CAS	Output	SDRAM column address strobe signal, active low
	WE	Output	SDRAM write enable signal, active low
	DQM0	Output	SDRAM I/O data mask enable signal for DQ07 to DQ00
	DQM1	Output	SDRAM I/O data mask enable signal for DQ15 to DQ08
	A00 to A15	Output	Address bus
	DQ00 to DQ15	I/O	Data bus
GPT	GTETRGA, GTETRGB, GTETRGC, GTETRGD	Input	External trigger input pins
	GTIOC0A to GTIOC13A, GTIOC0B to GTIOC13B	I/O	Input capture, output compare, or PWM output pins
	GTIU	Input	Hall sensor input pin U
	GTIV	Input	Hall sensor input pin V
	GTIW	Input	Hall sensor input pin W
	GTOUUP	Output	3-phase PWM output for BLDC motor control (positive U phase)
	GTOULO	Output	3-phase PWM output for BLDC motor control (negative U phase)
	GTOVUP	Output	3-phase PWM output for BLDC motor control (positive V phase)
	GTOVLO	Output	3-phase PWM output for BLDC motor control (negative V phase)
	GTOWUP	Output	3-phase PWM output for BLDC motor control (positive W phase)
	GTOWLO	Output	3-phase PWM output for BLDC motor control (negative W phase)
AGT	AGTEE0, AGTEE1	Input	External event input enable signals
	AGTIO0, AGTIO1	I/O	External event input and pulse output pins
	AGTO0, AGTO1	Output	Pulse output pins
	AGTOA0, AGTOA1	Output	Output compare match A output pins
	AGTOB0, AGTOB1	Output	Output compare match B output pins
RTC	RTCOUT	Output	Output pin for 1-Hz or 64-Hz clock
	RTCIC0 to RTCIC2	Input	Time capture event input pins

Table 1.17 Pin functions (3 of 6)

Function	Signal	I/O	Description
SCI	SCK0 to SCK9	I/O	Input/output pins for the clock (clock synchronous mode)
	RXD0 to RXD9	Input	Input pins for received data (asynchronous mode/clock synchronous mode)
	TXD0 to TXD9	Output	Output pins for transmitted data (asynchronous mode/clock synchronous mode)
	CTS0_RTS0 to	I/O	Input/output pins for controlling the start of transmission and reception
	CTS9_RTS9		(asynchronous mode/clock synchronous mode), active low
	SCL0 to SCL9	I/O	Input/output pins for the I ² C clock (simple IIC mode)
	SDA0 to SDA9	I/O	Input/output pins for the I ² C data (simple IIC mode)
	SCK0 to SCK9	I/O	Input/output pins for the clock (simple SPI mode)
	MISO0 to MISO9	I/O	Input/output pins for slave transmission of data (simple SPI mode)
	MOSI0 to MOSI9	I/O	Input/output pins for master transmission of data (simple SPI mode)
	SS0 to SS9	Input	Chip-select input pins (simple SPI mode), active low
IIC	SCL0 to SCL2	I/O	Input/output pins for the clock
	SDA0 to SDA2	I/O	Input/output pins for data
SSIE	SSIBCK0	I/O	SSIE serial bit clock pins
	SSIBCK1	1	
	SSILRCK0/SSIFS0	I/O	LR clock/frame synchronization pins
	SSILRCK1/SSIFS1		
	SSITXD0	Output	Serial data output pins
	SSIRXD0	Input	Serial data input pins
	SSIDATA1	I/O	Serial data input/output pins
	AUDIO CLK	Input	External clock pin for audio (input oversampling clock)
SPI	RSPCKA, RSPCKB	I/O	Clock input/output pin
	MOSIA, MOSIB	I/O	Input or output pins for data output from the master
	MISOA, MISOB	I/O	Input or output pins for data output from the slave
	SSLA0, SSLB0	I/O	Input or output pin for slave selection
	SSLA1 to SSLA3, SSLB1 to SSLB3	Output	Output pins for slave selection
QSPI	QSPCLK	Output	QSPI clock output pin
	QSSL	Output	QSPI slave output pin
	QIO0 to QIO3	I/O	Data0 to Data3
CAN	CRX0, CRX1	Input	Receive data
	CTX0, CTX1	Output	Transmit data
USBFS	VCC USB	Input	Power supply pins
	VSS_USB	Input	Ground pins
	USB_DP	I/O	D+ I/O pin of the USB on-chip transceiver. Connect this pin to the D+ pin of the USB bus
	USB_DM	I/O	D- I/O pin of the USB on-chip transceiver. Connect this pin to the D- pin of the USB bus
	USB_VBUS	Input	USB cable connection monitor pin. Connect this pin to VBUS of the USB bus. The VBUS pin status (connected or disconnected) can be detected when the USB module is operating as a function controller.
	USB_EXICEN	Output	Low-power control signal for external power supply (OTG) chip
	USB_VBUSEN	Output	VBUS (5 V) supply enable signal for external power supply chip
	USB_OVRCURA, USB_OVRCURB	Input	Connect the external overcurrent detection signals to these pins. Connect the VBUS comparator signals to these pins when the OTG power supply
	_	Innut	chip is connected. Connect the MicroAB connector ID input signal to this pin during operation in
	USB_ID	Input	OTG mode

Table 1.17 Pin functions (4 of 6)

Function	Signal	I/O	Description
USBHS	VCC_USBHS	Input	Power supply pin
	VSS1_USBHS	Input	Ground pin
	VSS2_USBHS	Input	Ground pin
	AVCC_USBHS	Input	Analog power supply pin for the USBHS
	AVSS_USBHS	Input	Analog ground pin for the USBHS. Must be shorted to the PVSS_USBHS pin
	PVSS_USBHS	Input	PLL circuit ground pin for the USBHS. Must be shorted to the AVSS_USBHS pin
	USBHS_RREF	I/O	USBHS reference current source pin. Connect this pin to the AVSS_USBHS pin through a 2.2 -k Ω resistor ($\pm1\%$)
	USBHS_DP	I/O	USB bus D+ data pin
	USBHS_DM	I/O	USB bus D- data pin
	USBHS_EXICEN	Output	Connect this pin to the OTG power supply IC
	USBHS_ID	Input	Connect this pin to the OTG power supply IC
	USBHS_VBUSEN	Output	VBUS power enable signal for USB
	USBHS_OVRCURA, USBHS_OVRCURB	Input	Overcurrent pin for USB
	USBHS_VBUS	Input	USB cable connection monitor input pin
ETHERC	REF50CK0	Input	50-MHz reference clock. This pin inputs reference signal for transmission/reception timing in RMII mode.
	RMII0_CRS_DV	Input	Indicates carrier detection signals and valid receive data on RMII0_RXD1 and RMII0_RXD0 in RMII mode
	RMII0_TXD0, RMII0_TXD1	Output	2-bit transmit data in RMII mode
	RMII0_RXD0, RMII0_RXD1	Input	2-bit receive data in RMII mode
	RMII0_TXD_EN	Output	Output pin for data transmit enable signal in RMII mode
	RMII0_RX_ER	Input	Indicates an error occurred during reception of data in RMII mode
	ET0_CRS	Input	Carrier detection/data reception enable signal
	ET0_RX_DV	Input	Indicates valid receive data on ET0_ERXD3 to ET0_ERXD0
	ET0_EXOUT	Output	General-purpose external output pin
	ET0_LINKSTA	Input	Input link status from the PHY-LSI
	ET0_ETXD0 to ET0_ETXD3	Output	4 bits of MII transmit data
	ET0_ERXD0 to ET0_ERXD3	Input	4 bits of MII receive data
	ET0_TX_EN	Output	Transmit enable signal. Functions as signal indicating that transmit data is ready on ET0_ETXD3 to ET0_ETXD0
	ET0_TX_ER	Output	Transmit error pin. Functions as signal notifying the PHY_LSI of an error during transmission
	ET0_RX_ER	Input	Receive error pin. Functions as signal to recognize an error during reception
	ET0_TX_CLK	Input	Transmit clock pin. This pin inputs reference signal for output timing from ET0_TX_EN, ET0_ETXD3 to ET0_ETXD0, and ET0_TX_ER
	ET0_RX_CLK	Input	Receive clock pin. This pin inputs reference signal for input timing to ET0_RX_DV, ET0_ERXD3 to ET0_ERXD0, and ET0_RX_ER
	ET0_COL	Input	Input collision detection signal
	ET0_WOL	Output	Receive Magic packets
	ET0_MDC	Output	Output reference clock signal for information transfer through ET0_MDIO.
	ET0_MDIO	I/O	Input or output bidirectional signal for exchange of management data with PHY-LSI

Table 1.17 Pin functions (5 of 6)

Function	Signal	I/O	Description
SDHI	SD0CLK, SD1CLK	Output	SD clock output pins
	SD0CMD, SD1CMD	I/O	Command output pin and response input signal pins
	SD0DAT0 to SD0DAT7, SD1DAT0 to SD1DAT7	I/O	SD and MMC data bus pins
	SD0CD, SD1CD	Input	SD card detection pins
	SD0WP, SD1WP	Input	SD write-protect signals
Analog power supply	AVCC0	Input	Analog voltage supply pin. This is used as the analog power supply for the respective modules. Supply this pin with the same voltage as the VCC pin.
	AVSS0	Input	Analog ground pin. This is used as the analog ground for the respective modules. Supply this pin with the same voltage as the VSS pin.
	VREFH0	Input	Analog reference voltage supply pin for the ADC12 (unit 0). Connect this pin to VCC when not using the ADC12 (unit 0) and sample-and-hold circuit for AN000 to AN002.
	VREFL0	Input	Analog reference ground pin for the ADC12. Connect this pin to VSS when not using the ADC12 (unit 0) and sample-and-hold circuit for AN000 to AN002
	VREFH	Input	Analog reference voltage supply pin for the ADC12 (unit 1) and D/A Converter. Connect this pin to VCC when not using the ADC12 (unit 1), sample-and-hold circuit for AN100 to AN102, and D/A Converter.
	VREFL	Input	Analog reference ground pin for the ADC12 and D/A Converter. Connect this pin to VSS when not using the ADC12 (unit 1), sample-and-hold circuit for AN100 to AN102, and D/A Converter.
ADC12	AN000 to AN007, AN016 to AN020	Input	Input pins for the analog signals to be processed by the ADC12. AN005 & AN105 and AN006 & AN106 are assigned to same port pin
	AN100 to AN103, AN105 to AN107, AN116 to AN119	Input	
	ADTRG0	Input	Input pins for the external trigger signals that start the A/D conversion
	ADTRG1	Input	
	PGAVSS000/PGAVS S100	Input	Differential input pins
DAC12	DA0, DA1	Output	Output pins for the analog signals processed by the D/A converter
ACMPHS	VCOUT	Output	Comparator output pin
	IVREF0 to IVREF3	Input	Reference voltage input pins for comparator
	IVCMP0 to IVCMP2	Input	Analog voltage input pins for comparator
CTSU	TS00 to TS17	Input	Capacitive touch detection pins (touch pins)
	TSCAP	-	Secondary power supply pin for the touch driver
I/O ports	P000 to P007	Input	General-purpose input pins
	P008 to P010, P014, P015	I/O	General-purpose input/output pins
	P100 to P115	I/O	General-purpose input/output pins
	P200	Input	General-purpose input pin
	P201 to P214	I/O	General-purpose input/output pins
	P300 to P315	I/O	General-purpose input/output pins
	P400 to P415	I/O	General-purpose input/output pins
	P500 to P508, P511 to P513	I/O	General-purpose input/output pins
	P600 to P615	I/O	General-purpose input/output pins
	P700 to P713	I/O	General-purpose input/output pins
	P800 to P806	I/O	General-purpose input/output pins
	P900, P901, P905 to P908	I/O	General-purpose input/output pins
	PA00, PA01, PA08 to PA10	I/O	General-purpose input/output pins
	PB00, PB01	I/O	General-purpose input/output pins

Table 1.17 Pin functions (6 of 6)

Function	Signal	I/O	Description
GLCDC	LCD_DATA23 to LCD_DATA00	Output	Data output pins for panel
	LCD_TCON3 to LCD_TCON0	Output	Output pins for panel timing adjustment
	LCD_CLK	Output	Panel clock output pin
	LCD_EXTCLK	Input	Panel clock source input pin
PDC	PIXCLK	Input	Image transfer clock pin
	VSYNC	Input	Vertical synchronization signal pin
	HSYNC	Input	Horizontal synchronization signal pin
	PIXD0 to PIXD7	Input	8-bit image data pins
	PCKO	Output	Output pin for dot clock

1.6 Pin Assignments

Figure 1.3 to Figure 1.7 show the pin assignments.

	A	В	С	D	E	F	G	H	J	К	L	М	N	P	R	1
15	P407	P409	P411	P414	P708	USBHS_ DM	PVSS_ USBHS	P212 /EXTAL	XCIN	VCL0	P707	P703	P700	P405	P401	1
14	USB_DP	USB_DM	P410	P412	P415	USBHS_ DP	AVSS_ USBHS	P213 /XTAL	XCOUT	VBATT	P706	P701	P406	P402	P512	14
13	P204	VCC_ USB	VSS_ USB	P408	P413	VCC_ USBHS	USBHS_ RREF	AVCC_ USBHS	VSS	PB01	P704	P404	P400	P511	P805	1:
12	P313	P202	P207	P206	P205	VSS1_ USBHS	VSS2_ USBHS	vcc	PB00	P705	P702	P403	P513	P806	P000	1:
11	P900	P315	P314	P203								VCC	P001	P004	P002	1
10	P214	P211	P901	VSS								VSS	P006	P008	P005	11
9	P210	P209	RES	vcc								P009	AVSS0	VREFL0	VREFH0	g
8	P208	P201/MD	P200	P908								P010	AVCC0	VREFL	VREFH	a
7	P906	P905	P312	P907								VCC	VSS	P015	P014	7
6	P310	P309	P307	P311								P007	P507	P505	P508	6
5	P308	P305	VSS	vcc								P003	P503	P504	P506	5
4	P306	P304	P300/TCK /SWCLK	P111	VSS	P613	PA09	PA00	P607	VCC	VSS	VSS	VCC	P501	P502	4
3	P303	P302	P108/TMS SWDIO	P110/TDI	VCC	P610	VCC	VSS	P604	P603	P105	P102	P800	P804	P500	3
2	P301	P112	P114	P608	P611	P614	PA10	PA01	P605	P601	P107	P104	P101	P802	P803	2
1	P109/TDO	P113	P115	P609	P612	P615	PA08	VCL	P606	P602	P600	P106	P103	P100	P801	1

Figure 1.3 Pin assignment for 176-pin BGA (top view)

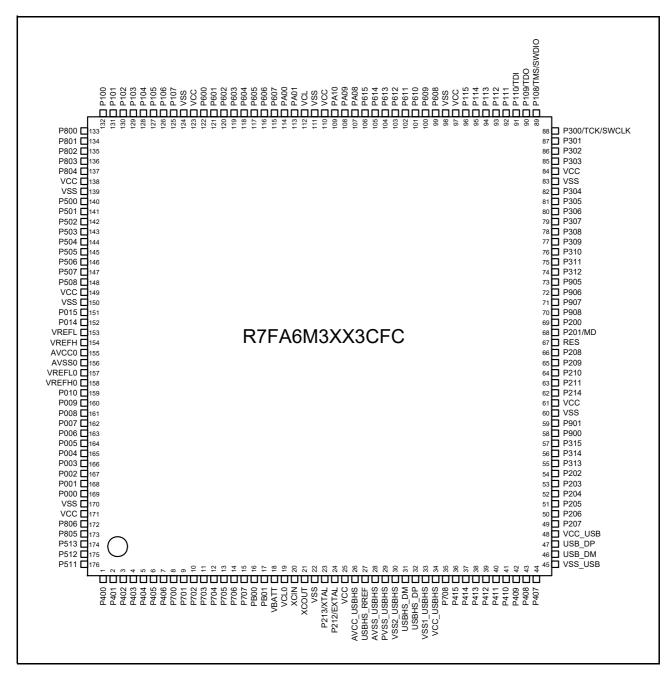


Figure 1.4 Pin assignment for 176-pin LQFP (top view)

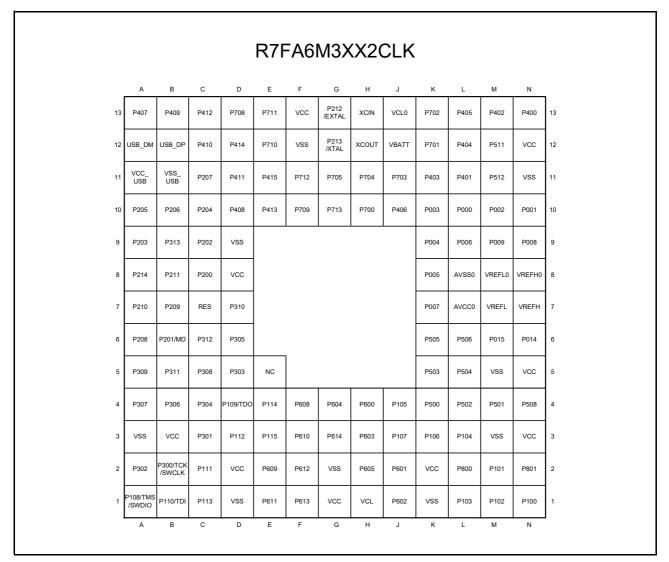


Figure 1.5 Pin assignment for 145-pin LGA (top view)

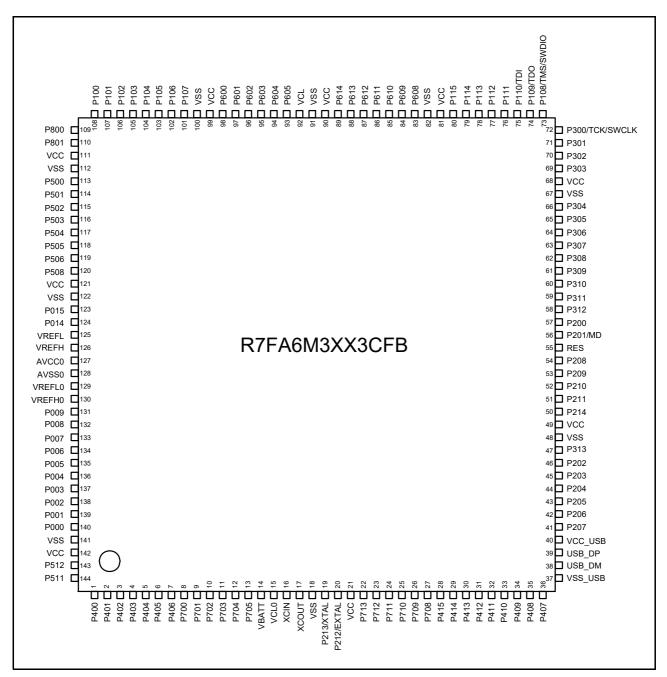


Figure 1.6 Pin assignment for 144-pin LQFP (top view)

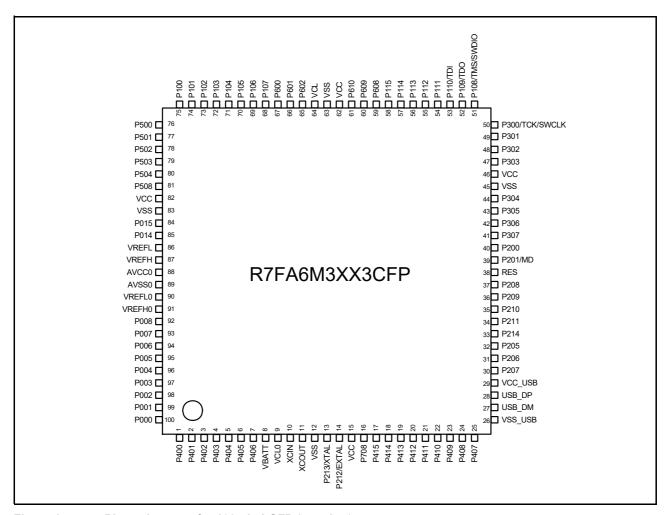


Figure 1.7 Pin assignment for 100-pin LQFP (top view)

1.7 Pin Lists

Pin	num	ber						Extb	us	Timers				Com	munica	ation i	nterfa	ces						Analog		НМІ	
BGA176	LQFP176	LGA145		LQFP100	Power, System, Clock, Debug, CAC	Interrupt	I/O port	External bus	SDRAM	AGT	GPT	GPT	RTC	USBFS, CAN	SCI0,2,4,6,8 (30 MHz)	SCI1,3,5,7,9 (30 MHz)	21	SPI, QSPI	SSIE	ETHERC (MII) (25 MHz)	ETHERC (RMII) (50 MHz)	USBHS	SDHI	ADC12	DAC12, ACMPHS	crsu	вссрс, Ррс
N13	1	N13	1	1		IRQU	P400		-	AGTIO1	-	GTIOC 6A	-	- CTVO	SCK4	SCK7	SCL0 _A		AUDIO _CLK	OL OL	WOL	_	_	ADTRG 1		-	
R15	2	L11	2	2		IRQ5- DS	P401	-	-	-	GTETRGA	6B	-	CIXU	CTS4_ RTS4/ SS4	TXD7/ MOSI7 /SDA7	SDA0 _A	-	-	DC DC	DC DC	-	-	-	-	-	
P14	3	M13	3	3	CACREF	IRQ4- DS	P402	-	-	AGTIO0/ AGTIO1	-	-	RTC IC0	CRX0	-	RXD7/ MISO7 /SCL7	-	-	AUDIO _CLK	ET0_M DIO	ET0_M DIO	-	-	-	-	-	VSYNC
M12	4	K11	4	4	-	-	P403	-	-	AGTIO0/ AGTIO1	-	GTIOC 3A	RTC IC1	-	-	CTS7_ RTS7/ SS7	-	-	SSIBC K0_A	ET0_LI NKSTA	ET0_LI NKST A	-	SD1 DAT7 B	-	-	-	PIXD7
M13	5	L12	5	5	-	-	P404	-	-	-	-	GTIOC 3B	RTC IC2	-	-	-	-	-	SSILR CK0/S SIFS0_ A	ET0_EX OUT	ET0_E XOUT	-	SD1 DAT6 _B	-	-	-	PIXD6
P15	6	L13	6	6	-	-	P405	-	-	-	-	GTIOC 1A	-	-	-	-	-	-	SSITX D0_A	ET0_TX _EN	RMII0_ TXD_E N B	-	SD1 DAT5 B	-	-	-	PIXD5
N14	7	J10	7	7	-	-	P406	-	-	-	-	GTIOC 1B	-	-	-	-	-	SSLB3 _C	SSIRX D0_A	ET0_RX _ER	RMII0_ TXD1_ B	-	SD1 DAT4 B	-	-	-	PIXD4
N15	8	H10	8	-	-	-	P700	-	-	-	-	GTIOC 5A	-	-	-	-	-	MISOB _C	-	ET0_ET XD1	RMII0_ TXD0_ B	-	SD1 DAT3 B	-	-	-	PIXD3
M14	9	K12	9	-	-	-	P701	-	-	-	-	GTIOC 5B	-	-	-	-	-	MOSIB _C	-	ET0_ET XD0	REF50 CK0_B	-	SD1 DAT2 B	-	-	-	PIXD2
L12	10	K13	10	-	-	-	P702	-	-	-	-	GTIOC 6A	-	-	-	-	-	RSPC KB_C	-	ET0_ER XD1	RMII0_ RXD0_ B	-	SD1 DAT1 B	-	ı	-	PIXD1
M15	11	J11	11	-	-	-	P703	-	-	-	-	GTIOC 6B	-	-	-	-	-	SSLB0 _C	-	ET0_ER XD0	RMII0_ RXD1_ B	-	SD1 DAT0 B	-	VCOUT	-	PIXD0
L13	12	H11	12	-	-	-	P704	-	-	AGTO0	-	-	-	CTX0	-	-	-	SSLB1 _C	-	ET0_RX _CLK		-	SD1 CLK_ B	-	-	-	HSYNC
K12	13	G11	13	-	-	-	P705	-	-	AGTIO0	-	-	-	CRX0	-	-	-	SSLB2 _C	-	ET0_C RS	RMII0_ CRS_ DV_B	-	SD1 CMD B	-	-	-	PIXCLK
L14	14		-	-	-	IRQ7	P706	-	-	-	-	-	-	-	-	RXD3/ MISO3 /SCL3	-	-	-	-	-	USB HS_ OVR CUR	SD1 CD_ B	-	-	-	-
L15	15	-	-	-	-	IRQ8	P707	-	-	-	-	-	-	-	-	TXD3/ MOSI3 /SDA3	-	-	-	-	-	USB HS_ OVR CUR	SD1 WP_ B	-	-	-	-
J12	16	-	-	-	-	-	PB00	-	-	-	-	-	-	-	-	SCK3	-	-	-	-	-	A USB HS_	-	-	-	-	-
K13	17	-	-	-	-	-	PB01	-	_	-	-	-	-	-	-	CTS3_ RTS3/	-	-	-	-	-	VBŪ SEN USB HS	-	-	-	-	-
V14	10	112	14	0	VBATT											SS3						VВŪ S					
K14 K15					VCL0	-	-	-	_	-	-	-	-	-	-	-	-	-	-	<u>-</u>	-	-	-	-	_	-	-
J15		H13			XCIN	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
J14 J13		H12 F12			XCOUT	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
H14		G12			VSS XTAL	IRQ2	- P213	-	-	-	GTETRGC	GTIOC 0A	-	-	-	TXD1/ MOSI1 /SDA1	-	-	-	-	-	-	-	ADTRG 1	-	-	-
H15	24	G13	20	14	EXTAL	IRQ3	P212	-	-	AGTEE1	GTETRGD	GTIOC 0B	-	-	-	RXD1/ MISO1 /SCL1	-	-	-	-	-	-	-	-		_	-
H12		F13 -	21	15 -	VCC AVCC_U SBHS	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
G13		-	-	-	USBHS_ RREF	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
G14			<u> </u>	-	AVSS_U SBHS PVSS_U		- -	-	-	- -		-	-	-	-	-	-	-	-	- -	-	 -	-	- -	-	-	-
G12	30	-	-	-	SBHS VSS2_U SBHS	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
F15		-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	USB HS_ DM	-	-	-	-	-
F14				-	-	-	-	-		-	-	-	-	-	-	-	-	-	-		-	USB HS_ DP	-	-	-	-	-
F12		-	-	_	VSS1_U SBHS VCC_US	-	- -	-	-	-	- -	-	-	-	-	-	- -	-	-	-	-	- -	-	- -	-		-
-		G10	22	-	BHS	-	P713	-	-	AGTOA0	-	GTIOC	-	-	-	-	-	-	-	-	-	 -	-	-	-	TS17	-
			<u> </u>			<u> </u>	<u> </u>			<u> </u>	<u> </u>	2A		<u> </u>]	<u> </u>			<u> </u>]	<u> </u>		<u> </u>			<u> </u>

Pin ı	num	ber	,					Extb	us	Timers				Com	munica	ation i	nterfa	ces						Analog	l	НМІ	
BGA176	LQFP176	LGA145	LQFP144	LQFP100	Power, System, Clock, Debug, CAC	Interrupt	I/O port	External bus	SDRAM	AGT	GPT	GPT	RTC	USBFS, CAN	SCI0,2,4,6,8 (30 MHz)	SCI1,3,5,7,9 (30 MHz)	21	SPI, QSPI	SSIE	ETHERC (MII) (25 MHz)	ETHERC (RMII) (50 MHz)	USBHS	SDHI	ADC12	DAC12, ACMPHS	CTSU	GLCDC, PDC
-	-			-	-	-	P712	-	-	AGTOB0	-	GTIOC 2B	-	-	-	-	-	-	-	-	-	-	-	-	-	TS16	-
-	-	E13	24	-		-	P711	-	-	AGTEE0		-	-		-	CTS1_ RTS1/ SS1	-	-	-	ET0_TX _CLK	-	-	-			TS15	-
-		E12		-	-	-	P710	-	-	-	-	-	-	-	-	SCK1	-	-	-	ET0_TX _ER		-	-	-	-	TS14	-
-	-	F10	26	-	-	IRQ10	P709	-	-	-	-	-	-	-	-	TXD1/ MOSI1 /SDA1	-	-	-	ET0_ET XD2	-	-	-	-	-	TS13	-
E15	35	D13	27	16	CACREF	IRQ11	P708	-	-	-	-	-	-	-	-	RXD1/ MISO1	-	SSLA3 _B	AUDIO _CLK	ET0_ET XD3	-	-	-	-	-	TS12	РСКО
E14	36	E11	28	17	-	IRQ8	P415	-	-	-	-	GTIOC 0A	-	USB_ VBUS	-	/SCL1	-	SSLA2 B	-	ET0_TX EN	RMII0_ TXD_E	-	SD0 CD	-	-	TS11	PIXD5
D15	37	D12	29	18	-	IRQ9	P414	-	-	-	-	GTIOC	-	EN -	 -	-	-	_B SSLA1	-	ET0_RX	N_A RMII0_	-	A SD0	-	-	TS10	PIXD4
= 10		=										0B						_B		_ER	TXD1_ A		WP_ A				
E13	38	E10	30	19	-	-	P413	-	-	-	GTOUUP	_	-	-	CTS0_ RTS0/ SS0	-	-	SSLA0 _B	-	ET0_ET XD1	RMII0_ TXD0_ A	-	SD0 CLK_ A	-	-	TS09	PIXD3
D14	39	C13	31	20	-	-	P412	-	-	AGTEE1	GTOULO	-	-	-	SCK0	-	-	RSPC KA_B	-	ET0_ET XD0	REF50 CK0_A	-	SD0 CMD	-	-	TS08	PIX02
C15	40	D11	32	21	-	IRQ4	P411	-	-	AGTOA1	GTOVUP	GTIOC 9A	-	-	TXD0/ MOSI0	CTS3_ RTS3/	-	MOSIA B	-	ET0_ER XD1	RMII0_ RXD0	-	_A SD0 DAT0	-	-	TS07	PIX01
C14	41	C12	33	22	-	IRQ5	P410	-	-	AGTOB1	GTOVLO	GTIOC	-	-	/SDA0 RXD0/	SS3 SCK3	-	- MISOA	-	ET0_ER	A RMII0_	-	_A SD0	-	-	TS06	PIXD0
DAE	10	D42	24	22		IDOS	D400				CTOWILD	9B		LICE	MISO0 /SCL0			_B		XD0	RXD1_ A	LICD	DAT1 _A			TS05	LICYNIC
B15	42	B13	34	23	-	IRQ6	P409	-		-	GTOWUP	GTIOC 10A		USB_ EXIC EN		TXD3/ MOSI3 /SDA3	-	-	-	ET0_RX _CLK	RMII0_ RX_E R_A	USB HS_ EXIC	-	-		1505	HSYNC
D13	43	D10	35	24	-	IRQ7	P408	-	-	-	GTOWLO	GTIOC 10B	-	USB_ ID	-	RXD3/ MISO3		-	-	ET0_C RS	RMII0_ CRS_	EN USB HS_I	-	-	-	TS04	PIXCLK
A15	44	A13	36	25	-	-	P407	-	-	AGTIO0	-	-	RTC	USB	CTS4	/SCL3		SSLB3	-	ET0_EX	DV_A ET0_E	D -	-	ADTRG	-	TS03	-
													OUT	VBUS	RTS4/ SS4		_B	_A		OUT	XOŪT			0			
C13 B14		B11 A12			VSS_US B	-		_		-	-		-	- USB_	-	-	-	-	-	-		_	- -	-		-	-
A14		B12			-	-	_	_	-	-	-	-	_	DM USB_	-	-	-	-	-	-	-	_	-	-	-	_	-
B13	48	A11	40	29	VCC_US	-	-	-	-	-	-	-	-	DP -	-	-	-	-	-	-	-	-	-	-	-	-	-
C12	49	C11	41	30	- -	-	P207	A17	-	-	-	-	-	-	-	-	-	SSLB2 A/QS	-	-	-	-	-	-	-	TS02	LCD_DATA 23_B
D12	50	B10	42	31	-	IRQ0-	P206	WAIT	-	-	GTIU	-	-	USB_	RXD4/	-	SDA1	SL		ET0_LI	ET0_LI	-	SD0	-	-	TS01	
E40	F4	110	42	20	CLIVOLIT	DS	DOOF	A4C		ACTO4	CTIV	CTIOC		EN	MISO4 /SCL4 TXD4/	CTCO	_A	_A	_	NKSTA	NKST A		DAT2 _A	!		TCCA	
E12	51	A10	43	32	CLKOUT	DS	P205	A16	-	AGTO1	GTIV	GTIOC 4A	-		MOSI4 /SDA4	RTS9/	SCL1 _A	SSLB0 _A	CK1/S SIFS1_	OL OL	WOL	-	SD0 DAT3 _A	-	-	TSCA P	-
A13	52	C10	44	-	CACREF	-	P204	A18	-	AGTIO1	GTIW	GTIOC 4B	-	A-DS USB_ OVR	SCK4	SCK9	SCL0 B			ET0_RX	-	-	SD0 DAT4	-	-	TS00	-
												46		CUR B-DS			_B	KB_A	K1_A	_50			_A				
D11	53	A9	45	-	-	IRQ2- DS	P203	A19	-	-	-	GTIOC 5A	-	CTX0	CTS2_ RTS2/ SS2	TXD9/ MOSI9 /SDA9	-	MOSIB _A	-	ET0_C OL	-	-	SD0 DAT5 A	-	-	TSCA P	-
B12	54	C9	46	-	-	IRQ3- DS	P202	WR1/ BC1	-	-	-	GTIOC 5B	-	CRX0		RXD9/ MISO9	-	MISOB _A		ET0_ER XD2	-	-	SD0 DAT6	-	-	-	LCD_TCO N3_B
A12	55	В9	47	-	-	-	P313	A20	-	-	-	-	-	-	-	/SCL9	-	-	-	ET0_ER		-	_A SD0		-	-	LCD_TCO
C11	56	_	_	_	_	-	P314	A21	_	-	_	_	_	-	 -	-	-	-	-	XD3	_	_	DAT7 _A	ADTRG	-	-	N2_B LCD_TCO
B11		-	-	-	-	-	P315		-	-	-	-	-	-	RXD4	-	-	-	-	-	-	-	-	0	-	-	N1_B LCD_TCO
A11	58	-	<u> </u>	<u> </u> -	-	 -	P900	A23	-	-	-	-	-	-	TXD4	-	-	-	-	 -	-	-	 -	-	-	-	N0_B LCD_CLK_
C10	59	-	-	-	-	-	P901	-	-	AGTIO1	-	-	-	-	SCK4	-	-	-	-	-	-	-	-	-	-	-	B LCD_DATA 15_B
D10 D9				<u>-</u>	VSS VCC	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	- -	-	-	-	
A10			50	33	TCLK	-	P214	-	-	-	GTIU	-	-	-	-	-	-	QSPC LK	-	ET0_M DC	ET0_M DC	-	SD0 CLK_	-	-	-	LCD_DATA 22_B
B10	63	B8	51	34	TDATA0	-	P211	-	-	-	GTIV	-	-	-	-	-	-	QIO0	-	ET0_M DIO	ET0_M DIO	-	B SD0 CMD	-	-	-	LCD_DATA 21_B
A9	64	A7	52	35	TDATA1	 -	P210	-	_	-	GTIW	-	_	_	 -	-	_	QIO1	-	ET0_W		_	_B SD0	-	-	-	LCD_DATA
																				OL	WOL		CD_ B				20_B
B9	65	в/	53	36	TDATA2	-	P209	-	-	-	GTOVUP	-	-	-	-	-	-	QIO2	-	ET0_EX OUT	XOUT	-	SD0 WP_ B		-	-	LCD_DATA 19_B

Pin	nun	nber			İ			Extb	us	Timers				Com	munica	ation in	nterfa	ces						Analog		НМІ	
BGA176	[®] LQFP176	⁹ LGA145	P LQFP144	37 TOFP100	EVACTI Power, System, Clock, Debug, CAC	Interrupt	1/O bort	External bus	SDRAM	AGT	GTOVLO	GPT	RTC	· USBFS, CAN	SCI0,2,4,6,8 (30 MHz)	SCI1,3,5,7,9 (30 MHz)	<u></u>	SPI, QSPI	SSIE	ETHERC (MII)	⊟ ETHERC (RMII) □ (50 MHz)	USBHS	SDO	ADC12	DAC12, ACMPHS	CTSU	GLCDC, PDC
																				NKSTA	NKST A		DAT0 _B				18_B
C9 B8		C7 B6			RES MD	-	- P201	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
C8 D8	69 70	C8	57	40	-	NMI	P200	-	-	-	-	- GTIOC	-	-	-	-	-	-	-	-	-	-	-	-	-	-	- LCD DATA
				-	-		P908				-	2A	_					-	_	-		_			-		14_B
D7	71	-	-	-	-	-	P907	CS6	-	-	-	GTIOC 2B	-	-	_	_	_	-	_	-	-	-	-	-	-		LCD_DATA 13_B
A7	72	•	-	-	-	-	P906		-	-	-	GTIOC 3A	-	-	-	-	-	-	-	-	-	-	-	-	-		LCD_DATA 12_B
В7	73	•	-	-	-	-	P905	CS4	-	-	-	GTIOC 3B	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_DATA 11_B
C7	74	C6	58	-	-	-	P312	CS3	CAS	AGTOA1	-	-	-	-	-	CTS3_ RTS3/	-	-	-	-	-	-	-	-	-	,	
D6	75	B5	59	-	-	-	P311	CS2	RAS	AGTOB1	-	-	-	-	-	SS3 SCK3	_	-	-	-	-	-	-	-	-	-	LCD_DATA
A6	76	D7	60	-	-	-	P310	A15	A15	AGTEE1	-	-	-	-	-	TXD3	-	QIO3	-	-	-	-	-	-	-	-	23_A LCD_DATA
В6	77	A5	61	_	-	-	P309	A14	A14	-	-	-	-	-	-	RXD3	-	QIO2	-	-	-	_	-	-	-	-	22_A LCD_DATA
A5	78	C5	62	-	-	-	P308	A13	A13	-	-	-	_	-	-	-	-	QIO1	_	-	-	_	-	-	_	-	21_A LCD_DATA
C6	79	A4	63	41	-	-	P307		A12	-	GTOUUP	_	_	-	CTS6	_	_	QIO0	-	-	-	_	_	_	-	_	20_A LCD_DATA
	80		64				P306		A11		GTOULO				SCK6	_		QSSL								_	19_A LCD_DATA
B5			65			IRQ8	P305		A10		GTOWUP				TXD6/			QSPC									18_A LCD_DATA
Бо	01	Do	00	40		ii (QO	000	7410	7.10		0101101				MOSI6 /SDA6			LK									17_A
B4	82	C4	66	44	-	IRQ9	P304	A09	A09	-	GTOWLO	GTIOC 7A	-	-	RXD6/ MISO6	-	-	-	-	-	-	-	-	-	-	-	LCD_DATA 16_A
C5	83	A3	67	45	VSS							,,,			/SCL6												10_7(
D5	84	ВЗ	68	46	VCC	-	-	-		-	-	-	-	-	-	-	-	E	E	-	-	-	-	-	-		-
A3	85	D5	69	47	-	-	P303	A08	A08	-	-	GTIOC 7B	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_DATA 15_A
ВЗ	86	A2	70	48	-	IRQ5	P302	A07	A07	-	GTOUUP	GTIOC 4A	-	-	TXD2/ MOSI2 /SDA2	-	-	SSLB3 _B	-	-	-	-	-	-	-	-	LCD_DATA 14_A
A2	87	СЗ	71	49	-	IRQ6	P301	A06	A06	AGTIO0	GTOULO	GTIOC 4B	-	-	RXD2/ MISO2	CTS9_	-	SSLB2 B	-	-	-	-	-	-	-	-	LCD_DATA 13_A
C4	00	DO.	70	50	TOKIOW		D200				CTOUUD				/SCL2												13_1
		B2	72		TCK/SW CLK		P300				GTOUUP	GTIOC 0A_A				0.700		SSLB1 _B							-		
C3	89	A1	73	51	TMS/SW DIO	-	P108	Ī	-	-	GTOULO	GTIOC 0B_A	-	-	-	CTS9_ RTS9/ SS9	-	SSLB0 _B	-	-	-	-	-	-	-		-
A1	90	D4	74	52	CLKOUT /TDO/S	-	P109	-	-	-	GTOVUP	GTIOC 1A_A	-	CTX1	-	TXD9/ MOSI9	-	MOSIB B	-	-	-	-	-	-	-	-	-
D3	91	D1	75	E2	WO TDI	IRQ3	P110				GTOVLO	GTIOC		CRX1	CTS2_	/SDA9 RXD9/									VCOUT		
D3	91	ы	73	55	IDI	ings	FIIU	-	_	-	GIOVLO	1B_A	-	CRXI		MISO9 /SCL9	-	MISOB _B	Ī			-		-	VC001	-	-
D4	92	C2	76	54	-	IRQ4	P111	A05	A05	-	-	GTIOC 3A A	-	-	SCK2	CCIVO	-	RSPC KB B	-	-	-	-	-	-	-	-	LCD_DATA 12_A
B2	93	D3	77	55	-	-	P112	A04	A04	-	-	GTIOC 3B_A	-	-	TXD2/ MOSI2	SCK1		SSLB0	SSIBC K0_B	-	-	-	-	-	-	-	LCD_DATA 11_A
B1	QΛ	C1	7Ω	56			D113	A03	VU3			GTIOC			/SDA2 RXD2/												LCD_DATA
ы	34	Ci	70	50			1113	A03	A03			2A			MISO2 /SCL2				SSILR CK0/S SIFS0								10_A
C2	95	F4	79	57	_	_	P114	A02	A02	_	_	GTIOC	_			_	_		B SSIRX	_	_			_	_		LCD_DATA
C1								A01				2B GTIOC			_	_		_	D0_B SSITX							_	09_A LCD_DATA
					VCC		1 110	7.01	7.01			4A							D0_B								08_A
E4	98	D1	82	-	VSS	-	-	-		-	-	-	-	-	-	-	-	-	E	-	-	-	-	-	-		-
D2					-	-		BC0		-	-	GTIOC 4B		-	-	-	-	-	-	-	-	-	-	-	-		LCD_DATA 07_A
D1					-	-		CS1		-	-	GTIOC 5A		CTX1	-	-	-	-	-	-	-	-	-	-	-		LCD_DATA 06_A
	101				-	-		CS0		-	-	GTIOC 5B	-	CRX1	-	-	-	-	-	-	-	-	-	-	-		LCD_DATA 05_A
E2	102	E1	86		CLKOUT /CACRE	-	P611	-	SDCS	-	-	-	-	-	-	CTS7_ RTS7/	-	-	-	-	-	-	-	-	-		-
E1	103	F2	87	-	F -	 -	P612	D08[DQ08	-	-	-	-	-	-	SS7 SCK7	-	-	-	-	-	-	 -	-	-	-	-
								A08/ D08]																			
F4	104	F1	88	-	-	-		A09/	DQ09	-	-	-	-	l	-	TXD7	-		-	-	-		-	-	-		-
F2	105	G3	89	-	 -	-	P614		DQ10	-	-	-	-	-	-	RXD7	-	-	-	-	-	-	-	-	-	-	-
								A10/ D10]																			
F1			-	-	-	-	P615		_	-	-	-			-					-	-	-		-	-		LCD_DATA 10_B
G1	107		-	-	-	-	PA08	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	- 	-		-	LCD_DATA 09_B

in n	um	ber						Extb	us	Timers				Com	munica	ation ii	nterfa	ices						Analog	<u> </u>	НМІ	
4 BGA176	LQFP176	LGA145	LQFP144	LQFP100	Power, System, Clock, Debug, CAC	Interrupt	I/O port	External bus	SDRAM	AGT	GPT	GPT	RTC	USBFS, CAN	SCI0,2,4,6,8 (30 MHz)	SCI1,3,5,7,9 (30 MHz)	2	SPI, QSPI	SSIE	ETHERC (MII) (25 MHz)	ETHERC (RMII) (50 MHz)	USBHS	SDHI	ADC12	DAC12, ACMPHS	CTSU	
	108	-	-	_	-	-	PA09 PA10		-	-	-	-		-	-	-		-	-	-	-	-	-	-		-	LCD_DA 08_B LCD_DA
	110	- G1	90	62	VCC		- A 10		_	-	-	-	_	-	-	-		-	-	-	-		-	-			07_B
3 1	111		91	63 64	VSS VCL	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-		-	-
	113	-	-	-	-	-	PA01	-	-	-	-	-	-	-	SCK8	-	-	-	-	-	-	-	-	-	-	-	LCD_D. 06_B
	114		-	-	-	-	PA00	_	-	-	-	-	-	-	TXD8	-	-	-	-	-	-			-	-	-	LCD_D 05_B
	115	-	-	_	-	-	P607	-	-	-	-	-	- RTC	-	RXD8 CTS8_	-	-	-	-	-	-	-	-	-		-	LCD_D 04_B LCD_D
ľ	110	-	-	-			F000	-		-	-	-	OUT		RTS8/ SS8	_	-		-	-	-	-	-	-	-	-	03_B
1	117	H2	93	-	-	-	P605	A11/	DQ11	-	-	GTIOC 8A	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
1	118	G4	94	-	-	-	P604	D11] D12[A12/	DQ12	-	-	GTIOC 8B	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
1	119	НЗ	95	_	-	-	P603	D12]	DQ13	-	-	GTIOC	-	-	-	CTS9_	-	-	-	_	-	-	-	-	_	-	-
								A13/ D13]				7A				RTS9/ SS9											
	120		96 97	65 66			P602 P601	EBC LK	SDCL K DQM0	-	-	GTIOC 7B GTIOC	_			TXD9 RXD9			-		-		-	-			LCD_D 04_A LCD_D
				67	CLKOUT	-	P600	WR0	-	-	-	6A GTIOC	-	-	-	SCK9	-	_	-	-	-		_	-		-	03_A LCD_D
		1/0			/CACRE F							6B															02_A
1	123 124	K1	99 100	-	VCC VSS	-	-	-	-	-	-	-	-	-	-	-	-	- -	-	-	-	-	-	-	-	-	-
1	125	J3	101	68	-	KR07	P107	D07[A07/ D07]	DQ07	AGTOA0	-	GTIOC 8A	-	-	CTS8_ RTS8/ SS8	-	-	-	-	-	-	-	-	-	-	-	LCD_D 01_A
1	126	K3	102	69	-	KR06	P106	D06[A06/	DQ06	AGTOB0	-	GTIOC 8B	-	-	SCK8	-	-	SSLA3 _A	-	-	-	-	-	-	-	-	LCD_D 00_A
1	127	J4	103	70	-	IRQ0/	P105		DQ05	-	GTETRGA		-	-	TXD8/	-	-	SSLA2	-	-	-	-	-	-	-	-	LCD_T
2 1	128	L3	104	71	-	KR05 IRQ1/	P104	A05/ D05]	DQ04	-	GTETRGB	1A GTIOC	_	-	MOSI8 /SDA8 RXD8/	-	_	_A SSLA1	-	-	-			-	_	_	N3_A LCD_T
	0					KR04		A04/ D04]	540.			1B			MISO8 /SCL8			_A									N2_A
1	129	L1	105	72	-	KR03	P103	D03[A03/ D03]	DQ03	-	GTOWUP	GTIOC 2A_A	-	CTX0	CTS0_ RTS0/ SS0	-	-	SSLA0 _A	-	-	-	-	-	-	-	-	LCD_T N1_A
3 1	130	M1	106	73	-	KR02	P102	-	DQ02	AGTO0	GTOWLO	GTIOC 2B_A	-	CRX0		-	-	RSPC KA_A	-	-	-	-	-	ADTRG 0	-	-	LCD_T N0_A
! 1	131	M2	107	74	-	IRQ1/	P101		DQ01	AGTEE0	GTETRGB		-	-	TXD0/	CTS1_		MOSIA	-	-	-	-	-	-	-	-	LCD_C
1	132	N1	108	75	_	KR01 IRQ2/	P100	A01/ D01]	DOM	AGTION	GTETRGA	5A GTIOC	_		/SDA0 RXD0/	RTS1/ SS1 SCK1	_B SCL1	_A MISOA	_	_	-		_	_	_		A LCD_E
ľ	102		100	10		KR00		A00/ D00]			OTETHOA	5B			MISO0 /SCL0	COICI	_B	_A									CLK_A
1	133	L2	109	-	-	-	P800	D14[A14/ D14]	DQ14	-	-	-	-	-	_	_	-	-	-	_		-	-	-		-	-
1	134	N2	110	-	-	-	P801	-	DQ15	-	-	-	-	-	-	-	-	-	-	-	-	-	SD1 DAT4	-	-	-	-
1	135	-	-	-	-	-	P802	D15]	-	-	-	-	-	-	-	-	-	-	-	-	-	-	_A SD1	-	-	-	LCD_D
1	136						P803																DAT5 _A SD1				02_B
ľ	130		-	-	-	-	P603	-		-	-	-			-	-	-		-	-	-	-	DAT6 _A	-		-	LCD_D 01_B
1	137	-	-	-		-	P804	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	SD1 DAT7	-	-	-	LCD_D 00_B
			111		VCC	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	_A -	-	-	-	-
		M3 K4	112 113		VSS -	-	- P500	-	-	- AGTOA0	- GTIU	GTIOC 11A	-	- USB_ VBUS	-	-	-	- QSPC LK	-	-	-	-	SD1 CLK	- AN016	- IVREF0	-	-
. 1	141	M4	114	77	-	IRQ11	P501	_	-	AGTOB0	GTIV	GTIOC	_	EN USB	-	TXD5/	_	QSSL	-	-	-	_	A SD1	AN116	IVREF1	-	-
ľ												11B		OVR CUR		MOSI5 /SDA5							CMD _A				
1	142	L4	115	78	-	IRQ12	P502	-	-	-	GTIW	GTIOC 12A	-	A USB_ OVR	-	RXD5/ MISO5	-	QIO0	-	-	-	-	SD1 DAT0	AN017	IVCMP0	-	-
									L					CUR B		/SCL5		L		L			_A				L
1	143	K5	116	79	-	-	P503	-	-	-	GTETRGC	GTIOC 12B	-	USB_ EXIC	CTS6_ RTS6/	SCK5	-	QIO1	-	-	-	-	SD1 DAT1	AN117	-	-	-
1	144	L5	117	80	-	-	P504	ALE	-	-	GTETRGD	GTIOC 13A	-	EN USB_ ID	SS6 SCK6	CTS5_ RTS5/	-	QIO2	-	-	-	-	_A SD1 DAT2	AN018	-	-	-
1	145	K6	118	<u> </u>	 -	IRQ14	P505	-	-	-	-	GTIOC	-	-	RXD6/	SS5	-	QIO3	 -	-	-	-	_A SD1	AN118	_	-	-
ľ	,											13B			MISO6 /SCL6								DAT3 _A				

Pin	nun	nber	r					Extb	us	Timers				Com	munica	ation in	nterfa	ces						Analog	J	НМІ	
BGA176	LQFP176	LGA145	LQFP144	LQFP100	Power, System, Clock, Debug, CAC		I/O port	External bus	SDRAM	AGT	GPT	GPT	RTC	USBFS, CAN	SCI0,2,4,6,8 (30 MHz)	SCI1,3,5,7,9 (30 MHz)	21	SPI, QSPI	SSIE	ETHERC (MII) (25 MHz)	ETHERC (RMII) (50 MHz)	USBHS	SDHI	ADC12	DAC12, ACMPHS	стѕи	GLCDC, PDC
R5	146	L6	119	-	-	IRQ15	P506	-	-	-	-	-	-	-	TXD6/ MOSI6	-	-	-	-	-	-	-	SD1 CD_	AN019	-	-	-
N6	147	_	_	_	-	-	P507	_	_	-	-	_	_	-	/SDA6	CTS5_	_	-	-	-	-	_	A SD1	AN119	-	-	
																RTS5/ SS5							WP_ A	,			
R6		N4	120		-	-	P508	-	-	-	-	-	-	-	SCK6	SCK5	-	-	-	-	-	-	-	AN020	-	-	-
M7	149		121		VCC	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
N7 P7	150 151	M5	122 123		VSS	- IRQ13	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	- AN006/	- DA1/	-	
Ρ/	151	IVIO	123	04	-	IKQ13	PU15	-		-	-	-	-	Ī	-	-	-	-	-	-	-	-	-	AN106	IVCMP1	-	-
R7	152	N6	124	85	-	-	P014	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	AN005/	DA0/	-	-
P8	153	MZ	125	86	VREFL																			AN105	IVREF3		
R8		N7	126		VREFH	-	-	-	_	- -	- -	-	-	_	-	-	-	-			-	_	-	-	-	-	
N8	155		127		AVCC0	_	-	-	_	-	-	-	-	-	_	-	-	_	-	-	-	_	-	-	-	-	-
N9	156	L8	128	89	AVSS0	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
P9		M8	129		VREFL0	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
R9		N8	130	91	VREFH0	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	
M8	159		-	-	-	IRQ14 -DS		_		-	-	_	-	-	_	_	-	_	-	-	_	_	-	AN103	-	-	
M9	160	M9	131	-	-	IRQ13 -DS	P009	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	AN004	-		-
P10	161	N9	132	92	-	IRQ12 -DS	P008	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	AN003	-	-	-
M6	162	K7	133	93	-	-	P007	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	PGAVS S100/A	-	-	-
																								N107			
	163		134		-	IRQ11- DS		_		-	-	-	-	-		_	-	_	-	-	_	_	-		IVCMP2		
R10	164	K8	135	95	-	IRQ10 -DS	P005	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	AN101	IVCMP2	-	-
P11	165	K9	136	96	-	IRQ9- DS	P004	-	,	-	-	-	-	-	-	-	-	-	-	-	-	-	-	AN100	IVCMP2	-	-
M5	166	K10	137	97	-	-	P003	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	PGAVS	-	-	-
																								S000/A N007			
R11	167	M10	138	98	-	IRQ8- DS	P002	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	AN002	IVCMP2	-	-
N11	168	N10	139	99	-	IRQ7- DS	P001	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	AN001	IVCMP2	-	-
R12	169	L10	140	100	-	IRQ6-	P000	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	AN000	IVCMP2	-	-
M10	170	N11	141	_	VSS	DS -	_	_		-	_	_	_	_	_	_	_	_			_	_	_	_		_	
	171			-	VCC	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
P12		-	-	-	-	-	P806	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_EXT
R13	173	_	-	-	-	-	P805	-	_	-	-	-	<u> </u>	<u> </u>	-	TXD5	-	-	-	-	-	_	_	-	-		CLK_B LCD_DATA
N12																											17_B LCD_DATA
					-		P513			-	-					RXD5			_					-	-		16_B
	175				-	IRQ14	P512	-		-	-	GTIOC 0A	-	CTX1	TXD4/ MOSI4 /SDA4	-	SCL2	-	-	-	-	-	-	-	-	-	VSYNC
P13	176	M12	144	-	-	IRQ15	P511	-	-	-	-	GTIOC 0B	-	CRX1	RXD4/ MISO4	-	SDA2	-	-	-	-	-	-	-	-	-	PCKO
															/SCL4												

Note: Some pin names have the added suffix of _A, _B, and _C. When assigning the GPT, IIC, SPI, SSIE, ETHERC (RMII), SDHI, and GLCDC functionality, select the functional pins with the same suffix.

RA6M3 Group 2. Electrical Characteristics

2. Electrical Characteristics

Unless otherwise specified, the electrical characteristics of the MCU are defined under the following conditions:

 $\label{eq:vcc} VCC = AVCC0 = VCC_USB = VBATT = 2.7 \ to \ 3.6 \ V, \ 2.7 \le VREFH0/VREFH \le AVCC0, \ VCC_USBHS = AVCC_USBHS = 3.0 \ to \ 3.6 \ V, \ VSS = AVSS0 = VREFL0/VREFL = VSS_USB = VSS1_USBHS = VSS2_USBHS = PVSS_USBHS = AVSS_USBHS = 0 \ V, \ Ta = Topr.$

Figure 2.1 shows the timing conditions.

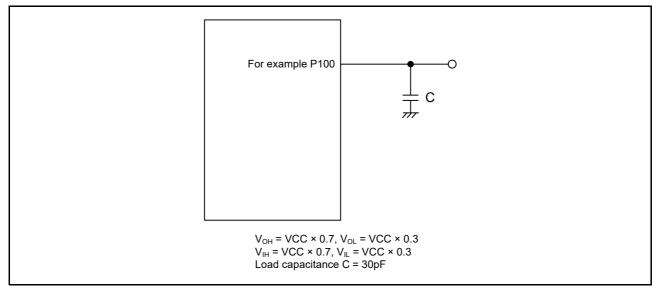


Figure 2.1 Input or output timing measurement conditions

The measurement conditions of timing specification in each peripherals are recommended for the best peripheral operation, however make sure to adjust driving abilities of each pins to meet your conditions.

2.1 Absolute Maximum Ratings

Table 2.1 Absolute maximum ratings

Parameter	Symbol	Value	Unit
Power supply voltage	VCC, VCC_USB *2	-0.3 to +4.0	V
VBATT power supply voltage	VBATT	-0.3 to +4.0	V
Input voltage (except for 5 V-tolerant ports*1)	V _{in}	-0.3 to VCC + 0.3	V
Input voltage (5 V-tolerant ports*1)	V _{in}	-0.3 to + VCC + 4.0 (max 5.8)	V
Reference power supply voltage	VREFH/VREFH0	-0.3 to AVCC0 + 0.3	V
Analog power supply voltage	AVCC0 *2	-0.3 to +4.0	V
USBHS power supply voltage	VCC_USBHS	-0.3 to +4.0	V
USBHS analog power supply voltage	AVCC_USBHS	-0.3 to +4.0	V
Analog input voltage (except for P000 to P007)	V _{AN}	-0.3 to AVCC0 + 0.3	V
Analog input voltage (P000 to P007) when PGA differential input is disabled	V _{AN}	-0.3 to AVCC0 + 0.3	V
Analog input voltage (P000 to P002, P004 to P006) when PGA differential input is enabled	V _{AN}	-1.3 to AVCC0 + 0.3	V
Analog input voltage (P003, P007) when PGA differential input is enabled	V _{AN}	-0.8 to AVCC0 + 0.3	V
Operating temperature*3,*4,*5	T _{opr}	-40 to +85 -40 to +105	°C
Storage temperature	T _{stg}	-55 to +125	°C

RA6M3 Group 2. Electrical Characteristics

Caution: Permanent damage to the MCU might result if absolute maximum ratings are exceeded.

- Note 1. Ports P205, P206, P400, P401, P407 to P415, P511, P512, P708 to P713, and PB01 are 5 V-tolerant.
- Note 2. Connect AVCC0 and VCC USB to VCC.
- Note 3. See section 2.2.1, T_i/T_a Definition.
- Note 4. Contact a Renesas Electronics sales office for information on derating operation when T_a = +85°C to +105°C. Derating is the systematic reduction of load for improved reliability.
- Note 5. The upper limit of operating temperature is 85°C or 105°C, depending on the product. For details, see section 1.3, Part Numbering.

Table 2.2 Recommended operating conditions

Parameter	Symbol	Value	Min	Тур	Max	Unit
Power supply voltages	VCC	When USB/SDRAM is not used	2.7	-	3.6	V
		When USB/SDRAM is used	3.0	-	3.6	V
	VSS		-	0	-	V
USB power supply voltages	VCC_USB, VCC_USBHS		-	VCC	-	V
	VSS_USB, AVSS_USBHS, PVSS_USBHS, VSS1_USBHS, VSS2_USBHS		-	0	-	V
VBATT power supply voltage	VBATT		1.65* ²	-	3.6	V
Analog power supply voltages	AVCC0*1		-	VCC	-	V
	AVSS0		-	0	-	V

Note 1. Connect AVCC0 to VCC. When neither the A/D converter nor the D/A converter nor the comparator is in use, do not leave the AVCC0, VREFH/VREFH0, AVSS0, and VREFL/VREFL0 pins open. Connect the AVCC0 and VREFH/VREFH0 pins to VCC, and the AVSS0 and VREFL/VREFL0 pins to VSS, respectively.

2.2 DC Characteristics

2.2.1 T_i/T_a Definition

Table 2.3 DC characteristics

Conditions: Products with operating temperature (Ta) -40 to +105°C

Parameter	Symbol	Тур	Max	Unit	Test conditions
Permissible junction temperature	T _j	-	125	°C	High-speed mode
			105* ¹		Low-speed mode Subosc-speed mode

Note: Make sure that $T_j = T_a + \theta ja \times \text{total power consumption (W)}$, where total power consumption = $(\text{VCC - V}_{OH}) \times \Sigma I_{OH} + \text{V}_{OL} \times \Sigma I_{OL} + I_{CC} \text{max} \times \text{VCC}$.

Note 1. The upper limit of operating temperature is 85°C or 105°C, depending on the product. For details, see section 1.3, Part Numbering. If the part number shows the operation temperature to 85°C, then Tj max is 105°C, otherwise, 125°C.



Note 2. Low CL crystal cannot be used below VBATT = 1.8 V.

$2.2.2 \hspace{1.5cm} \text{I/O V}_{\text{IH}}, \hspace{0.5cm} \text{V}_{\text{IL}}$

Table 2.4 I/O V_{IH}, V_{IL}

Parameter					Symbol	Min	Тур	Max	Uı
Input voltage Peripheral EXTAL(external clock input), WAIT, SPI (except						VCC × 0.8	-	-	V
(except for Schmitt trigger input pins)	function pin	RSPCK)			V _{IL}	-	-	VCC × 0.2	
	рш	D00 to D1		V _{IH}	VCC × 0.7	-	-		
		DQ00 to DQ15			V _{IL}	-	-	VCC × 0.3	1
		ETHERC			V _{IH}	2.3	-	-	
				V _{IL}	-	-	VCC × 0.2		
		IIC (SMBus)*1			V _{IH}	2.1	-		
					V _{IL}	-	-	0.8	
		IIC (SMB	us)* ²		V _{IH}	2.1	-	VCC + 3.6 (max 5.8)	
					V _{IL}	-	-	0.8	
Schmitt trigger input voltage		IIC (excep	ot for SMBus)*1		V _{IH}	VCC × 0.7	-	-	
					V _{IL}	-	-	VCC × 0.3	
				ΔV_{T}	VCC × 0.05	-	-	1	
		IIC (except for SMBus)*2			V _{IH}	VCC × 0.7	-	VCC + 3.6 (max 5.8)	
				V _{IL}	-	-	VCC × 0.3		
				ΔV_{T}	VCC × 0.05	-	-		
		5 V-tolerant ports*3, *7			V _{IH}	VCC × 0.8	-	VCC + 3.6 (max 5.8)	
					V _{IL}	-	-	VCC × 0.2	
				ΔV_T	VCC × 0.05	-	-		
		RTCIC0, RTCIC1, RTCIC2	When using the	Backup power supply is	V _{IH}	V _{BATT} × 0.8	-	V _{BATT} + 0.3	
			Function		V _{IL}	-	-	V _{BATT} × 0.2	
					ΔV_T	V _{BATT} × 0.05	-	-	
					V _{IH}	VCC × 0.8	-	Higher voltage either VCC + 0.3 V or V _{BATT} + 0.3 V	
					V _{IL}	-	-	VCC × 0.2	
					ΔV_T	VCC × 0.05	-	-	
			When not using t	V _{IH}	VCC × 0.8	-	VCC + 0.3		
			Function		V _{IL}	-	-	VCC × 0.2	
					ΔV_T	VCC × 0.05	-	-	
		Other inp	ut pins* ⁴	V _{IH}	VCC × 0.8	-	-		
				V _{IL}	-	-	VCC × 0.2		
				ΔV_{T}	VCC × 0.05	-	-		
	Ports	5 V-tolera	nt ports*5, *7		V _{IH}	VCC × 0.8	-	VCC + 3.6 (max 5.8)	
				V _{IL}	-	-	VCC × 0.2		
		Other inp	ut pins* ⁶		V _{IH}	VCC × 0.8	-	-	
					V _{IL}	-	-	VCC × 0.2	1

Note 1. SCL0_B (P204), SCL1_B, SDA1_B (total 3 pins).

Note 2. SCLO_A, SDAO_A, SCLO_B (P408), SDAO_B, SCL1_A, SDA1_A, SCL2, SDA2 (total 8 pins).

Note 3. RES and peripheral function pins associated with P205, P206, P400, P401, P407 to P415, P511, P512, P708 to P713, PB01 (total 23 pins).

RA6M3 Group 2. Electrical Characteristics

- Note 4. All input pins except for the peripheral function pins already described in the table.
- Note 5. P205, P206, P400, P401, P407 to P415, P511, P512, P708 to P713, PB01 (total 22 pins).
- Note 6. All input pins except for the ports already described in the table.
- Note 7. When VCC is less than 2.7 V, the input voltage of 5 V-tolerant ports should be less than 3.6 V, otherwise breakdown might occur because the 5 V-tolerant ports are electrically controlled to not violate the breakdown voltage.

2.2.3 I/O I_{OH}, I_{OL}

Table 2.5 I/O I_{OH}, I_{OL}

Parameter			Symbol	Min	Тур	Max	Unit
Permissible output current	Ports P008 to P010, P201	-	I _{OH}	-		-2.0	mA
(average value per pin)			I _{OL}	-	-	2.0	mA
	Ports P014, P015	-	I _{OH}	-	-	-4.0	mA
			I _{OL}	-	-	4.0	mA
	Ports P205, P206, P407 to P415,	Low drive*1	I _{OH}	-	-	-2.0	mA
	P602, P708 to P713, PB01 (total 19 pins)		I _{OL}	-	-	2.0	mA
		Middle drive*2	I _{OH}	-	-	-4.0	mA
			I _{OL}	-	-	4.0	mA
		High drive*3	l _{OH}	-	-	-20	mA
			l _{OL}	-	-	20	mA
	Other output pins*4	Low drive*1	ГОН	-	-	-2.0	mA
			I _{OL}	-	-	2.0	mA
		Middle drive*2	I _{OH}	-	-	-4.0	mA
			I _{OL}	-	-	4.0	mA
		High drive*3	I _{OH}	-	-	-16	mA
			I _{OL}	-	-	16	mA
Permissible output current	Ports P008 to P010, P201	-	l _{OH}	-	-	-4.0	mA
(max value per pin)			I _{OL}	-	-	4.0	mA
	Ports P014, P015	-	I _{OH}	-	-	-8.0	mA
			I _{OL}	-	-	8.0	mA
	Ports P205, P206, P407 to P415, P602, P708 to P713, PB01 (total 19 pins)	Low drive*1	l _{OH}	-	-	-4.0	mA
			I _{OL}	-	-	4.0	mA
		Middle drive*2	l _{OH}	-	-	-8.0	mA
			I _{OL}	-	-	8.0	mA
		High drive*3	I _{OH}	-	-	-40	mA
			I _{OL}	-	-	40	mA
	Other output pins*4	Low drive*1	I _{OH}	-	-	-4.0	mA
			I _{OL}	-	-	4.0	mA
		Middle drive*2	I _{OH}	-	-	-8.0	mA
			I _{OL}	-	-	8.0	mA
		High drive*3	I _{OH}	-	-	-32	mA
			I _{OL}	-	-	32	mA
Permissible output current	Maximum of all output pins	•	ΣI _{OH (max)}	-	-	-80	mA
(max value total pins)			ΣΙ _{ΟL (max)}	-	-	80	mA

Caution: To protect the reliability of the MCU, the output current values should not exceed the values in this table. The average output current indicates the average value of current measured during 100 µs.

- Note 1. This is the value when low driving ability is selected in the port drive capability bit in the PmnPFS register. The selected driving ability is retained in Deep Software Standby mode.
- Note 2. This is the value when middle driving ability is selected in the port drive capability bit in the PmnPFS register. The selected driving ability is retained in Deep Software Standby mode.
- Note 3. This is the value when high driving ability is selected in the port drive capability bit in the PmnPFS register. The selected driving ability is retained in Deep Software Standby mode.



RA6M3 Group 2. Electrical Characteristics

Note 4. Except for P000 to P007, P200, which are input ports.

I/O V_{OH} , V_{OL} , and Other Characteristics 2.2.4

I/O $\mathbf{V}_{\mathrm{OH}},\,\mathbf{V}_{\mathrm{OL}},$ and other characteristics Table 2.6

Parameter			Symbol	Min	Тур	Max	Unit	Test conditions
Output voltage	IIC		V _{OL}	-	-	0.4	V	I _{OL} = 3.0 mA
			V _{OL}	-	-	0.6		I _{OL} = 6.0 mA
	IIC*1		V _{OL}	-	-	0.4		I _{OL} = 15.0 mA (ICFER.FMPE = 1)
			V _{OL}	-	0.4	-		I _{OL} = 20.0 mA (ICFER.FMPE = 1)
	ETHERC		V _{OH}	VCC - 0.5	-	-		I _{OH} = -1.0 mA
			V _{OL}	-	-	0.4		I _{OL} = 1.0 mA
	Ports P205, P206, P407 to P415, P602, P708 to P713, PB01 (total 19		V _{OH}	VCC - 1.0	-	-		I _{OH} = -20 mA VCC = 3.3 V
	pins)* ²		V _{OL}	-	-	1.0		I _{OL} = 20 mA VCC = 3.3 V
	Other output pins		V _{OH}	VCC - 0.5	-	-		I _{OH} = -1.0 mA
		V _{OL}	-	-	0.5		I _{OL} = 1.0 mA	
Input leakage current	RES		I _{in}	-	-	5.0	μА	V _{in} = 0 V V _{in} = 5.5 V
	Ports P000 to P00 P200	2, P004 to P006,		-	-	1.0		V _{in} = 0 V V _{in} = VCC
	Ports P003, P007	Before initialization*3		-	-	45.0		V _{in} = 0 V V _{in} = VCC
		After initialization*4	1	-	-	1.0		V _{in} = 0 V V _{in} = VCC
Three-state leakage current (off state)	5 V-tolerant ports		I _{TSI}	-	-	5.0	μА	V _{in} = 0 V V _{in} = 5.5 V
	Other ports (excepto P007, P200)	t for ports P000		-	-	1.0		V _{in} = 0 V V _{in} = VCC
Input pull-up MOS current	Ports P0 to PB (ex P000 to P007)	cept for ports	I _p	-300	-	-10	μА	VCC = 2.7 to 3.6 V V _{in} = 0 V
Input capacitance	USB_DP, USB_DM P003, P007, P014 P401, P511, P512	, P015, P400,	C _{in} -	-	-	16	pF	Vbias = 0V Vamp = 20mV f = 1 MHz
	Other input pins			-	-	8		T _a = 25°C

Note 1. SCL0_A, SDA0_A (total 2 pins).

Note 2. This is the value when high driving ability is selected in the port drive capability bit in the PmnPFS register.

The selected driving ability is retained in Deep Software Standby mode.

Note 3. P0nPFS.ASEL (n = 3 or 7) = 1.

Note 4. P0nPFS.ASEL (n = 3 or 7) = 0.

2.2.5 Operating and Standby Current

Table 2.7 Operating and standby current (1 of 2)

Parameter					Symbol	Min	Тур	Max	Unit	Test conditions
Supply current*1		Maximum*2			Icc*3	-	-	137*2	mA	ICLK = 120 MHz PCLKA = 120 MHz* PCLKB = 60 MHz
current ·		CoreMark®*5				-	21	-		
		Normal mode	All pe while flash*	ripheral clocks enabled, (1) code executing from 4		-	34	-		PCLKC = 60 MHz PCLKD = 120 MHz FCLK = 60 MHz BCLK = 120 MHz
	High-speed mode			ripheral clocks disabled, (1) code executing from 5, *6		-	14	-		BOLIX 120 III 12
	eed	Sleep mode*5, *6	· ·		1	-	12	46		
	h-sp	Increase during BGO	Data	flash P/E		-	6	-		
	Η̈́	operation	Code	flash P/E		-	8	-		
	Lo	w-speed mode*5	· ·			-	2.4	-		ICLK = 1 MHz
	Su	bosc-speed mode*5				-	2	-		ICLK = 32.768 kHz
	So	ftware Standby mode				-	1.8	18		Ta ≤ 85°C
						-	1.8	28		Ta ≤ 105°C
		Power supplied to Standby SRAM and USB resu detecting unit		I and USB resume		-	30	79	μΑ	Ta ≤ 85°C
						-	30	113	μΑ	Ta ≤ 105°C
		Power not supplied to		r-on reset circuit low-		-	13	33	μA	Ta ≤ 85°C
	e	SRAM or USB resume detecting unit	powe	r function disabled		-	13	40		Ta ≤ 105°C
	mo		Power-on reset circuit low- power function enabled			-	6.3	28		Ta ≤ 85°C
	dp					-	6.3	34		Ta ≤ 105°C
	are Standby mode	Increase when the RTC and AGT are operating		the low-speed on-chip ator (LOCO) is in use		-	5	-	-	-
	Deep Software			a crystal oscillator for ock loads is in use		-	1.0	-		-
	Deep			a crystal oscillator for ard clock loads is in use		-	1.5	-		-
	the	RTC operating while VCC is off (with the battery backup function, only the RTC and sub-clock oscillator operate) When a crystal oscillator for low clock loads is in use When a crystal oscillator for standard clock loads is in use				-	0.9	-	- - -	V _{BATT} = 1.8 V, VCC = 0 V
						-	1.3	-		V _{BATT} = 3.3 V, VCC = 0 V
						-	1.1	-		V _{BATT} = 1.8 V, VCC = 0 V
		uring 12 bit A/D conversion				-		-		V _{BATT} = 3.3 V, VCC = 0 V
Analog oower		ring 12-bit A/D conversion	Alcc	-	0.8	1.1	mA	-		
supply current		ring 12-bit A/D conversion v	amp	_	-	2.3	3.3	mA	-	
Suitent		PGA (1ch)				-	1	3	mA	-
		ACMPHS (1unit)				-	100	150	μA	-
		mperature sensor	Mith and AMD and and		-	0.1	0.2	mA	-	
	Du	ring D/A conversion (per un	III)	Without AMP output	4	-	0.1	0.2	mA	-
			With AMP output		-	-	0.6	1.1	mA mA μA	-
		aiting for A/D, D/A conversion	·	-		0.9	1.6	-		
		OC12, DAC12 in standby mo	units)" ⁰	-		2	8	-		
Reference power supply current (VREFH0)		ring 12-bit A/D conversion (,	1.0)	AI _{REFH0}	-	70	120	μA	-
		aiting for 12-bit A/D convers		(0)		-	0.07	0.5	μA	-
	AL	C12 in standby modes (uni	t ()			-	0.07	0.5	μA	-
Reference	Du	ring 12-bit A/D conversion ((unit 1)		Al _{REFH}	-	70	120	μΑ	-
oower supply		ring D/A conversion		Without AMP output		-	0.1	0.4	mA	-
current	(pe	er unit) With AMP our		With AMP ouput		-	0.1	0.4	mA	-
(VREFH)	Wa	aiting for 12-bit A/D (unit 1), D/A (all units) conversion				-	0.07	0.8	μA	-
	ADC12 unit 1 in standby modes				1	_	0.07	0.8	μA	_

RA6M3 Group 2. Electrical Characteristics

Table 2.7 Operating and standby current (2 of 2)

Parameter	Parameter			Min	Тур	Max	Unit	Test conditions
USB	Low speed	USB	I _{CCUSBLS}	-	3.5	6.5	mA	VCC_USB
operating current		USBHS		-	10.5	13.5	mA	VCC_USBHS = AVCC_USBHS (PHYSET.HSEB = 0)
		USBHS		-	2.8	3.6	mA	VCC_USBHS = AVCC_USBHS (PHYSET.HSEB = 1)
	Full speed	USB	Iccusbfs	-	4.0	10.0	mA	VCC_USB
		USBHS		-	14	22	mA	VCC_USBHS = AVCC_USBHS (PHYSET.HSEB = 0)
		USBHS		-	6.5	13.0	mA	VCC_USBHS = AVCC_USBHS (PHYSET.HSEB = 1)
	High speed	USBHS	Iccusens	-	50	65	mA	VCC_USBHS = AVCC_USBHS
	Standby mode (direct power down)	USBHS	ICCUSBSBY	-	0.5	4.5	μA	VCC_USBHS = AVCC_USBHS

- Note 1. Supply current values are with all output pins unloaded and all input pull-up MOS transistors in the off state.
- Note 2. Measured with clocks supplied to the peripheral functions. This does not include the BGO operation.
- Note 3. ICC depends on f (ICLK) as follows. (ICLK:PCLKA:PCLKB:PCLKC:PCLKD:BCK:EBCLK = 2:2:1:1:2:1:1)
 - ICC Max. = 0.84 × f + 37 (max. operation in High-speed mode)
 - ICC Typ. = 0.09 × f + 3.7 (normal operation in High-speed mode)
 - ICC Typ. = $0.6 \times f + 1.8$ (Low-speed mode 1)
 - ICC Max. = $0.08 \times f + 37$ (Sleep mode).
- Note 4. This does not include the BGO operation.
- Note 5. Supply of the clock signal to peripherals is stopped in this state. This does not include the BGO operation.
- Note 6. FCLK, BCLK, PCLKA, PCLKB, PCLKC, and PCLKD are set to divided by 64 (3.75 MHz).
- Note 7. When using ETHERC, GLCDC, DRW, and JPEG, PCLKA frequency is such that PCLKA = ICLK.
- Note 8. When the MCU is in Software Standby mode or the MSTPCRD.MSTPD16 (ADC120 Module Stop bit) and MSTPCRD.MSTPD15 (ADC121 Module Stop bit) are in the module-stop state. See section 47.6.8, Available Functions and Register Settings of AN000 to AN002, AN007, AN100 to AN102, and AN107 in User's Manual.

RA6M3 Group 2. Electrical Characteristics

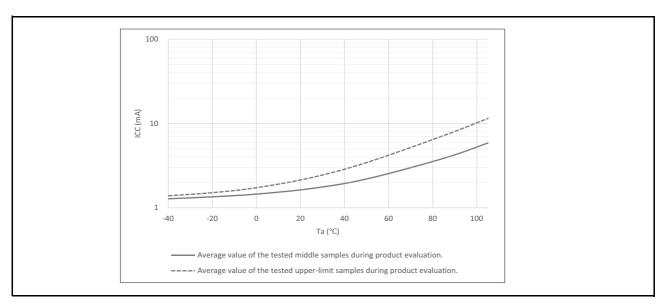


Figure 2.2 Temperature dependency in Software Standby mode (reference data)

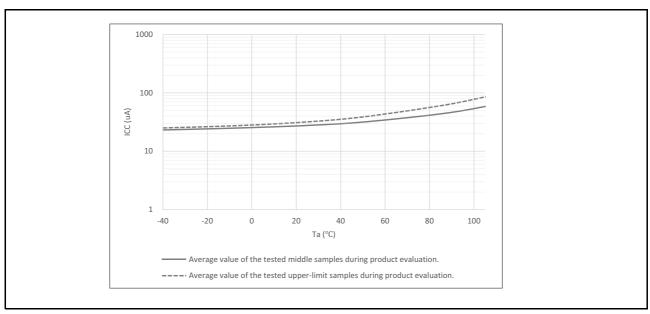


Figure 2.3 Temperature dependency in Deep Software Standby mode, power supplied to standby SRAM and USB resume detecting unit (reference data)

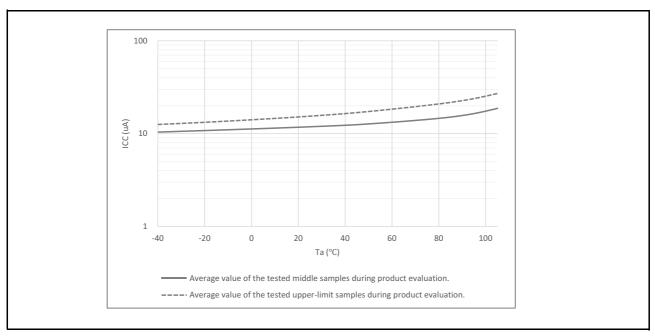


Figure 2.4 Temperature dependency in Deep Software Standby mode, power not supplied to SRAM or USB resume detecting unit, power-on reset circuit low-power function disabled (reference data)

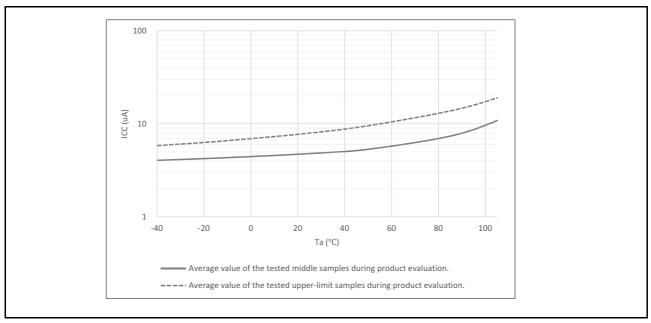


Figure 2.5 Temperature dependency in Deep Software Standby mode, power not supplied to SRAM or USB resume detecting unit, power-on reset circuit low-power function enabled (reference data)

VCC Rise and Fall Gradient and Ripple Frequency 2.2.6

Table 2.8 Rise and fall gradient characteristics

Parameter		Symbol	Min	Тур	Max	Unit	Test conditions
VCC rising gradient	Voltage monitor 0 reset disabled at startup	SrVCC	0.0084	-	20	ms/V	-
	Voltage monitor 0 reset enabled at startup		0.0084	-	-		-
	SCI/USB boot mode*1		0.0084	-	20		-
VCC falling gradient* ²		SfVCC	0.0084	-	-	ms/V	-

At boot mode, the reset from voltage monitor 0 is disabled regardless of the value of OFS1.LVDAS bit.

This applies when VBATT is used. Note 2.

Table 2.9Rise and fall gradient and ripple frequency characteristicsThe ripple voltage must meet the allowable ripple frequency $f_{r(VCC)}$ within the range between the VCC upper limit (3.6 V) and lower limit (2.7 V). When the VCC change exceeds VCC ±10%, the allowable voltage change rising and falling gradient dt/dVCC must be met.

Parameter	Symbol	Min	Тур	Max	Unit	Test conditions
Allowable ripple frequency	f _{r (VCC)}	-	-	10	kHz	Figure 2.6 V _{r (VCC)} ≤ VCC × 0.2
		-	-	1	MHz	Figure 2.6 V _{r (VCC)} ≤ VCC × 0.08
		-	-	10	MHz	Figure 2.6 V _{r (VCC)} ≤ VCC × 0.06
Allowable voltage change rising and falling gradient	dt/dVCC	1.0	-	-	ms/V	When VCC change exceeds VCC ±10%

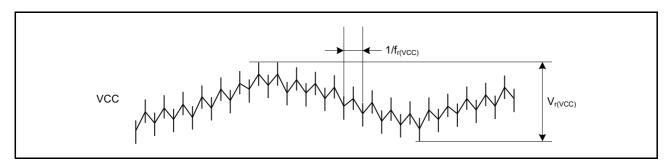


Figure 2.6 Ripple waveform

2.3 **AC Characteristics**

2.3.1 Frequency

Table 2.10 Operation frequency value in high-speed mode

Parameter				Min	Тур	Max	Unit
Operation frequency	System clock (ICLK*2)		f	-	-	120	MHz
	Peripheral module clock (F	Peripheral module clock (PCLKA)*2		-	-	120	
	Peripheral module clock (PCLKB)*2			-	-	60	
	Peripheral module clock (PCLKC)*2			_*3	-	60	
	Peripheral module clock (PCLKD)*2			-	-	120	
	Flash interface clock (FCLI	K)*2		_*1	-	60	
	External bus clock (BCLK)*2 EBCLK pin output SDCLK pin output VCC ≥ 3.0 V			-	-	120	
				-	-	60	
				-	-	120	

- Note 1. FCLK must run at a frequency of at least 4 MHz when programming or erasing the flash memory.
- Note 2. See section 9, Clock Generation Circuit in User's Manual for the relationship between the ICLK, PCLKA, PCLKB, PCLKC, PCLKD, FCLK, and BCLK frequencies.
- Note 3. When the ADC12 is used, the PCLKC frequency must be at least 1 MHz.

Table 2.11 Operation frequency value in low-speed mode

Parameter		Symbol	Min	Тур	Max	Unit
Operation frequency	System clock (ICLK)*2	f	-	-	1	MHz
	Peripheral module clock (PCLKA)*2		-	-	1	
	Peripheral module clock (PCLKB)*2		-	-	1	
	Peripheral module clock (PCLKC)*2,*3		_*3	-	1	
	Peripheral module clock (PCLKD)*2		-	-	1	
	Flash interface clock (FCLK)*1, *2		-	-	1	
	External bus clock (BCLK)		-	-	1	
	EBCLK pin output		-	-	1	

- Note 1. Programming or erasing the flash memory is disabled in low-speed mode.
- Note 2. See section 9, Clock Generation Circuit in User's Manual for the relationship between the ICLK, PCLKA, PCLKB, PCLKC, PCLKD, FCLK, and BCLK frequencies.
- Note 3. When the ADC12 is used, the PCLKC frequency must be set to at least 1 MHz.

Table 2.12 Operation frequency value in Subosc-speed mode

Parameter		Symbol	Min	Тур	Max	Unit
Operation frequency	System clock (ICLK)*2	f	27.8	-	37.7	kHz
	Peripheral module clock (PCLKA)*2		-	-	37.7	
	Peripheral module clock (PCLKB)*2		-	-	37.7	
	Peripheral module clock (PCLKC)*2,*3		-	-	37.7	
	Peripheral module clock (PCLKD)*2		-	-	37.7	
	Flash interface clock (FCLK)*1, *2		27.8	-	37.7	
	External bus clock (BCLK)*2		-	-	37.7	
	EBCLK pin output		-	-	37.7	

- Note 1. Programming or erasing the flash memory is disable in Subosc-speed mode.
- Note 2. See section 9, Clock Generation Circuit in User's Manual for the relationship between the ICLK, PCLKA, PCLKB, PCLKC, PCLKD, FCLK, and BCLK frequencies.
- Note 3. The ADC12 cannot be used.

2.3.2 Clock Timing

Table 2.13 Clock timing except for sub-clock oscillator (1 of 2)

Parameter	Symbol	Min	Тур	Max	Unit	Test conditions
EBCLK pin output cycle time	t _{Bcyc}	16.6	-	-	ns	Figure 2.7
EBCLK pin output high pulse width	t _{CH}	3.3	-	-	ns	
EBCLK pin output low pulse width	t _{CL}	3.3	-	-	ns	7
EBCLK pin output rise time	t _{Cr}	-	-	5.0	ns	
EBCLK pin output fall time	t _{Cf}	-	-	5.0	ns	
SDCLK pin output cycle time	t _{SDcyc}	8.33	-	-	ns	7
SDCLK pin output high pulse width	t _{CH}	1.0	-	-	ns	
SDCLK pin output low pulse width	t _{CL}	1.0	-	-	ns	
SDCLK pin output rise time	t _{Cr}	-	-	3.0	ns	
SDCLK pin output fall time	t _{Cf}	-	-	3.0	ns	

Table 2.13 Clock timing except for sub-clock oscillator (2 of 2)

Parameter		Symbol	Min	Тур	Max	Unit	Test conditions
EXTAL external clock input	cycle time	t _{EXcyc}	41.66	-	-	ns	Figure 2.8
EXTAL external clock input	high pulse width	t _{EXH}	15.83	-	-	ns	1
EXTAL external clock input	low pulse width	t _{EXL}	15.83	-	-	ns	1
EXTAL external clock rise t	ime	t _{EXr}	-	-	5.0	ns	1
EXTAL external clock fall time		t _{EXf}	-	-	5.0	ns	1
Main clock oscillator frequency		f _{MAIN}	8	-	24	MHz	-
Main clock oscillation stabil (crystal) *1	ization wait time	t _{MAINOSCWT}	-	-	_*1	ms	Figure 2.9
LOCO clock oscillation frequency		f _{LOCO}	27.8528	32.768	37.6832	kHz	-
LOCO clock oscillation stabilization wait time		t _{LOCOWT}	-	-	60.4	μs	Figure 2.10
ILOCO clock oscillation frequency		f _{ILOCO}	12.75	15	17.25	kHz	-
MOCO clock oscillation frequency		F _{MOCO}	6.8	8	9.2	MHz	-
MOCO clock oscillation sta	bilization wait time	t _{MOCOWT}	-	-	15.0	μs	-
HOCO clock oscillator	Without FLL	f _{HOCO16}	15.78	16	16.22	MHz	-20 ≤ Ta ≤ 105°C
oscillation frequency		f _{HOCO18}	17.75	18	18.25		
		f _{HOCO20}	19.72	20	20.28		
		f _{HOCO16}	15.71	16	16.29		-40 ≤ Ta ≤ -20°C
		f _{HOCO18}	17.68	18	18.32		
		f _{HOCO20}	19.64	20	20.36		
	With FLL	f _{HOCO16}	15.960	16	16.040		-40 ≤ Ta ≤ 105°C
		f _{HOCO18}	17.955	18	18.045		Sub-clock frequency accuracy
		f _{HOCO20}	19.950	20	20.050		is ±50 ppm.
HOCO clock oscillation stabilization wait time*2		t _{HOCOWT}	-	-	64.7	μs	-
FLL stabilization wait time		t _{FLLWT}	-	-	1.8	ms	-
PLL clock frequency		f _{PLL}	120	-	240	MHz	-
PLL clock oscillation stabilize	zation wait time	t _{PLLWT}	-	-	174.9	μs	Figure 2.11

Note 1. When setting up the main clock oscillator, ask the oscillator manufacturer for an oscillation evaluation and use the results as the recommended oscillation stabilization time. Set the MOSCWTCR register to a value equal to or greater than the recommended

Table 2.14 Clock timing for the sub-clock oscillator

Parameter	Symbol	Min	Тур	Max	Unit	Test conditions
Sub-clock frequency	f _{SUB}	-	32.768	-	kHz	-
Sub-clock oscillation stabilization wait time	t _{SUBOSCWT}	-	-	*1	S	Figure 2.12

Note 1. When setting up the sub-clock oscillator, ask the oscillator manufacturer for an oscillation evaluation and use the results as the recommended oscillation stabilization time.

After changing the setting in the SOSCCR.SOSTP bit to start sub-clock operation, only start using the sub-clock oscillator after the sub-clock oscillation stabilization time elapses with an adequate margin. Two times the value shown is recommended.

After changing the setting in the MOSCCR.MOSTP bit to start main clock operation, read the OSCSF.MOSCSF flag to confirm that it is 1, and then start using the main clock oscillator.

Note 2. This is the time from release from reset state until the HOCO oscillation frequency (fHOCO) reaches the range for guaranteed operation.

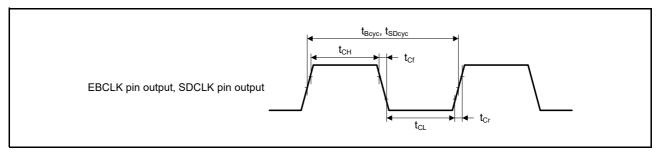


Figure 2.7 EBCLK and SDCLK output timing

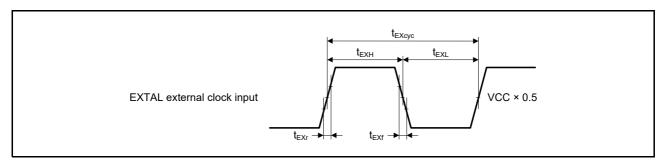


Figure 2.8 EXTAL external clock input timing

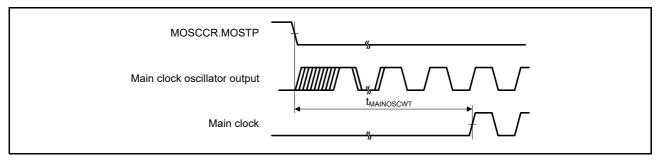


Figure 2.9 Main clock oscillation start timing

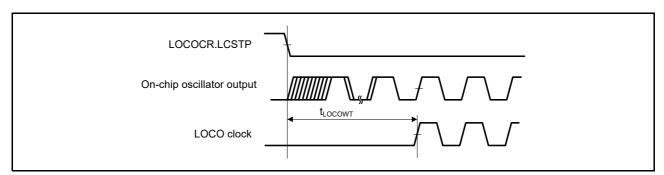


Figure 2.10 LOCO clock oscillation start timing

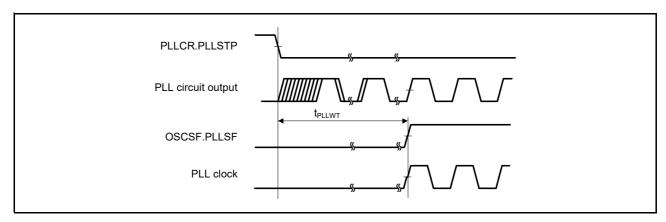


Figure 2.11 PLL clock oscillation start timing

Note: Only operate the PLL is operated after main clock oscillation has stabilized.

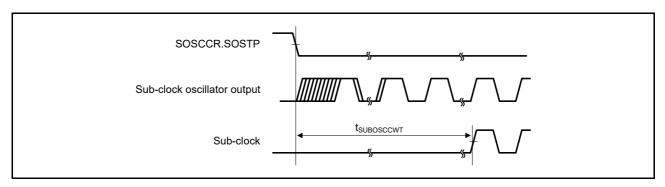


Figure 2.12 Sub-clock oscillation start timing

2.3.3 Reset Timing

Table 2.15 Reset timing

Parameter	Parameter		Min	Тур	Max	Unit	Test conditions
RES pulse width Power-on		t _{RESWP}	1	-	-	ms	Figure 2.13
	Deep Software Standby mode	t _{RESWD}	0.6	-	-	ms	Figure 2.14
	Software Standby mode, Subosc-speed mode	t _{RESWS}	0.3	-	-	ms	
	All other	t _{RESW}	200	-	-	μs	
Wait time after RE	S cancellation	t _{RESWT}	-	29	33	μs	Figure 2.13
Wait time after internal reset cancellation (IWDT reset, WDT reset, software reset, SRAM parity error reset, SRAM ECC error reset, bus master MPU error reset, bus slave MPU error reset, stack pointer error reset)		t _{RESW2}	-	320	408	μs	-

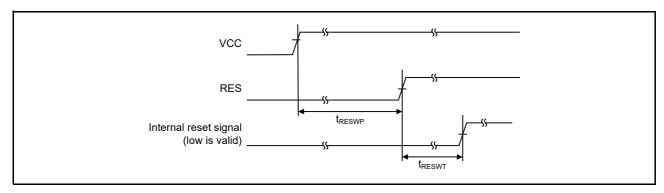


Figure 2.13 Power-on reset timing

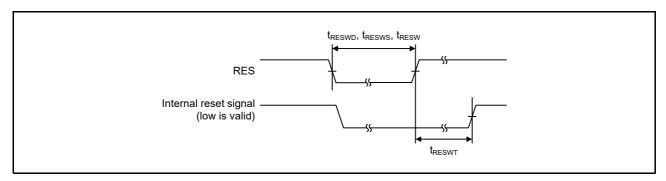


Figure 2.14 Reset input timing

2.3.4 Wakeup Timing

Table 2.16 Timing of recovery from low power modes

Parameter	Parameter		Symbol	Min	Тур	Max	Unit	Test conditions
Recovery time from Software	Crystal resonator	System clock source is main clock oscillator*2	t _{SBYMC}	-	2.4* ⁹	2.8*9	ms	Figure 2.15 The division
Standby mode*1 connected to main clock oscillator		System clock source is PLL with main clock oscillator*3	t _{SBYPC}	-	2.7*9	3.2*9	ms	ratio of all oscillators is 1.
	External clock input	System clock source is main clock oscillator*4	t _{SBYEX}	-	230* ⁹	280*9	μs	
	to main clock oscillator	System clock source is PLL with main clock oscillator*5	t _{SBYPE}	-	570* ⁹	700* ⁹	μs	
	System clock source is sub-clock oscillator*8		t _{SBYSC}	-	1.2* ⁹	1.3*9	ms	
	System clock	source is LOCO*8	t _{SBYLO}	-	1.2* ⁹	1.4*9	ms	
	System clock oscillator*6	source is HOCO clock	t _{SBYHO}	-	240*9, *10	310 *9, *10	μs	
•	System clock oscillator*7	source is MOCO clock	t _{SBYMO}	-	220*9	300*9	μs	
Recovery time from	n Deep Softwa	re Standby mode	t _{DSBY}	-	0.65	1.0	ms	Figure 2.16
Wait time after cancellation of Deep Software Standby mode		t _{DSBYWT}	34	-	35	t _{cyc}]	
Recovery time from Software	Software source is HOCO (20 MHz)		t _{SNZ}	-	35* ^{9,} * ¹⁰	71 *9, *10	μs	Figure 2.17
Standby mode to Snooze mode	High-speed r source is MC	mode when system clock DCO (8 MHz)	t _{SNZ}	-	11* ⁹	14* ⁹	μs	

Note 1. The recovery time is determined by the system clock source. When multiple oscillators are active, the recovery time can be determined with the following equation:
 Total recovery time = recovery time for an oscillator as the system clock source + the longest oscillation stabilization time of any oscillators requiring longer stabilization times than the system clock source + 2 LOCO cycles (when LOCO is operating) + 3 SOSC cycles (when Subosc is oscillating and MSTPC0 = 0 (CAC module stop)).

- Note 2. When the frequency of the crystal is 24 MHz (Main Clock Oscillator Wait Control Register (MOSCWTCR) is set to 05h). For other settings (MOSCWTCR is set to Xh), the recovery time can be determined with the following equation:

 t_{SBYMC} (MOSCWTCR = Xh) = t_{SBYMC} (MOSCWTCR = 05h) + (t_{MAINOSCWT} (MOSCWTCR = Xh) t_{MAINOSCWT} (MOSCWTCR = 05h))
- Note 3. When the frequency of PLL is 240 MHz (Main Clock Oscillator Wait Control Register (MOSCWTCR) is set to 05h). For other settings (MOSCWTCR is set to Xh), the recovery time can be determined with the following equation:

 t_{SBYMC} (MOSCWTCR = Xh) = t_{SBYMC} (MOSCWTCR = 05h) + (t_{MAINOSCWT} (MOSCWTCR = Xh) t_{MAINOSCWT} (MOSCWTCR = 05h))
- Note 4. When the frequency of the external clock is 24 MHz (Main Clock Oscillator Wait Control Register (MOSCWTCR) is set to 01h). For other settings (MOSCWTCR is set to Xh), the recovery time can be determined with the following equation:

 t_{SBYMC} (MOSCWTCR = Xh) = t_{SBYMC} (MOSCWTCR = 01h) + (t_{MAINOSCWT} (MOSCWTCR = Xh) t_{MAINOSCWT} (MOSCWTCR = 01h))
- Note 5. When the frequency of PLL is 240 MHz (Main Clock Oscillator Wait Control Register (MOSCWTCR) is set to 01h). For other settings (MOSCWTCR is set to Xh), the recovery time can be determined with the following equation:
 t_{SBYMC} (MOSCWTCR = Xh) = t_{SBYMC} (MOSCWTCR = 01h) + (t_{MAINOSCWT} (MOSCWTCR = Xh) t_{MAINOSCWT} (MOSCWTCR = 01h))
- Note 6. The HOCO frequency is 20 MHz.
- Note 7. The MOCO frequency is 8 MHz.
- Note 8. In Subosc-speed mode, the sub-clock oscillator or LOCO continues oscillating in Software Standby mode.
- Note 9. When the SNZCR.RXDREQEN bit is set to 0, the following time is added as the power supply recovery time: STCONR.STCON[1:0] = 00b:16 μs (typical), 34 μs (maximum) STCONR.STCON[1:0] = 11b:16 μs (typical), 104 μs (maximum).
- Note 10. When the SNZCR.RXDREQEN bit is set to 0, 16 μs (typical) or 18 μs (maximum) is added as the HOCO wait time.

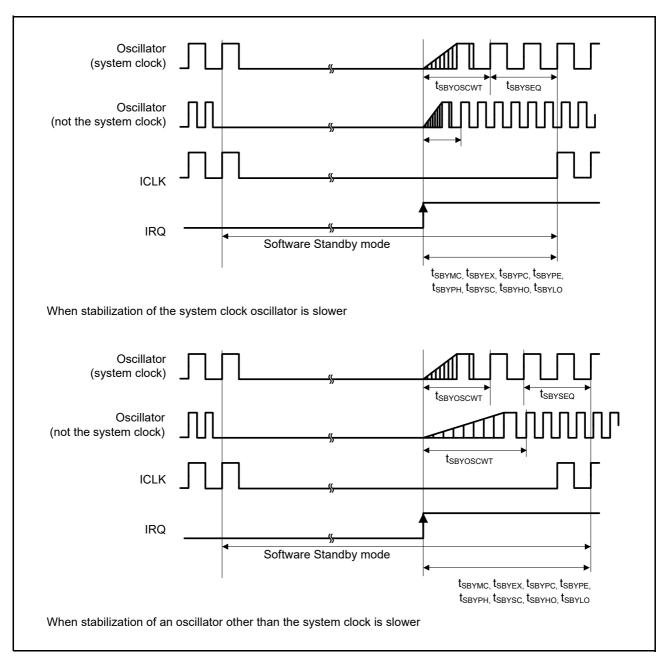


Figure 2.15 Software Standby mode cancellation timing

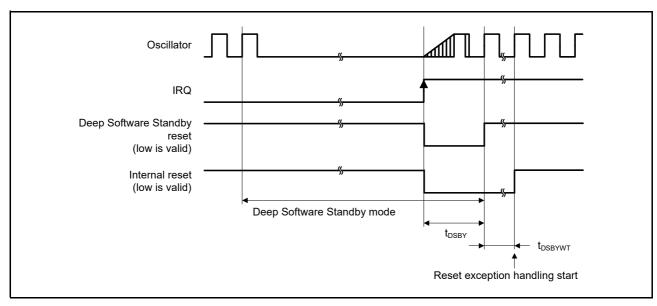


Figure 2.16 Deep Software Standby mode cancellation timing

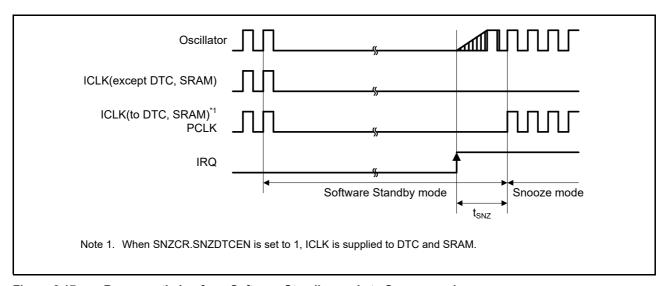


Figure 2.17 Recovery timing from Software Standby mode to Snooze mode

2.3.5 NMI and IRQ Noise Filter

Table 2.17 NMI and IRQ noise filter

Parameter	Symbol	000	Тур	Max	Unit	Test conditions			
NMI pulse width	t _{NMIW}		-	ns	NMI digital filter disabled	t _{Pcyc} × 2 ≤ 200 ns			
		t _{Pcyc} × 2*1	-	-			t _{Pcyc} × 2 > 200 ns		
		200	-	-		NMI digital filter enabled	t _{NMICK} × 3 ≤ 200 ns		
		t _{NMICK} × 3.5*2	-	-			t _{NMICK} × 3 > 200 ns		
IRQ pulse width	t _{IRQW}	200	-	-	ns	IRQ digital filter disabled	t _{Pcyc} × 2 ≤ 200 ns		
		t _{Pcyc} × 2*1	-	-			t _{Pcyc} × 2 > 200 ns		
		200	-	-		IRQ digital filter enabled	t _{IRQCK} × 3 ≤ 200 ns		
		t _{IRQCK} × 3.5*3	-	-			t _{IRQCK} × 3 > 200 ns		

Note: 200 ns minimum in Software Standby mode.

Note: If the clock source is switched, add 4 clock cycles of the switched source.

2. Electrical Characteristics RA6M3 Group

- $t_{\mbox{\footnotesize PCVC}}$ indicates the PCLKB cycle. Note 1.
- $t_{\mbox{\scriptsize NMICK}}$ indicates the cycle of the NMI digital filter sampling clock. Note 2.
- t_{IRQCK} indicates the cycle of the IRQi digital filter sampling clock. Note 3.

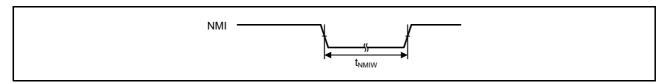


Figure 2.18 **NMI** interrupt input timing

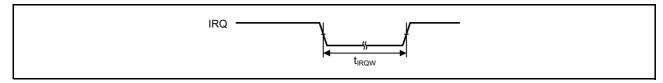


Figure 2.19 IRQ interrupt input timing

2.3.6 Bus Timing

Table 2.18 Bus timing (1 of 2) Condition 1: When using the CS area controller (CSC).

BCLK = 8 to 120 MHz, EBCLK = 8 to 60 MHz

VCC = AVCC0 = VCC_USB = VBATT = 2.7 to 3.6 V, VREFH/VREFH0 = 2.7 V to AVCC0,

VCC_USBHS = AVCC_USBHS = 3.0 to 3.6 V

Output load conditions: VOH = VCC × 0.5, VOL = VCC × 0.5, C = 30 pF

EBCLK: High drive output is selected in the port drive capability bit in the PmnPFS register.

Others: Middle drive output is selected in the port drive capability bit in the PmnPFS register.

Condition 2: When using the SDRAM area controller (SDRAMC).

BCLK = SDCLK = 8 to 120 MHz

VCC = AVCC0 = VCC_USB = VBATT = 3.0 to 3.6 V, VREFH/VREFH0 = 3.0 V to AVCC0,

VCC_USBHS = AVCC_USBHS = 3.0 to 3.6 V

Output load conditions: VOH = VCC × 0.5, VOL = VCC × 0.5, C = 15 pF

High drive output is selected in the port drive capability bit in the PmnPFS register.

Condition 3: When using the SDRAM area controller (SDRAMC) and CS area controller (CSC) simultaneously.

BCLK = SDCLK = 8 to 60 MHz

VCC = AVCC0 = VCC_USB = VBATT = 3.0 to 3.6 V, VREFH/VREFH0 = 3.0 V to AVCC0,

VCC USBHS = AVCC USBHS = 3.0 to 3.6 V

Output load conditions: VOH = VCC × 0.5, VOL = VCC × 0.5, C = 15 pF

High drive output is selected in the port drive capability bit in the PmnPFS register.

Parameter	Symbol	Min	Max	Unit	Test conditions
Address delay	t _{AD}	-	12.5	ns	Figure 2.20 to
Byte control delay	t _{BCD}	-	12.5	ns	Figure 2.25
CS delay	t _{CSD}	-	12.5	ns	
ALE delay time	t _{ALED}	-	12.5	ns	
RD delay	t _{RSD}	-	12.5	ns	
Read data setup time	t _{RDS}	12.5	-	ns	
Read data hold time	t _{RDH}	0	-	ns	
WR/WRn delay	t _{WRD}	-	12.5	ns	
Write data delay	t _{WDD}	-	12.5	ns	
Write data hold time	t _{WDH}	0	-	ns	
WAIT setup time	t _{WTS}	12.5	-	ns	Figure 2.26
WAIT hold time	twтн	0	-	ns	

Table 2.18 Bus timing (2 of 2) Condition 1: When using the CS area controller (CSC).

BCLK = 8 to 120 MHz, EBCLK = 8 to 60 MHz

VCC = AVCC0 = VCC_USB = VBATT = 2.7 to 3.6 V, VREFH/VREFH0 = 2.7 V to AVCC0,

VCC USBHS = AVCC USBHS = 3.0 to 3.6 V

Output load conditions: VOH = VCC \times 0.5, VOL = VCC \times 0.5, C = 30 pF

EBCLK: High drive output is selected in the port drive capability bit in the PmnPFS register. Others: Middle drive output is selected in the port drive capability bit in the PmnPFS register.

Condition 2: When using the SDRAM area controller (SDRAMC).

BCLK = SDCLK = 8 to 120 MHz

 $\label{eq:VCC} VCC = AVCC0 = VCC_USB = VBATT = 3.0 to 3.6 V, VREFH/VREFH0 = 3.0 V to AVCC0, VCC_USBHS = AVCC_USBHS = 3.0 to 3.6 V$

Output load conditions: VOH = VCC × 0.5, VOL = VCC × 0.5, C = 15 pF

High drive output is selected in the port drive capability bit in the PmnPFS register.

Condition 3: When using the SDRAM area controller (SDRAMC) and CS area controller (CSC) simultaneously.

BCLK = SDCLK = 8 to 60 MHz

VCC = AVCC0 = VCC_USB = VBATT = 3.0 to 3.6 V, VREFH/VREFH0 = 3.0 V to AVCC0,

VCC_USBHS = AVCC_USBHS = 3.0 to 3.6 V

Output load conditions: VOH = VCC × 0.5, VOL = VCC × 0.5, C = 15 pF

High drive output is selected in the port drive capability bit in the PmnPFS register.

Parameter	Symbol	Min	Max	Unit	Test conditions
Address delay 2 (SDRAM)	t _{AD2}	0.8	6.8	ns	Figure 2.27 to
CS delay 2 (SDRAM)	t _{CSD2}	0.8	6.8	ns	Figure 2.33
DQM delay (SDRAM)	t _{DQMD}	0.8	6.8	ns	
CKE delay (SDRAM)	t _{CKED}	0.8	6.8	ns	
Read data setup time 2 (SDRAM)	t _{RDS2}	2.9	-	ns	
Read data hold time 2 (SDRAM)	t _{RDH2}	1.5	-	ns	
Write data delay 2 (SDRAM)	t _{WDD2}	-	6.8	ns	
Write data hold time 2 (SDRAM)	t _{WDH2}	0.8	-	ns	
WE delay (SDRAM)	t _{WED}	0.8	6.8	ns	
RAS delay (SDRAM)	t _{RASD}	0.8	6.8	ns	
CAS delay (SDRAM)	t _{CASD}	0.8	6.8	ns	

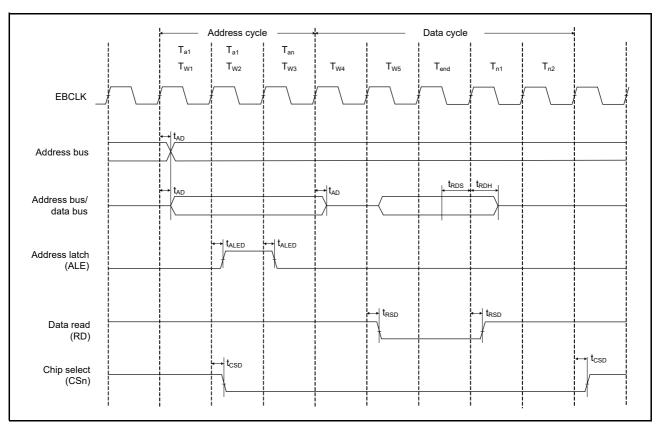


Figure 2.20 Address/data multiplexed bus read access timing

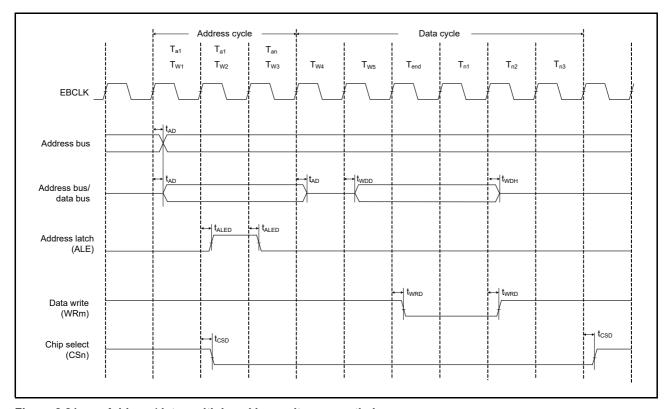


Figure 2.21 Address/data multiplexed bus write access timing

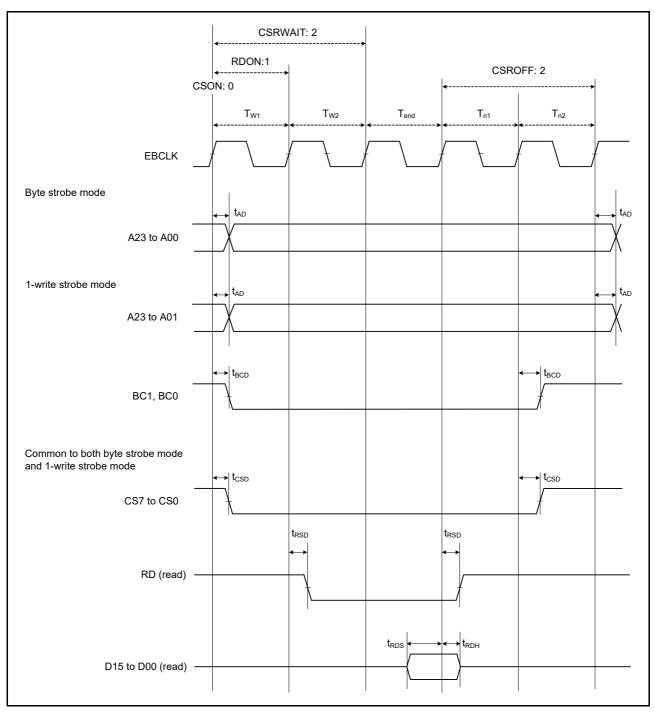


Figure 2.22 External bus timing for normal read cycle with bus clock synchronized

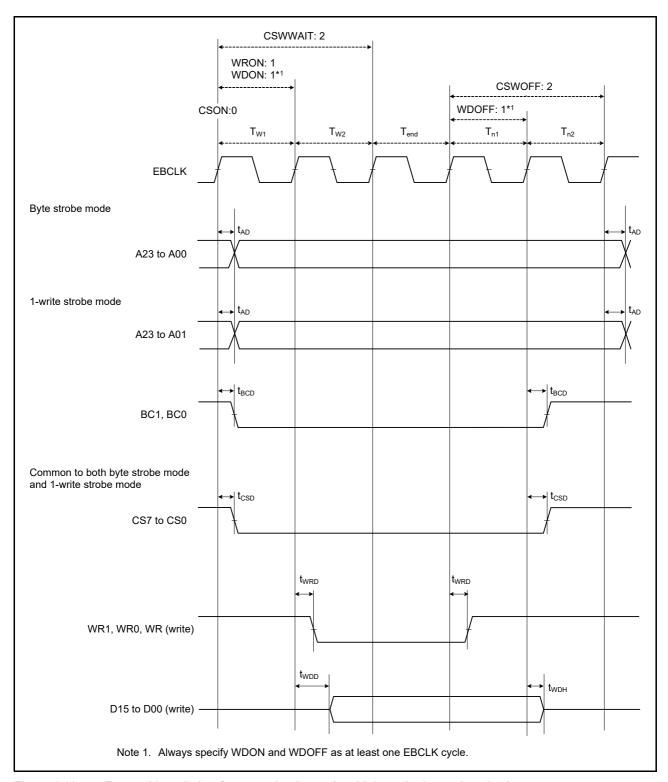


Figure 2.23 External bus timing for normal write cycle with bus clock synchronized

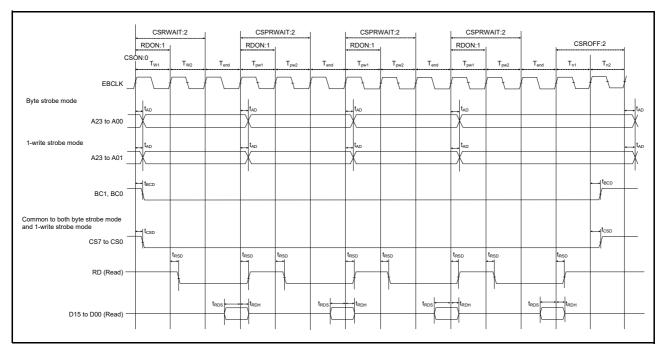


Figure 2.24 External bus timing for page read cycle with bus clock synchronized

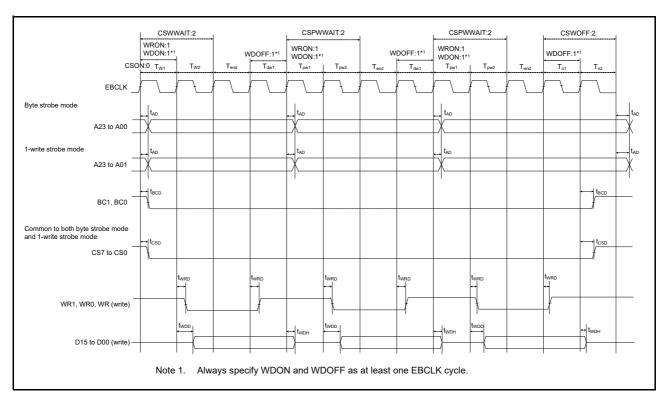


Figure 2.25 External bus timing for page write cycle with bus clock synchronized

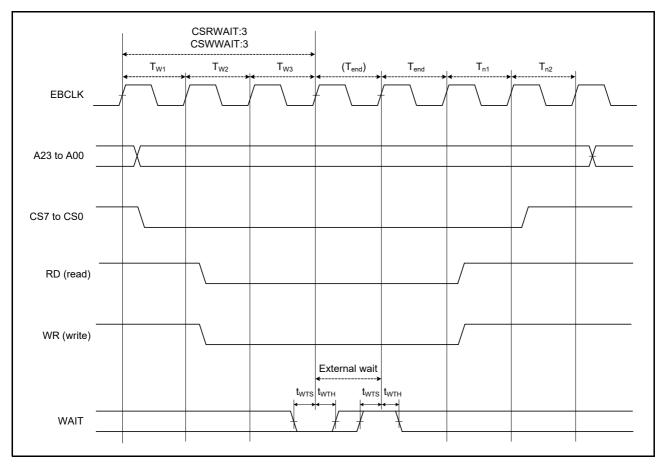


Figure 2.26 External bus timing for external wait control

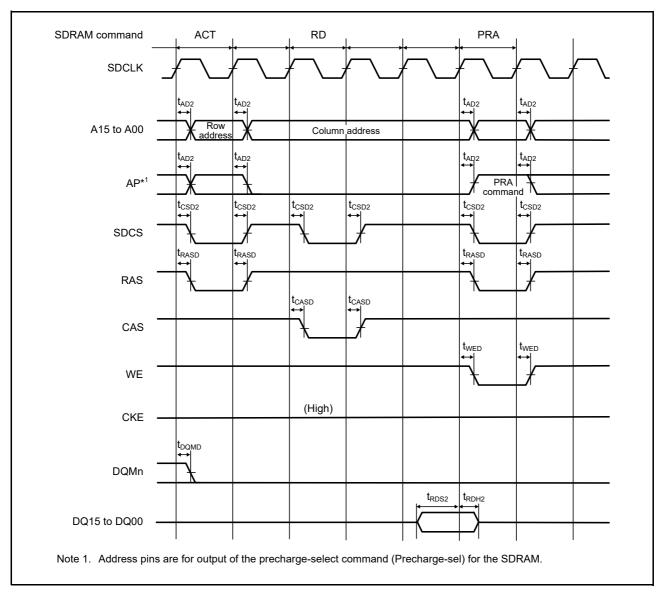


Figure 2.27 SDRAM single read timing

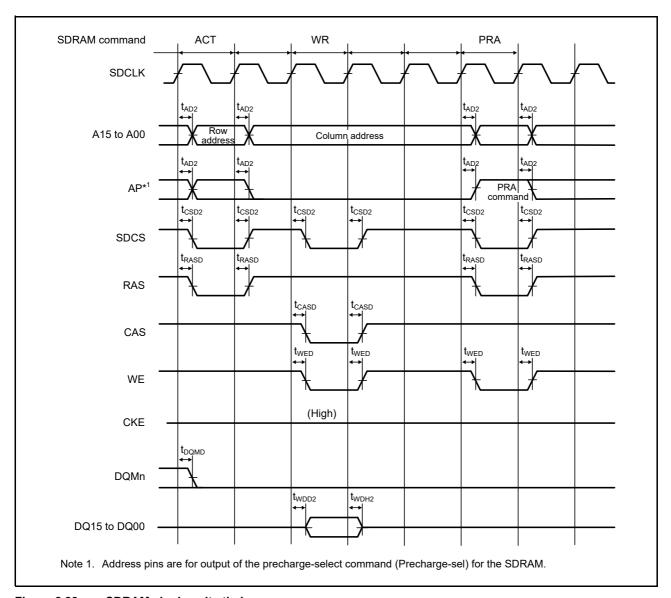


Figure 2.28 SDRAM single write timing

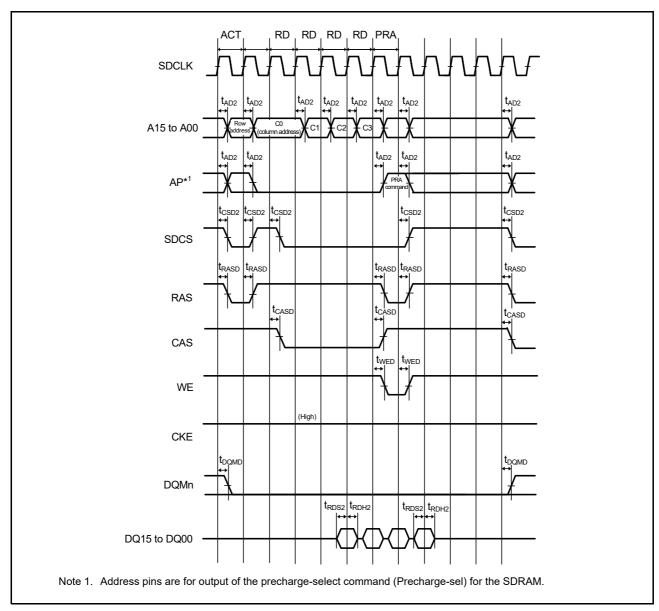


Figure 2.29 SDRAM multiple read timing

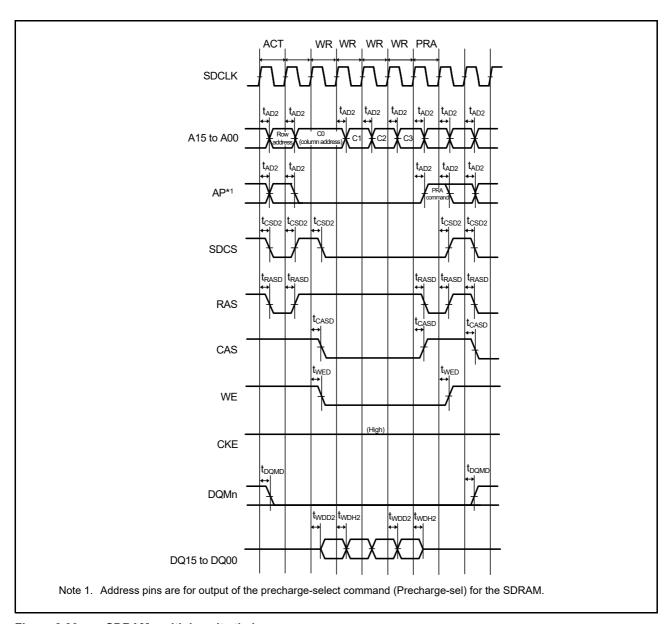


Figure 2.30 SDRAM multiple write timing

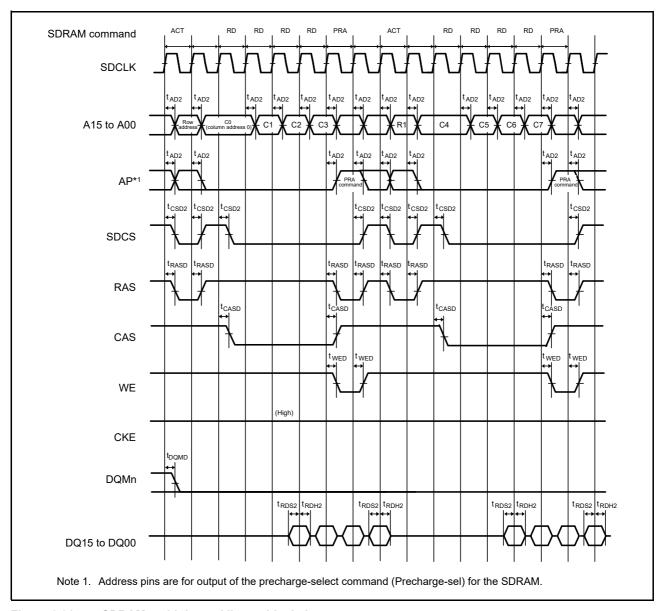


Figure 2.31 SDRAM multiple read line stride timing

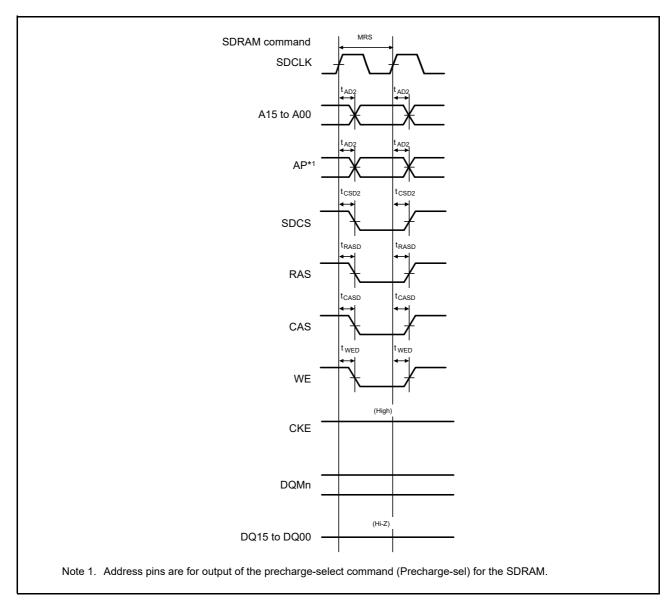


Figure 2.32 SDRAM mode register set timing

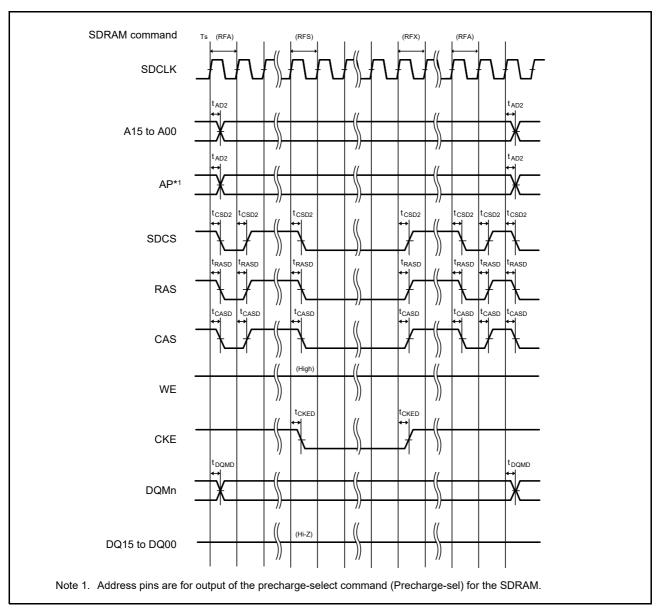


Figure 2.33 SDRAM self-refresh timing

2.3.7 I/O Ports, POEG, GPT32, AGT, KINT, and ADC12 Trigger Timing

Table 2.19 I/O ports, POEG, GPT32, AGT, KINT, and ADC12 trigger timing (1 of 2)

GPT32 Conditions:

High drive output is selected in the port drive capability bit in the PmnPFS register.

AGT Conditions:

Middle drive output is selected in the port drive capability bit in the PmnPFS register.

Parameter		Symbol	Min	Max	Unit	Test conditions
I/O ports	Input data pulse width	t _{PRW}	1.5	-	t _{Pcyc}	Figure 2.34
POEG	POEG input trigger pulse width	t _{POEW}	3	-	t _{Pcyc}	Figure 2.35

I/O ports, POEG, GPT32, AGT, KINT, and ADC12 trigger timing (2 of 2) **Table 2.19**

GPT32 Conditions:

High drive output is selected in the port drive capability bit in the PmnPFS register.

AGT Conditions:

Middle drive output is selected in the port drive capability bit in the PmnPFS register.

Parameter			Symbol	Min	Max	Unit	Test conditions
GPT32	Input capture pulse width	Single edge	t _{GTICW}	1.5	-	t _{PDcyc}	Figure 2.36
		Dual edge		2.5	-		
	GTIOCxY output skew	Middle drive buffer	t _{GTISK} *1	-	4	ns	Figure 2.37
	(x = 0 to 7, Y= A or B)	High drive buffer		-	4		
	GTIOCxY output skew	Middle drive buffer		-	4		
	(x = 8 to 13, Y = A or B)	High drive buffer		-	4		
	GTIOCxY output skew (x = 0 to 13, Y = A or B)	Middle drive buffer		-	6		
		High drive buffer		-	6		
	OPS output skew GTOUUP, GTOULO, GTOVUP, GTOVLO, GTOWUP, GTOWLO		t _{GTOSK}	-	5	ns	Figure 2.38
GPT(PWM Delay Generation Circuit)	GTIOCxY_Z output skew (x = 0 to 3, Y = A or B, Z = A)		t _{HRSK} *2	-	2.0	ns	Figure 2.39
AGT	AGTIO, AGTEE input cycle		t _{ACYC} *3	100	-	ns	Figure 2.40
	AGTIO, AGTEE input high width, low width			40	-	ns	
	AGTIO, AGTO, AGTOA, AGTOB output cycle			62.5	-	ns	
ADC12	ADC12 trigger input pulse width t		t _{TRGW}	1.5	-	t _{Pcyc}	Figure 2.41
KINT	KRn (n = 00 to 07) pulse width		t _{KR}	250	-	ns	Figure 2.42

 $t_{\mbox{\footnotesize PCyc}}$: PCLKB cycle, $t_{\mbox{\footnotesize PDcyc}}$: PCLKD cycle. Note:

This skew applies when the same driver I/O is used. If the I/O of the middle and high drivers is mixed, operation is not Note 1.

guaranteed.

Note 2. The load is 30 pF.

Note 3. Constraints on input cycle:

> When not switching the source clock: $t_{\text{Pcyc}} \times 2 < t_{\text{ACYC}}$ should be satisfied. When switching the source clock: $t_{Pcyc} \times 6 < t_{ACYC}$ should be satisfied.

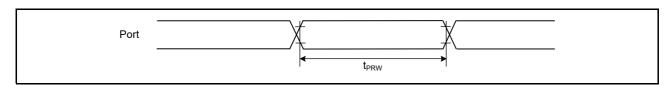


Figure 2.34 I/O ports input timing

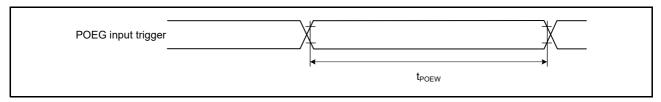


Figure 2.35 **POEG** input trigger timing

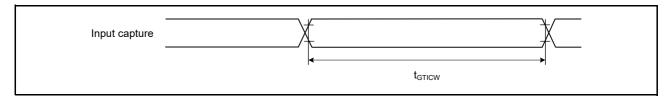


Figure 2.36 GPT32 input capture timing

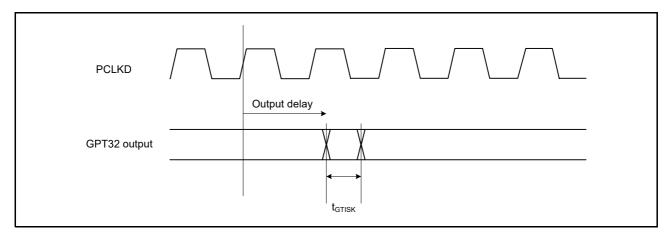


Figure 2.37 GPT32 output delay skew

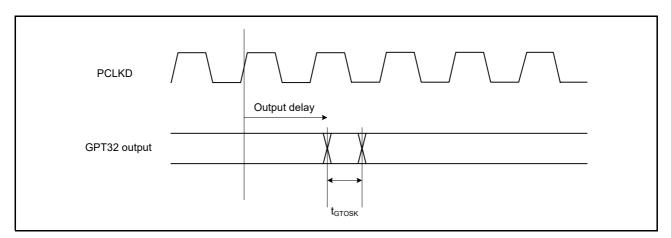


Figure 2.38 GPT32 output delay skew for OPS

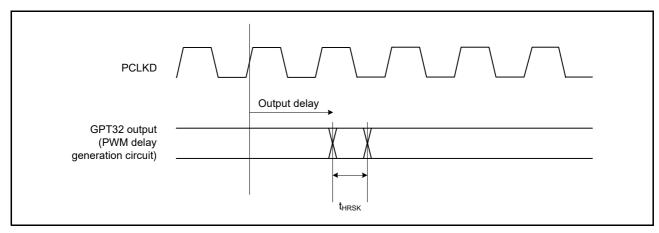


Figure 2.39 GPT32 (PWM Delay Generation Circuit) output delay skew

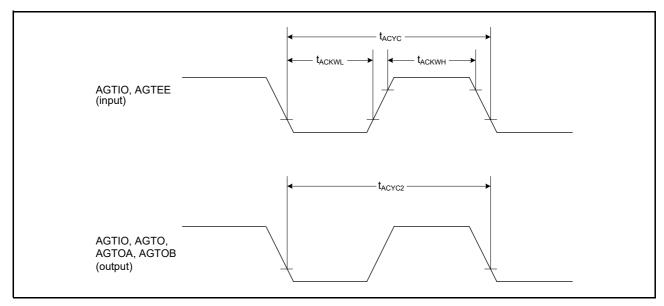


Figure 2.40 AGT input/output timing

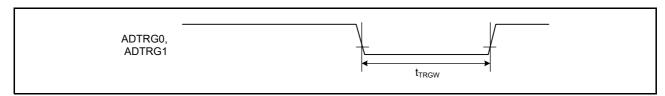


Figure 2.41 ADC12 trigger input timing

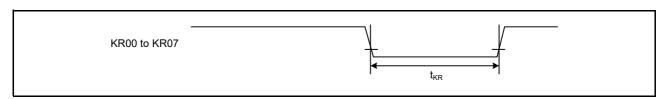


Figure 2.42 Key interrupt input timing

2.3.8 PWM Delay Generation Circuit Timing

Table 2.20 PWM Delay Generation Circuit timing

Parameter	Min	Тур	Max	Unit	Test conditions
Operation frequency	80	-	120	MHz	-
Resolution	-	260	-	ps	PCLKD = 120 MHz
DNL*1	-	±2.0	-	LSB	-

Note 1. This value normalizes the differences between lines in 1-LSB resolution.

2.3.9 CAC Timing

Table 2.21 CAC timing

Parameter			Symbol	Min	Тур	Max	Unit	Test conditions
CAC	CACREF input pulse width	t _{PBcyc} ≤ tcac*2	t _{CACREF}	$4.5 \times t_{cac} + 3 \times t_{PBcyc}$	-	-	ns	-
		t _{PBcyc} > tcac*2		$5 \times t_{cac} + 6.5 \times t_{PBcyc}$	-	-	ns	

Note 1. t_{PBcyc} : PCLKB cycle.

Note 2. t_{cac} : CAC count clock source cycle.

2.3.10 **SCI Timing**

Table 2.22 SCI timing (1)
Conditions: High drive output is selected in the port drive capability bit in the PmnPFS register for the following pins: SCK0 to SCK9. For other pins, middle drive output is selected in the port drive capability bit in the PmnPFS register.

Parameter	Parameter			Min	Max	Unit*1	Test conditions
SCI	Input clock cycle	Asynchronous	t _{Scyc}	4	-	t _{Pcyc}	Figure 2.43
		Clock synchronous		6	-		
	Input clock pulse width	•	t _{SCKW}	0.4	0.6	t _{Scyc}	
	Input clock rise time		t _{SCKr}	-	5	ns	
	Input clock fall time		t _{SCKf}	-	5	ns	
	Output clock cycle	Asynchronous	t _{Scyc}	6	-	t _{Pcyc}	
		Clock synchronous		4	-		
	Output clock pulse width	•	t _{SCKW}	0.4	0.6	t _{Scyc}	
	Output clock rise time		t _{SCKr}	-	5	ns	
	Output clock fall time		t _{SCKf}	-	5	ns	
	Transmit data delay	Clock synchronous	t _{TXD}	-	25	ns	Figure 2.44
	Receive data setup time	Clock synchronous	t _{RXS}	15	-	ns	
	Receive data hold time	Clock synchronous	t _{RXH}	5	-	ns	

Note 1. t_{Pcyc}: PCLKA cycle.

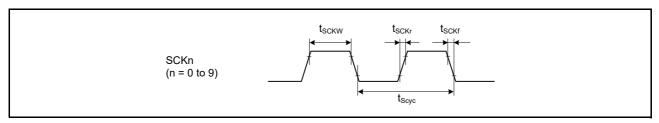


Figure 2.43 SCK clock input/output timing

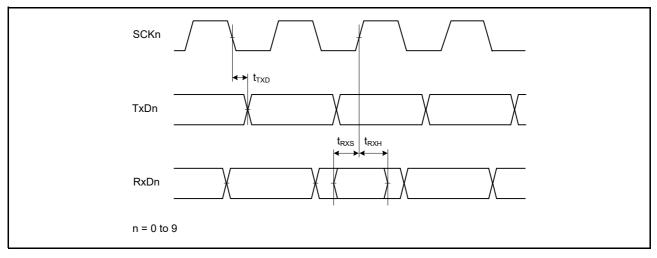


Figure 2.44 SCI input/output timing in clock synchronous mode

Table 2.23 SCI timing (2)
Conditions: High drive output is selected in the port drive capability bit in the PmnPFS register for the following pins: SCK0 to SCK9. For other pins, middle drive output is selected in the port drive capability bit in the PmnPFS register.

Parame	ter	Symbol	Min	Max	Unit	Test conditions
Simple SPI	SCK clock cycle output (master)	t _{SPcyc}	4 (PCLKA ≤ 60 MHz) 8 (PCLKA > 60 MHz)	65536	t _{Pcyc}	Figure 2.45
	SCK clock cycle input (slave)	-	6 (PCLKA ≤ 60 MHz) 12 (PCLKA > 60 MHz)	65536		
	SCK clock high pulse width	t _{SPCKWH}	0.4	0.6	t _{SPcyc}	=
	SCK clock low pulse width	t _{SPCKWL}	0.4	0.6	t _{SPcyc}	=
	SCK clock rise and fall time	t _{SPCKr} , t _{SPCKf}	-	20	ns	=
	Data input setup time	t _{SU}	33.3	-	ns	Figure 2.46 to
	Data input hold time	t _H	33.3	-	ns	Figure 2.49
	SS input setup time	t _{LEAD}	1	-	t _{SPcyc}	
	SS input hold time	t _{LAG}	1	-	t _{SPcyc}	=
	Data output delay	t _{OD}	-	33.3	ns	=
	Data output hold time	t _{OH}	-10	-	ns	=
	Data rise and fall time	t _{Dr} , t _{Df}	-	16.6	ns	=
	SS input rise and fall time	t _{SSLr} , t _{SSLf}	-	16.6	ns	=
	Slave access time	t _{SA}	-	4 (PCLKA ≤ 60 MHz) 8 (PCLKA > 60 MHz)	t _{Pcyc}	Figure 2.49
	Slave output release time	t _{REL}	-	5 (PCLKA ≤ 60 MHz) 10 (PCLKA > 60 MHz)	t _{Pcyc}	

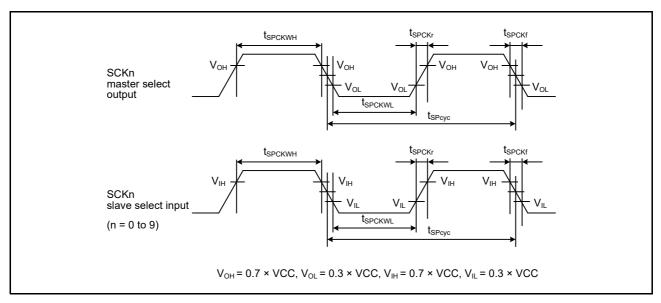


Figure 2.45 SCI simple SPI mode clock timing

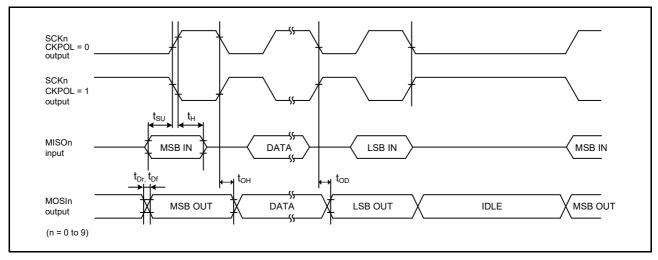


Figure 2.46 SCI simple SPI mode timing for master when CKPH = 1

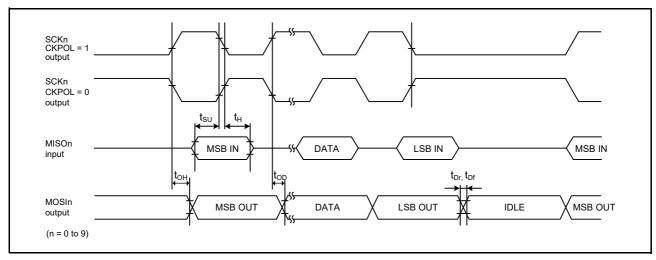


Figure 2.47 SCI simple SPI mode timing for master when CKPH = 0

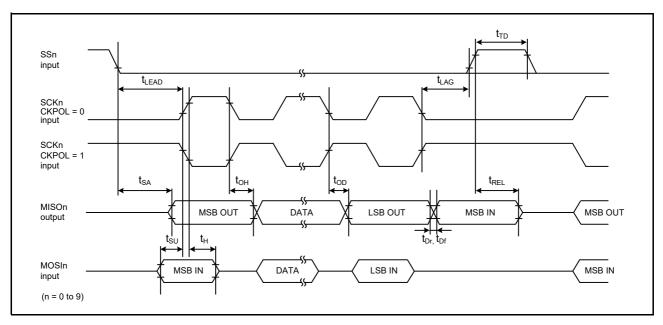


Figure 2.48 SCI simple SPI mode timing for slave when CKPH = 1

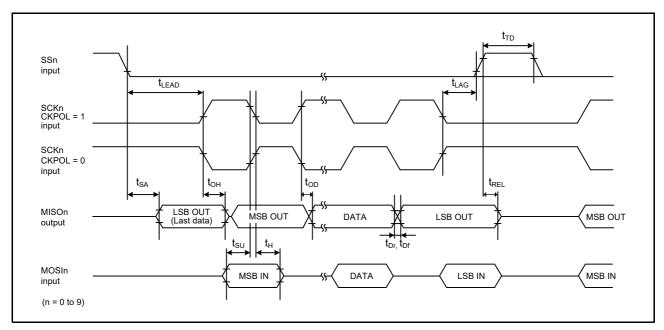


Figure 2.49 SCI simple SPI mode timing for slave when CKPH = 0

Table 2.24 SCI timing (3) (1 of 2)
Conditions: Middle drive output is selected in the port drive capability bit in the PmnPFS register.

Parameter		Symbol	Min	Max	Unit	Test conditions
Simple IIC	SDA input rise time	t _{Sr}	-	1000	ns	Figure 2.50
(Standard mode)	SDA input fall time	t _{Sf}	-	300	ns	
	SDA input spike pulse removal time	t _{SP}	0	4 × t _{IICcyc}	ns	
	Data input setup time	t _{SDAS}	250	-	ns	
	Data input hold time	t _{SDAH}	0	-	ns]
	SCL, SDA capacitive load		-	400	pF	

Table 2.24 SCI timing (3) (2 of 2)
Conditions: Middle drive output is selected in the port drive capability bit in the PmnPFS register.

Parameter		Symbol	Min	Max	Unit	Test conditions
Simple IIC	SDA input rise time	t _{Sr}	-	300	ns	Figure 2.50
(Fast mode)	SDA input fall time	t _{Sf}	-	300	ns]
	SDA input spike pulse removal time	t _{SP}	0	4 × t _{IICcyc}	ns]
	Data input setup time	t _{SDAS}	100	-	ns]
	Data input hold time	t _{SDAH}	0	-	ns]
	SCL, SDA capacitive load	C _{b*} 1	-	400	pF	1

Note: $t_{IIC\,cyc}$: IIC internal reference clock (IIC ϕ) cycle. Note 1. Cb indicates the total capacity of the bus line.

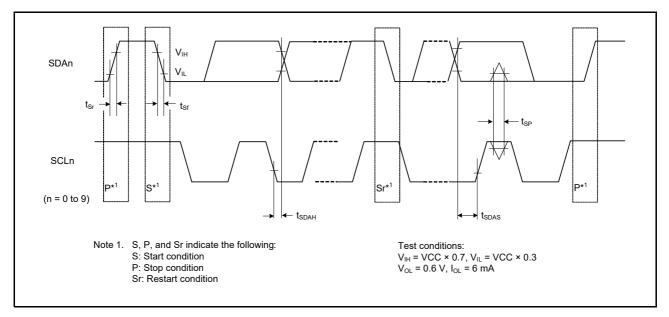


Figure 2.50 SCI simple IIC mode timing

2.3.11 SPI Timing

Table 2.25 SPI timing

Conditions:

For RSPCKA and RSPCKB pins, high drive output is selected with the port drive capability bit in the PmnPFS register.

For other pins, middle drive output is selected in the port drive capability bit in the PmnPFS register.

Param	eter		Symbol	Min	Max	Unit*1	Test conditions*2
SPI	RSPCK clock cycle	Master	t _{SPcyc}	2 (PCLKA ≤ 60 MHz) 4 (PCLKA > 60 MHz)	4096	t _{Pcyc}	Figure 2.51 C = 30 pF
		Slave		4	4096		
	RSPCK clock high pulse width	Master	t _{SPCKWH}	(t _{SPcyc} - t _{SPCKr} - t _{SPCKf}) / 2 - 3	-	ns	
		Slave		2 × t _{Pcyc}	-		
	RSPCK clock low pulse width	Master	t _{SPCKWL}	(t _{SPcyc} - t _{SPCKr} - t _{SPCKf}) / 2 - 3	-	ns	
		Slave		2 × t _{Pcyc}	-		
	RSPCK clock rise and	Master	t _{SPCKr,}	-	5	ns	
	fall time	Slave	t _{SPCKf}	-	1	μs	
	Data input setup time	Master	t _{SU}	4	-	ns	Figure 2.52 to
		Slave		5	-		Figure 2.57 C = 30 pF
	Data input hold time	Master (PCLKA division ratio set to 1/2)	t _{HF}	0	-	ns	. C = 30 pr
		Master (PCLKA division ratio set to a value other than 1/2)	t _H	t _{Pcyc}	-		
		Slave	t _H	20	-		
	SSL setup time	Master	t _{LEAD}	N × t _{SPcyc} - 10*3	N × t _{SPcyc} + 100* ³	ns	
		Slave		6 x t _{Pcyc}	-	ns	
	SSL hold time	Master	t _{LAG}	N × t _{SPcyc} - 10 *4	N × t _{SPcyc} + 100*4	ns	
		Slave		6 x t _{Pcyc}	-	ns	
	Data output delay	Master	t _{OD}	-	6.3	ns	
		Slave		-	20		
	Data output hold time	Master	t _{OH}	0	-	ns	
		Slave		0	-		
	Successive transmission delay	Master	t _{TD}	t _{SPcyc} + 2 × t _{Pcyc}	8 × t _{SPcyc} + 2 × t _{Pcyc}	ns	
		Slave		6 × t _{Pcyc}			
	MOSI and MISO rise	Output	t _{Dr.} t _{Df}	-	5	ns	
	and fall time	Input	1	-	1	μs	
	SSL rise and fall time	Output	t _{SSLr.}	-	5	ns	-
		Input	t _{SSLf}	-	1	μs	
	Slave access time	1	t _{SA}	-	2 x t _{Pcyc} + 28	ns	Figure 2.56 and Figure 2.57
	Slave output release time	e	t _{REL}	-	2 x t _{Pcyc} + 28		C = 30 _P F

Note 1. t_{Pcyc} : PCLKA cycle.

Note 2. Must use pins that have a letter ("_A", "_P") to indicate group membership appended to their name as groups. For the SPI interface, the AC portion of the electrical characteristics is measured for each group.

- Note 3. N is set to an integer from 1 to 8 by the SPCKD register.
- Note 4. N is set to an integer from 1 to 8 by the SSLND register.

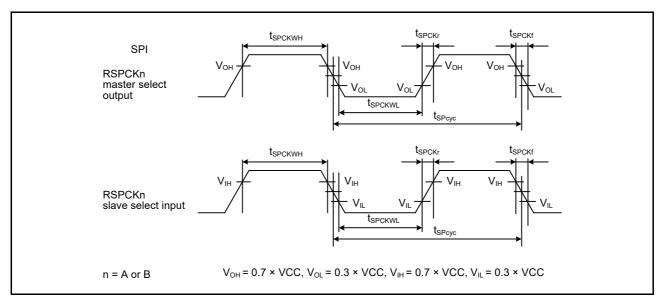


Figure 2.51 SPI clock timing

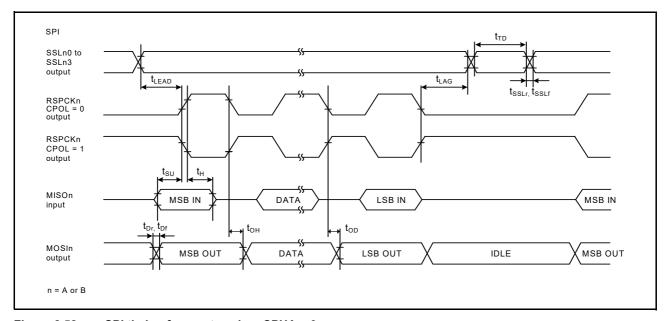


Figure 2.52 SPI timing for master when CPHA = 0

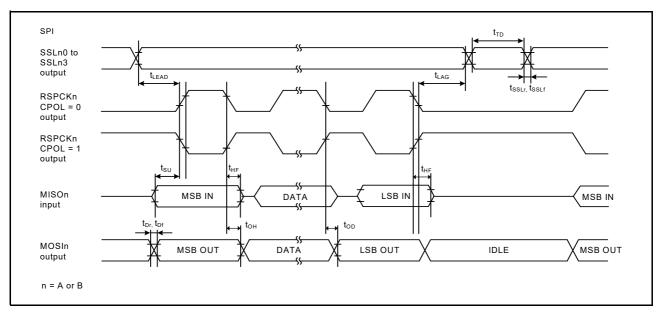


Figure 2.53 SPI timing for master when CPHA = 0 and the bit rate is set to PCLKA/2

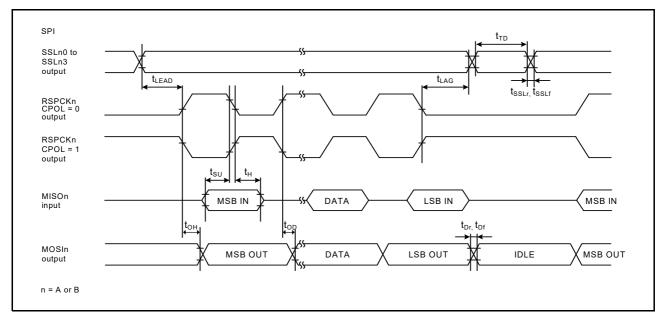


Figure 2.54 SPI timing for master when CPHA = 1

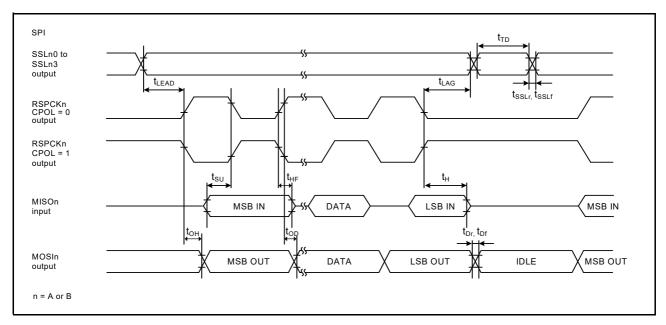


Figure 2.55 RSPI timing for master when CPHA = 1 and the bit rate is set to PCLKA/2

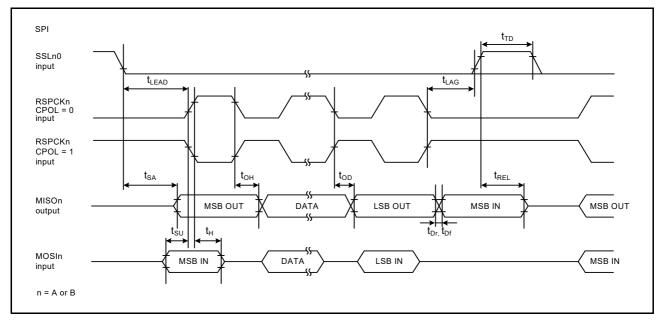


Figure 2.56 SPI timing for slave when CPHA = 0

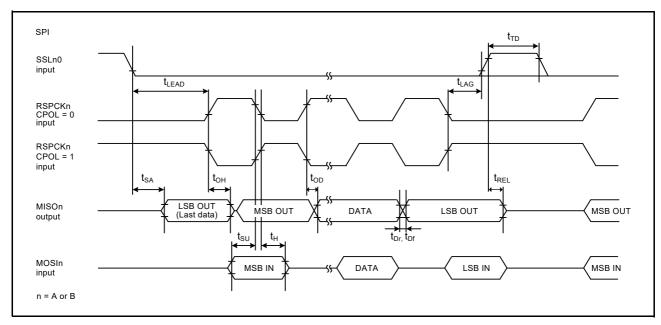


Figure 2.57 SPI timing for slave when CPHA = 1

2.3.12 QSPI Timing

Table 2.26 QSPI timingConditions: High drive output is selected in the port drive capability bit in the PmnPFS register.

Param	Parameter		Min	Max	Unit*1	Test conditions	
QSPI	QSPCK clock cycle	t _{QScyc}	2	48	t _{Pcyc}	Figure 2.58	
	QSPCK clock high pulse width	t _{QSWH}	t _{QScyc} × 0.4	-	ns	7	
	QSPCK clock low pulse width	t _{QSWL}	t _{QScyc} × 0.4	-	ns		
	Data input setup time	t _{Su}	8	-	ns	Figure 2.59	
	Data input hold time	t _{IH}	0	-	ns		
	QSSL setup time	t _{LEAD}	(N+0.5) x t _{Qscyc} - 5 *2	(N+0.5) x t _{Qscyc} +100 *2	ns		
	QSSL hold time	t _{LAG}	(N+0.5) x t _{Qscyc} - 5 *3	(N+0.5) x t _{Qscyc} +100 *3	ns		
	Data output delay	t _{OD}	-	4	ns		
	Data output hold time	t _{OH}	-3.3	-	ns		
	Successive transmission delay	t _{TD}	1	16	t _{QScyc}		

Note 1. t_{Pcyc} : PCLKA cycle.

Note 2. N is set to 0 or 1 in SFMSLD. Note 3. N is set to 0 or 1 in SFMSHD.

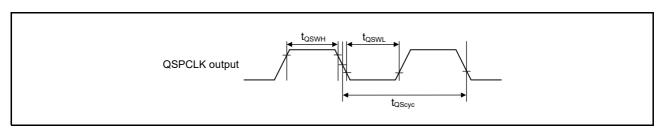


Figure 2.58 QSPI clock timing

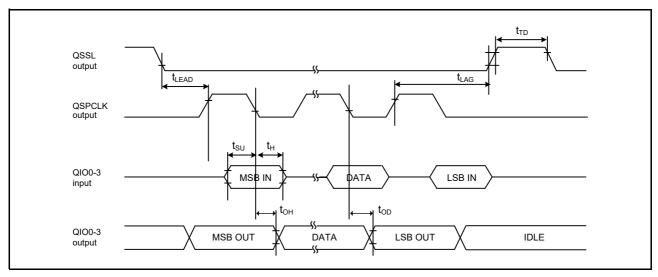


Figure 2.59 Transmit and receive timing

2.3.13 **IIC Timing**

- Table 2.27 IIC timing (1) (1 of 2)
 (1) Conditions: Middle drive output is selected in the port drive capability bit in the PmnPFS register for the following pins: SDA0_B, SCL0_B, SDA1_A, SCL1_A, SDA1_B, SCL1_B.
- (2) The following pins do not require setting: SCL0_A, SDA0_A, SCL2, SDA2.
- (3) Use pins that have a letter appended to their names, for instance "_A" or "_B", to indicate group membership. For the IIC interface, the AC portion of the electrical characteristics is measured for each group.

Parameter		Symbol	Min*1	Max	Unit	Test conditions*3
IIC	SCL input cycle time	t _{SCL}	6 (12) × t _{IICcyc} + 1300	-	ns	Figure 2.60
(Standard mode, SMBus)	SCL input high pulse width	t _{SCLH}	3 (6) × t _{IICcyc} + 300	-	ns	
ICFER.FMPE = 0	SCL input low pulse width	t _{SCLL}	3 (6) × t _{IICcyc} + 300	3 (6) × t _{IICcyc} + 300 -		
	SCL, SDA input rise time	t _{Sr}	-	1000	ns	
	SCL, SDA input fall time	t _{Sf}	-	300	ns	
	SCL, SDA input spike pulse removal time	t _{SP}	0	1 (4) × t _{IICcyc}	ns	
	SDA input bus free time when wakeup function is disabled	t _{BUF}	3 (6) × t _{IICcyc} + 300	- ns		
	SDA input bus free time when wakeup function is enabled	t _{BUF}	3 (6) × t _{IICcyc} + 4 × t _{Pcyc} + 300	-	ns	
	START condition input hold time when wakeup function is disabled	t _{STAH}	t _{IICcyc} + 300	-	ns	
	START condition input hold time when wakeup function is enabled	t _{STAH}	1 (5) × t _{IICcyc} + t _{Pcyc} + 300	-	ns	
	Repeated START condition input setup time	t _{STAS}	1000	-	ns	
	STOP condition input setup time	t _{STOS}	1000	-	ns	
	Data input setup time	t _{SDAS}	t _{IICcyc} + 50	-	ns	
	Data input hold time	t _{SDAH}	0	-	ns	
	SCL, SDA capacitive load	C _b	-	400	pF	

Table 2.27 IIC timing (1) (2 of 2)
(1) Conditions: Middle drive output is selected in the port drive capability bit in the PmnPFS register for the following pins: SDA0_B, SCL0 B, SDA1 A, SCL1 A, SDA1 B, SCL1 B.

- (2) The following pins do not require setting: SCL0_A, SDA0_A, SCL2, SDA2.
- (3) Use pins that have a letter appended to their names, for instance "_A" or "_B", to indicate group membership. For the IIC interface, the AC portion of the electrical characteristics is measured for each group.

Parameter		Symbol	Min*1	Max	Unit	Test conditions*3
IIC	SCL input cycle time	t _{SCL}	6 (12) × t _{IICcyc} + 600	-	ns	Figure 2.60
(Fast mode)	SCL input high pulse width	t _{SCLH}	3 (6) × t _{IICcyc} + 300	-	ns	
	SCL input low pulse width	t _{SCLL}	3 (6) × t _{IICcyc} + 300	-	ns	
	SCL, SDA input rise time	t _{Sr}	20 × (external pullup voltage/5.5V)*2	300	ns	
	SCL, SDA input fall time	t _{Sf}	20 × (external pullup voltage/5.5V)*2	300	ns	
	SCL, SDA input spike pulse removal time	t _{SP}	0	1 (4) × t _{IICcyc}	ns	
	SDA input bus free time when wakeup function is disabled	t _{BUF}	3 (6) × t _{IICcyc} + 300	-	ns	
	SDA input bus free time when wakeup function is enabled	t _{BUF}	3 (6) × t _{IICcyc} + 4 × t _{Pcyc} + 300	-	ns	
	START condition input hold time when wakeup function is disabled	t _{STAH}	t _{IICcyc} + 300	-	ns	
	START condition input hold time when wakeup function is enabled	t _{STAH}	1 (5) × t _{IICcyc} + t _{Pcyc} + 300	-	ns	
	Repeated START condition input setup time	t _{STAS}	300	-	ns	
	STOP condition input setup time	t _{STOS}	300	-	ns	
	Data input setup time	t _{SDAS}	t _{IICcyc} + 50	-	ns	
	Data input hold time	t _{SDAH}	0	-	ns	
	SCL, SDA capacitive load	C _b	-	400	pF	

Note: $t_{\text{IICcyc}}\!\!:$ IIC internal reference clock (IIC ϕ) cycle, $t_{\text{Pcyc}}\!\!:$ PCLKB cycle.

Values in parentheses apply when ICMR3.NF[1:0] is set to 11b while the digital filter is enabled with ICFER.NFE set to 1. Note 1.

Only supported for SCL0_A, SDA0_A, SCL2, and SDA2. Note 2.

Note 3. Must use pins that have a letter ("_A", "_B") to indicate group membership appended to their name as groups. For the IIC interface, the AC portion of the electrical characteristics is measured for each group.

Table 2.28 IIC timing (2)
Setting of the SCL0_A, SDA0_A pins is not required with the port drive capability bit in the PmnPFS register.

Parameter		Symbol	Min*1,*2	Max	Unit	Test conditions	
IIC	SCL input cycle time	t _{SCL}	6 (12) × t _{IICcyc} + 240	-	ns	Figure 2.60	
(Fast-mode+) ICFER.FMPE = 1	SCL input high pulse width	t _{SCLH}	3 (6) × t _{IICcyc} + 120	-	ns		
	SCL input low pulse width	t _{SCLL}	3 (6) × t _{IICcyc} + 120	-	ns		
	SCL, SDA input rise time	t _{Sr}	-	120	ns		
	SCL, SDA input fall time	t _{Sf}	-	120	ns		
	SCL, SDA input spike pulse removal time	t _{SP}	0	1 (4) × t _{IICcyc}	ns		
	SDA input bus free time when wakeup function is disabled	t _{BUF}	3 (6) × t _{IICcyc} + 120	-	ns		
	SDA input bus free time when wakeup function is enabled	t _{BUF}	3 (6) × t _{IICcyc} + 4 × t _{Pcyc} + 120	-	ns		
	Start condition input hold time when wakeup function is disabled	t _{STAH}	t _{IICcyc} + 120	-	ns		
	START condition input hold time when wakeup function is enabled	t _{STAH}	1 (5) × t _{IICcyc} + t _{Pcyc} + 120	-	ns		
	Restart condition input setup time	t _{STAS}	120	-	ns		
	Stop condition input setup time	t _{STOS}	120	-	ns		
	Data input setup time	t _{SDAS}	t _{IICcyc} + 30	-	ns		
	Data input hold time	t _{SDAH}	0	-	ns		
	SCL, SDA capacitive load	C _b	-	550	pF		

Note: t_{IICcyc} : IIC internal reference clock (IIC ϕ) cycle, t_{Pcyc} : PCLKB cycle.

Note 1. Values in parentheses apply when ICMR3.NF[1:0] is set to 11b while the digital filter is enabled with ICFER.NFE set to 1.

Note 2. Cb indicates the total capacity of the bus line.

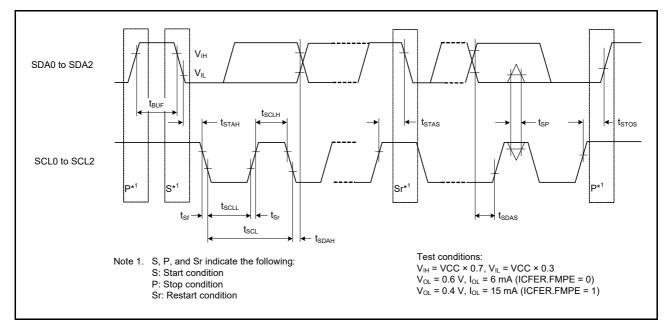


Figure 2.60 I²C bus interface input/output timing

SSIE Timing 2.3.14

- Table 2.29 SSIE timing
 (1) High drive output is selected with the port drive capability bit in the PmnPFS register.
- (2) Use pins that have a letter appended to their names, for instance "_A" or "_B" to indicate group membership. For the SSIE interface, the AC portion of the electrical characteristics is measured for each group.

				Target	specification		
Parameter			Symbol	Min.	Max.	Unit	Comments
SSIBCK	Cycle	Master	t _O	80	-	ns	Figure 2.61
		Slave	t _l	80	-	ns	
	High level/ low level	Master	t _{HC} /t _{LC}	0.35	-	t _O	
		Slave		0.35	-	t _l	
	Rising time/falling time	Master	t _{RC} /t _{FC}	-	0.15	t _O / t _I	
		Slave		-	0.15	t _O / t _I	
SSILRCK/SSIFS,	Input set up time	Master	t _{SR}	12	-	ns	Figure 2.63,
SSITXD0, SSIRXD0, SSIDATA1		Slave		12	-	ns	Figure 2.64
COIDITITI	Input hold time	Master	t _{HR}	8	-	ns	
		Slave		15	-	ns	
	Output delay time	Master	t _{DTR}	-10	5	ns	
		Slave		0	20	ns	Figure 2.63, Figure 2.64
	Output delay time from SSILRCK/SSIFS change	Slave	t _{DTRW}	-	20	ns	Figure 2.65*1
GTIOC1A,	Cycle	•	t _{EXcyc}	20	-	ns	Figure 2.62
AUDIO_CLK	High level/ low level	•		0.4	0.6	t _{EXcyc}	

Note 1. For slave-mode transmission, SSIE has a path, through which the signal input from the SSILRCK/SSIFS pin is used to generate transmit data, and the transmit data is logically output to the SSITXD0 or SSIDATA1 pin.

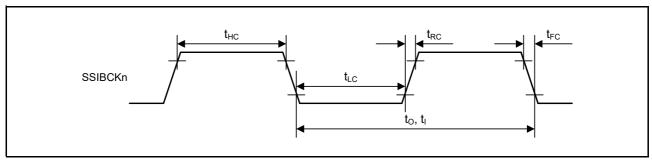


Figure 2.61 SSIE clock input/output timing

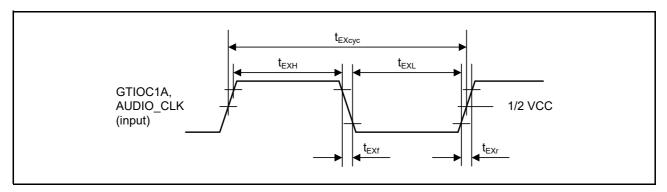


Figure 2.62 Clock input timing

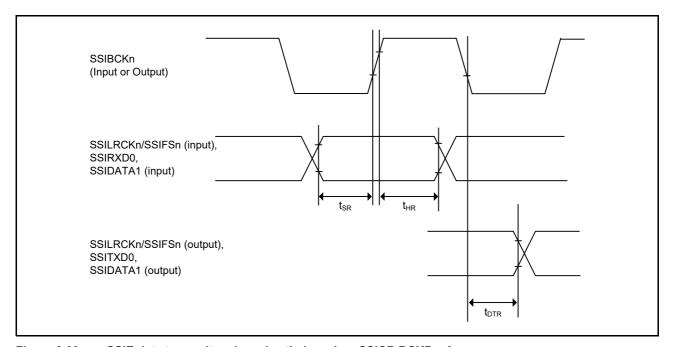
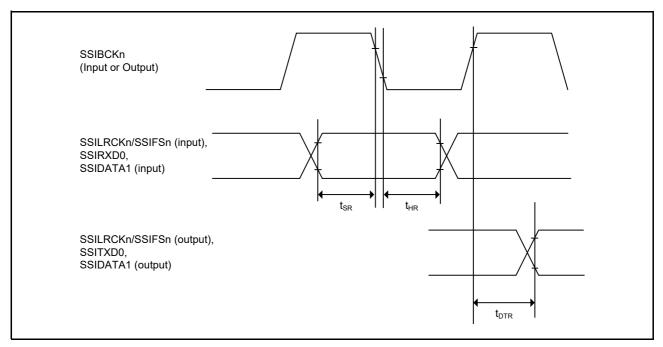


Figure 2.63 SSIE data transmit and receive timing when SSICR.BCKP = 0



SSIE data transmit and receive timing when SSICR.BCKP = 1 Figure 2.64

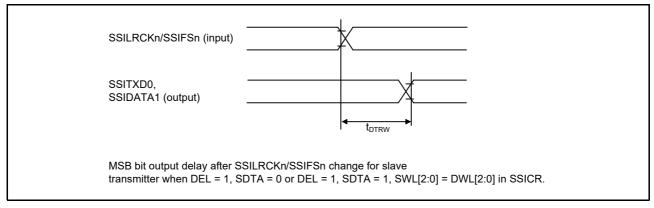


Figure 2.65 SSIE data output delay after SSILRCKn/SSIFSn change

2.3.15 SD/MMC Host Interface Timing

Table 2.30 SD/MMC Host Interface signal timingConditions: High drive output is selected in the port drive capability bit in the PmnPFS register. Clock duty ratio is 50%.

Parameter	Symbol	Min	Max	Unit	Test conditions*1
SDnCLK clock cycle	T _{SDCYC}	20	-	ns	Figure 2.66
SDnCLK clock high pulse width	T _{SDWH}	6.5	-	ns	
SDnCLK clock low pulse width	T _{SDWL}	6.5	-	ns	
SDnCLK clock rise time	T _{SDLH}	-	3	ns	
SDnCLK clock fall time	T _{SDHL}	-	3	ns	
SDnCMD/SDnDATm output data delay	T _{SDODLY}	-6	5	ns	
SDnCMD/SDnDATm input data setup	T _{SDIS}	4	-	ns	
SDnCMD/SDnDATm input data hold	T _{SDIH}	2	-	ns	

Note 1. Must use pins that have a letter ("_A", "_B") to indicate group membership appended to their name as groups. For

the SD/MMC Host interface, the AC portion of the electrical characteristics is measured for each group.

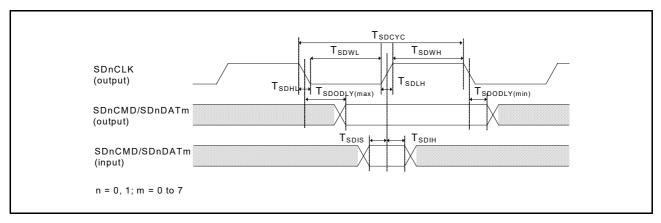


Figure 2.66 SD/MMC Host Interface signal timing

2.3.16 **ETHERC Timing**

 Table 2.31
 ETHERC timing

 Conditions: ETHERC (RMII): Middle drive output is selected in the port drive capability bit in the PmnPFS register for the following pins:
 ET0_MDC, ET0_MDIO.

For other pins, high drive output is selected in the port drive capability bit in the PmnPFS register.

ETHERC (MII): Middle drive output is selected in the port drive capability bit in the PmnPFS register.

Parameter		Symbol	Min	Max	Unit	Test conditions*3	
ETHERC	REF50CK cycle time	T _{ck}	20	-	ns	Figure 2.67 to	
(RMII)	REF50CK frequency, typical 50 MHz	-	-	50 + 100 ppm	MHz	Figure 2.70	
	REF50CK duty	-	35	65	%		
	REF50CK rise/fall time	T _{ckr/ckf}	0.5	3.5	ns		
	RMII0_xxxx*1 output delay	T _{co}	2.5	12.0	ns		
	RMII0_xxxx*2 setup time	T _{su}	3	-	ns		
	RMII0_xxxx*2 hold time	T _{hd}	1	-	ns		
	RMII0_xxxx*1, *2 rise/fall time	T_r/T_f	0.5	4	ns		
	ET0_WOL output delay	t _{WOLd}	1	23.5	ns	Figure 2.71	
ETHERC	ET0_TX_CLK cycle time	t _{Tcyc}	40	-	ns	-	
(MII)	ET0_TX_EN output delay	t _{TENd}	1	20	ns	Figure 2.72	
	ET0_ETXD0 to ET0_ETXD3 output delay	t _{MTDd}	1	20	ns		
	ET0_CRS setup time	t _{CRSs}	10	-	ns		
	ET0_CRS hold time	t _{CRSh}	10	-	ns		
	ET0_COL setup time	t _{COLs}	10	-	ns	Figure 2.73	
	ET0_COL hold time	t _{COLh}	10	-	ns		
	ET0_RX_CLK cycle time	t _{TRcyc}	40	-	ns	-	
	ET0_RX_DV setup time	t _{RDVs}	10	-	ns	Figure 2.74	
	ET0_RX_DV hold time	t _{RDVh}	10	-	ns		
	ET0_ERXD0 to ET0_ERXD3 setup time	t _{MRDs}	10	-	ns		
	ET0_ERXD0 to ET0_ERXD3 hold time	t _{MRDh}	10	-	ns		
	ET0_RX_ER setup time	t _{RERs}	10	-	ns	Figure 2.75	
	ET0_RX_ER hold time	t _{RESh}	10	-	ns	1	
	ET0_WOL output delay	t _{WOLd}	1	23.5	ns	Figure 2.76	

Note 1. RMII0_TXD_EN, RMII0_TXD1, RMII0_TXD0.

Note 2. RMIIO_CRS_DV, RMIIO_RXD1, RMIIO_RXD0, RMIIO_RX_ER.

Note 3. The following pins, must use pins that have a letter ("_A", "_B") to indicate group membership appended to their name as groups. For the ETHERC (RMII) Host interface, the AC portion of the electrical characteristics is measured for each group. REF50CK0_A, REF50CK0_B, RMII0_xxxx_A, RMII0_xxxx_B

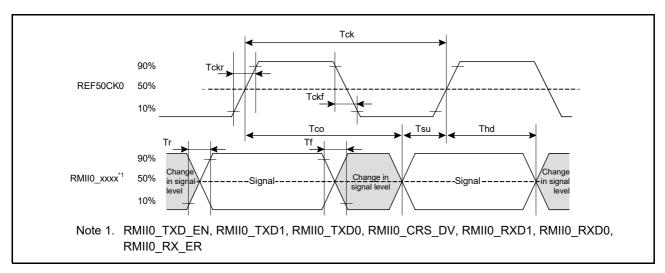


Figure 2.67 REF50CK0 and RMII signal timing

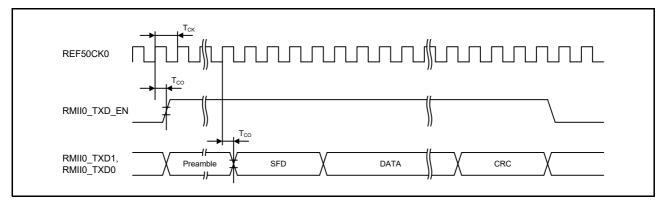


Figure 2.68 RMII transmission timing

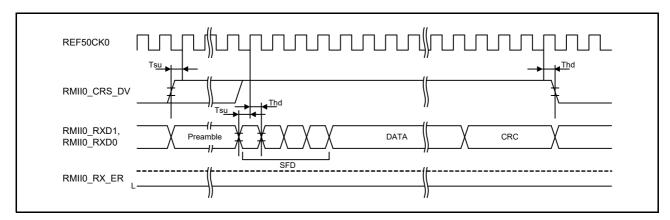


Figure 2.69 RMII reception timing in normal operation

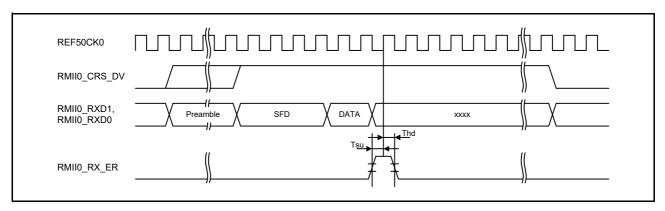


Figure 2.70 RMII reception timing when an error occurs

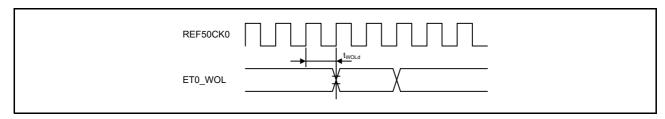


Figure 2.71 WOL output timing for RMII

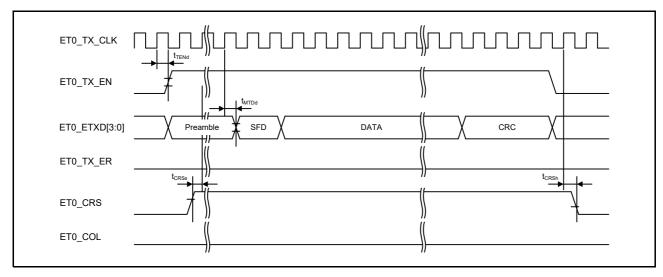


Figure 2.72 MII transmission timing in normal operation

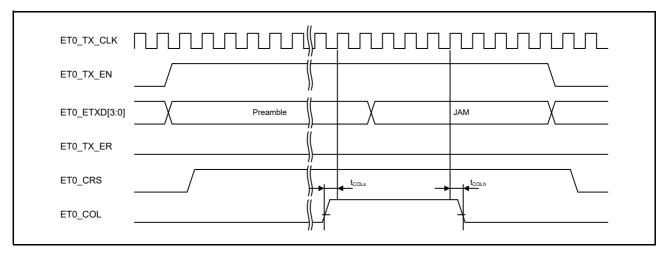


Figure 2.73 MII transmission timing when a conflict occurs

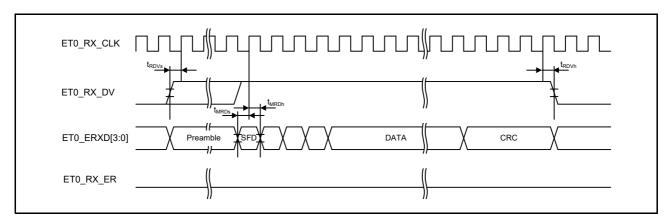


Figure 2.74 MII reception timing in normal operation

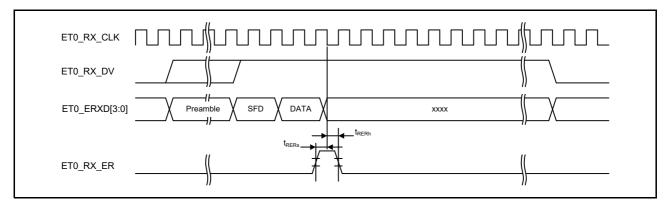


Figure 2.75 MII reception timing when an error occurs

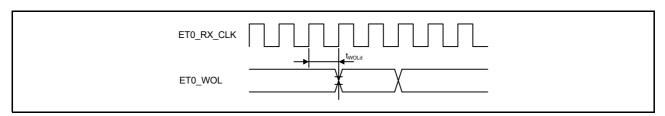


Figure 2.76 WOL output timing for MII

PDC Timing 2.3.17

Table 2.32PDC timingConditions: Middle drive output is selected in the port drive capability bit in the PmnPFS register.Output load conditions: $V_{OH} = VCC \times 0.5$, $V_{OL} = VCC \times 0.5$, C = 30 pF

Param	Parameter		Min	Max	Unit	Test conditions	
PDC	PIXCLK input cycle time	t _{PIXcyc}	37	-	ns	Figure 2.77	
	PIXCLK input high pulse width	t _{PIXH}	10	-	ns		
	PIXCLK input low pulse width	t _{PIXL}	10	-	ns	1	
	PIXCLK rise time	t _{PIXr}	-	5	ns	1	
	PIXCLK fall time	t _{PIXf}	-	5	ns	1	
	PCKO output cycle time	t _{PCKcyc}	2 × t _{PBcyc}	-	ns	Figure 2.78	
	PCKO output high pulse width	t _{PCKH}	(t _{PCKcyc} - t _{PCKr} - t _{PCKf})/2 - 3	-	ns	1	
	PCKO output low pulse width	t _{PCKL}	(t _{PCKcyc} - t _{PCKr} - t _{PCKf})/2 - 3	-	ns		
	PCKO rise time	t _{PCKr}	-	5	ns	1	
	PCKO fall time	t _{PCKf}	-	5	ns	1	
	VSYNV/HSYNC input setup time	t _{SYNCS}	10	-	ns	Figure 2.79	
	VSYNV/HSYNC input hold time	t _{SYNCH}	5	-	ns		
	PIXD input setup time	IXD input setup time t _{PIXDS}		- ns	ns	1	
	PIXD input hold time	t _{PIXDH}	5	-	ns		

Note 1. t_{PBcyc} : PCLKB cycle.

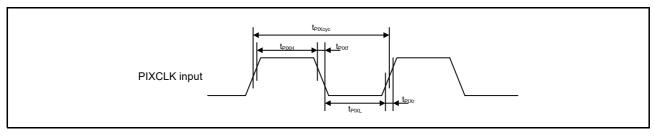


Figure 2.77 **PDC** input clock timing

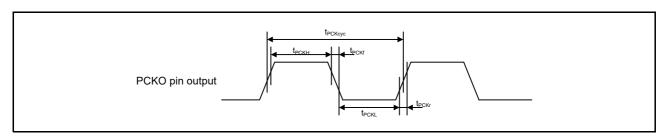


Figure 2.78 **PDC** output clock timing

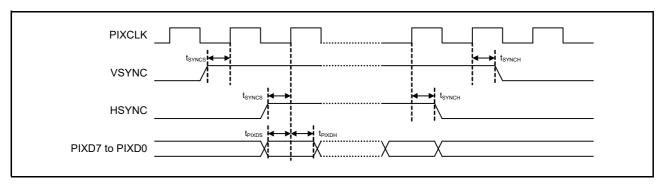


Figure 2.79 PDC AC timing

2.3.18 GLCDC Timing

Table 2.33 GLCDC timing

Conditions:

LCD CLK: High drive output is selected in the port drive capability bit in the PmnPFS register.

LCD_DATA: Middle drive output is selected in the port drive capability bit in the PmnPFS register.

Parameter		Symbol	Min	Тур	Max	Unit	Test conditions
LCD_EXTCLK input clock free	uency	t _{Ecyc}	-	-	60*1	MHz	Figure 2.80
LCD_EXTCLK input clock low pulse width		t _{WL}	0.45	-	0.55	t _{Ecyc}	
LCD_EXTCLK input clock high pulse width		t _{WH}	0.45	-	0.55		
LCD_CLK output clock frequency		t _{Lcyc}	-	-	60* ¹	MHz	Figure 2.81
LCD_CLK output clock low pu	lse width	t _{LOL}	0.4	-	0.6	t _{Lcyc}	Figure 2.81
LCD_CLK output clock high pulse width		t _{LOH}	0.4	-	0.6	t _{Lcyc}	Figure 2.81
LCD data output delay timing	_A or _B combinations*2	t _{DD}	-3.5	-	4	ns	Figure 2.82
	_A and _B combinations*3		-5.0	-	5.5		

Note 1. Parallel RGB888, 666,565: Maximum 54 MHz

Serial RGB888: Maximum 60 MHz (4x speed)

Note 2. Use pins that have a letter appended to their names, for instance, "_A" or "_B", to indicate

Note 3. Pins of group "_A" and "_B" combinations are used.

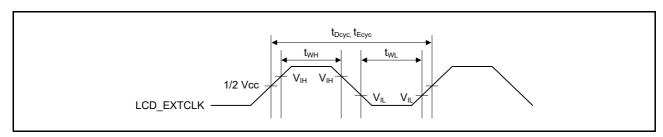


Figure 2.80 LCD_EXTCLK clock input timing

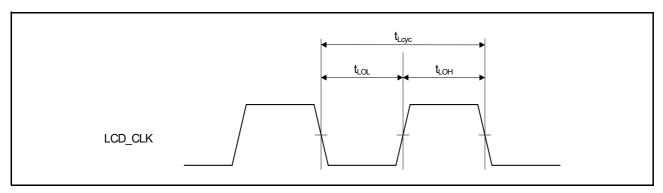


Figure 2.81 LCD_CLK clock output timing

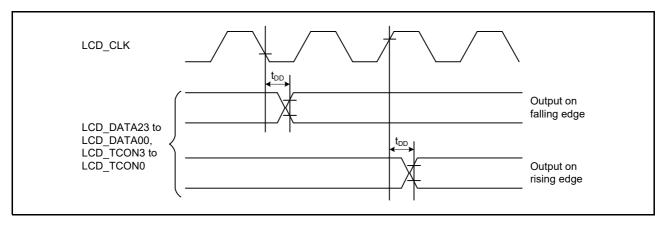


Figure 2.82 Display output timing

2.4 USB Characteristics

2.4.1 USBHS Timing

Table 2.34 USBHS low-speed characteristics for host only (USBHS_DP and USBHS_DM pin characteristics) Conditions: USBHS_RREF = $2.2 \text{ k}\Omega \pm 1\%$, USBMCLK = 12/20/24 MHz, UCLK = 48 MHz

Parameter		Symbol	Min	Тур	Max	Unit	Test conditions		
Input	Input high voltage	V _{IH}	2.0	-	-	V	-	-	
characteristics	Input low voltage	V _{IL}	-	-	0.8	V	-	-	
	Differential input sensitivity	V _{DI}	0.2	-	-	V	USBHS_DP - USBHS_DM	-	
	Differential common-mode range	V _{CM}	0.8	-	2.5	V	-	-	
Output	Output high voltage	V _{OH}	2.8	-	3.6	V	I _{OH} = -200 μA	-	
characteristics	Output low voltage	V _{OL}	0.0	-	0.3	V	I _{OL} = 2 mA	-	
	Cross-over voltage	V _{CRS}	1.3	-	2.0	V	-	Figure 2.83,	
	Rise time	t _{LR}	75	-	300	ns	-	Figure 2.84	
	Fall time	t _{LF}	75	-	300	ns	-		
	Rise/fall time ratio	t _{LR} / t _{LF}	80	-	125	%	t _{LR} / t _{LF}	-	
Pull-up, Pull-down characteristics	USBHS_DP and USBHS_DM pull-down resistors (Host)	R _{pd}	14.25	-	24.80	kΩ	-	•	

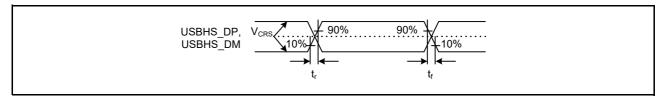


Figure 2.83 USBHS_DP and USBHS_DM output timing in low-speed mode

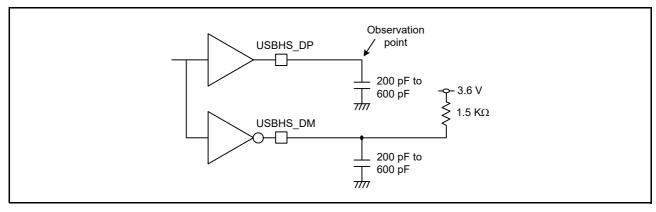


Figure 2.84 Test circuit in low-speed mode

 $\begin{tabular}{ll} \textbf{Table 2.35} & \textbf{USBHS full-speed characteristics (USBHS_DP and USBHS_DM pin characteristics)} \\ \textbf{Conditions: USBHS_RREF = 2.2 k} & \textbf{L} \\ \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} \\ \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} \\ \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} \\ \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} \\ \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} \\ \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} \\ \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} \\ \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} \\ \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} \\ \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} \\ \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} \\ \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} \\ \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} \\ \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} \\ \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} \\ \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} \\ \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} \\ \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} \\ \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} \\ \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} \\ \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} \\ \textbf{L} & \textbf{L} & \textbf{L} \\ \textbf{L} & \textbf{L} & \textbf{L} \\ \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} \\ \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} \\ \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} \\ \textbf{L} & \textbf{L} & \textbf{L} \\ \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} \\ \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} \\ \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} \\ \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} & \textbf{L} \\$

Parameter		Symbol	Min	Тур	Max	Unit	Test condition	s	
Input	Input high voltage	V _{IH}	2.0	-	-	V	-	-	
characteristics	Input low voltage	V _{IL}	-	-	0.8	V	-	-	
	Differential input sensitivity	V _{DI}	0.2	-	-	٧	USBHS_DP - USBHS_DM	-	
	Differential common-mode range	V _{CM}	0.8	-	2.5	٧	-	-	
Output characteristics	Output high voltage	V _{OH}	2.8	-	3.6	V	I _{OH} = -200 μA	-	
	Output low voltage	V _{OL}	0.0	-	0.3	V	I _{OL} = 2 mA	-	
	Cross-over voltage	V _{CRS}	1.3	-	2.0	V	-	Figure 2.85,	
	Rise time	t _{LR}	4	-	20	ns	-	Figure 2.86	
	Fall time	t _{LF}	4	-	20	ns	-		
	Rise/fall time ratio	t _{LR} / t _{LF}	90	-	111.11	%	t _{FR} / t _{FF}	-	
	Output resistance	Z _{DRV}	40.5	-	49.5	Ω	Rs Not used (PHYSET.REPSEL[1:0] = 01b and PHYSET. HSEB = 0)		
DC	USBHS_DM pull-up resistor	R _{pu}	0.900	-	1.575	kΩ	During idle state	Э	
characteristics	(device)		1.425	-	3.090	kΩ	During transmis reception	sion and	
	USBHS_DP/USBHS_DM pull-down resistor (host)	R _{pd}	14.25	-	24.80	kΩ	-		

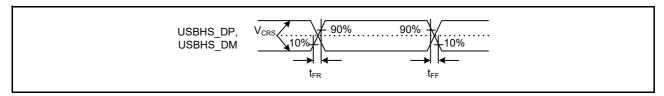


Figure 2.85 USBHS_DP and USBHS_DM output timing in full-speed mode

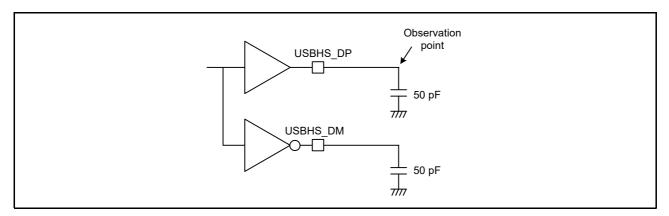


Figure 2.86 Test circuit in full-speed mode

Table 2.36 USBHS high-speed characteristics (USBHS_DP and USBHS_DM pin characteristics) Conditions: USBHS_RREF = $2.2 \text{ k}\Omega \pm 1\%$, USBMCLK = 12/20/24 MHz

Parameter		Symbol	Min	Тур	Max	Unit	Test conditions
Input	Squelch detect sensitivity	V_{HSSQ}	100	-	150	mV	Figure 2.87
characteristics	Disconnect detect sensitivity	V _{HSDSC}	525	-	625	mV	Figure 2.88
	Common-mode voltage	V _{HSCM}	-50	-	500	mV	-
Output	Idle state	V _{HSOI}	-10.0	-	10	mV	-
characteristics	Output high voltage	V _{HSOH}	360	-	440	mV	
	Output low voltage	V _{HSOL}	-10.0	-	10	mV	
	Chirp J output voltage (difference)	V _{CHIRPJ}	700	-	1100	mV	
	Chirp K output voltage (difference)	V _{CHIRPK}	-900	-	-500	mV	
AC	Rise time	t _{HSR}	500	-	-	ps	Figure 2.89
characteristics	Fall time	t _{HSF}	500	-	-	ps	
	Output resistance	Z _{HSDRV}	40.5	-	49.5	Ω	-

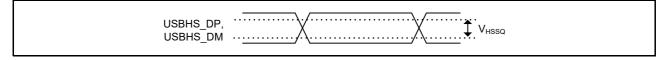


Figure 2.87 USBHS_DP and USBHS_DM squelch detect sensitivity in high-speed mode

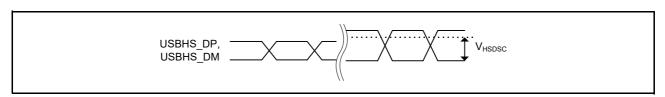


Figure 2.88 USBHS_DP and USBHS_DM disconnect detect sensitivity in high-speed mode

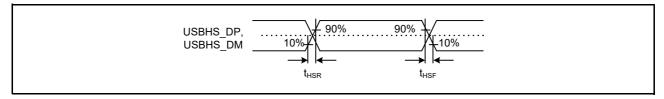


Figure 2.89 USBHS_DP and USBHS_DM output timing in high-speed mode

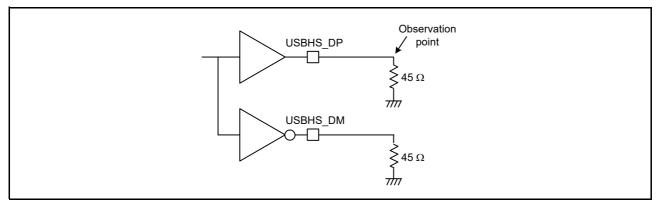


Figure 2.90 Test circuit in high-speed mode

Table 2.37 USBHS high-speed characteristics (USBHS_DP and USBHS_DM pin characteristics) Conditions: USBHS_RREF = $2.2 \text{ k}\Omega \pm 1\%$, USBMCLK = 12/20/24 MHz

Parameter		Symbol	Min	Max	Unit	Test conditions
Battery Charging	D+ sink current	I _{DP_SINK}	25	175	μΑ	-
Specification	D- sink current	I _{DM_SINK}	25	175	μΑ	-
	DCD source current	I _{DP_SRC}	7	13	μΑ	-
	Data detection voltage	V _{DAT_REF}	0.25	0.4	V	-
	D+ source voltage	V _{DP_SRC}	0.5	0.7	V	Output current = 250 μA
	D- source voltage	V _{DM_SRC}	0.5	0.7	V	Output current = 250 μA

2.4.2 USBFS Timing

Table 2.38 USBFS low-speed characteristics for host only (USB_DP and USB_DM pin characteristics) (1 of 2) Conditions: $VCC = AVCC0 = VCC_USB = VBATT = 3.0$ to 3.6V, $2.7 \le VREFH0/VREFH \le AVCC0$, $VCC_USBHS = AVCC_USBHS = 3.0$ to 3.6V, UCLK = 48 MHz

Parameter		Symbol	Min	Тур	Max	Unit	Test conditions
Input	Input high voltage	V _{IH}	2.0	-	-	V	-
characteristics	Input low voltage	V _{IL}	-	-	0.8	V	-
	Differential input sensitivity	V _{DI}	0.2	-	-	V	USB_DP - USB_DM
	Differential common-mode range	V _{CM}	0.8	-	2.5	V	-
Output	Output high voltage	V _{OH}	2.8	-	3.6	V	I _{OH} = -200 μA
characteristics	Output low voltage	V _{OL}	0.0	-	0.3	V	I _{OL} = 2 mA
	Cross-over voltage	V _{CRS}	1.3	-	2.0	V	Figure 2.91
	Rise time	t _{LR}	75	-	300	ns	
	Fall time	t _{LF}	75	-	300	ns	
	Rise/fall time ratio	t _{LR} / t _{LF}	80	-	125	%	t _{LR} / t _{LF}

Table 2.38 USBFS low-speed characteristics for host only (USB_DP and USB_DM pin characteristics) (2 of 2) Conditions: VCC = AVCC0 = VCC_USB = VBATT = 3.0 to 3.6V, 2.7 ≤ VREFH0/VREFH ≤ AVCC0, VCC_USBHS = AVCC_USBHS = 3.0 to 3.6 V, UCLK = 48 MHz

Parameter		Symbol	Min	Тур	Max	Unit	Test conditions
Pull-up and pull- down characteristics	USB_DP and USB_DM pull- down resistance in host controller mode	R _{pd}	14.25	-	24.80	kΩ	-

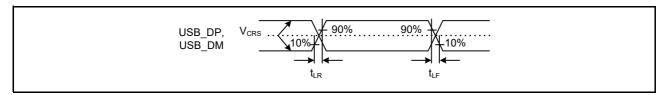


Figure 2.91 USB_DP and USB_DM output timing in low-speed mode

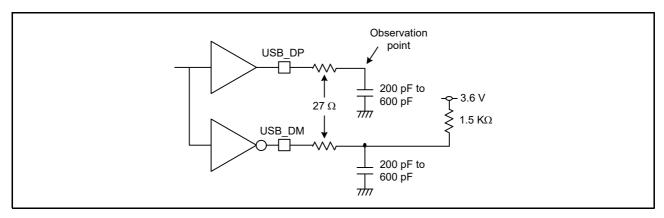


Figure 2.92 Test circuit in low-speed mode

Table 2.39 USBFS full-speed characteristics (USB_DP and USB_DM pin characteristics)
Conditions: VCC = AVCC0 = VCC_USB = VBATT = 3.0 to 3.6 V, 2.7 ≤ VREFH0/VREFH ≤ AVCC0, VCC_USBHS = AVCC_USBHS = 3.0 to 3.6 V, UCLK = 48 MHz

Parameter		Symbol	Min	Тур	Max	Unit	Test conditions
Input	Input high voltage	V _{IH}	2.0	-	-	V	-
characteristics	Input low voltage	V _{IL}	-	-	0.8	V	-
	Differential input sensitivity	V _{DI}	0.2	-	-	V	USB_DP - USB_DM
	Differential common-mode range	V _{CM}	0.8	-	2.5	V	-
Output	Output high voltage	V _{OH}	2.8	-	3.6	V	I _{OH} = -200 μA
characteristics	Output low voltage	V _{OL}	0.0	-	0.3	V	I _{OL} = 2 mA
	Cross-over voltage	V _{CRS}	1.3	-	2.0	V	Figure 2.93
	Rise time	t _{LR}	4	-	20	ns	
	Fall time	t _{LF}	4	-	20	ns	
	Rise/fall time ratio	t _{LR} / t _{LF}	90	-	111.11	%	t _{FR} / t _{FF}
	Output resistance	Z _{DRV}	28	-	44	Ω	USBFS: Rs = 27 Ω included
Pull-up and pull-	DM pull-up resistance in	R _{pu}	0.900	-	1.575	kΩ	During idle state
down characteristics	device controller mode		1.425	-	3.090	kΩ	During transmission and reception
	USB_DP and USB_DM pull- down resistance in host controller mode	R _{pd}	14.25	-	24.80	kΩ	-

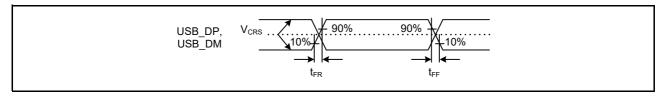


Figure 2.93 USB_DP and USB_DM output timing in full-speed mode

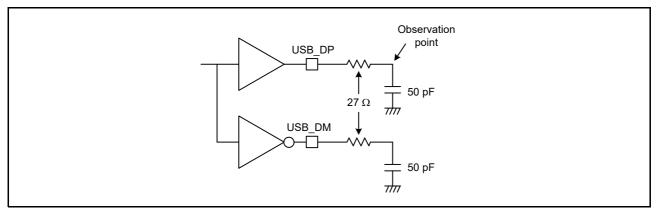


Figure 2.94 Test circuit in full-speed mode

2.5 ADC12 Characteristics

Table 2.40 A/D conversion characteristics for unit 0 (1 of 2) Conditions: PCLKC = 1 to 60 MHz

Parameter			Min	Тур	Max	Unit	Test conditions
Frequency			1	-	60	MHz	-
Analog input capacita	ance		-	-	30	pF	-
Quantization error		-	±0.5	-	LSB	-	
Resolution			-	-	12	Bits	-
Channel-dedicated sample-and-hold circuits in use (AN000 to AN002)	Conversion time*1 (operation at PCLKC = 60 MHz) Permissible signal source impedance Max. = 1 kΩ		1.06 (0.4 + 0.25)*2	-	-	μs	Sampling of channel-dedicated sample-and-hold circuits in 24 states Sampling in 15 states
Offset error		-	±1.5	±3.5	LSB	AN000 to AN002 = 0.25 V	
	Full-scale error		-	±1.5	±3.5	LSB	AN000 to AN002 = VREFH0- 0.25 V
	Absolute accuracy	Absolute accuracy		±2.5	±5.5	LSB	-
	DNL differential nonli	nearity error	-	±1.0	±2.0	LSB	-
	INL integral nonlinear	rity error	-	±1.5	±3.0	LSB	-
	Holding characteristic circuits	cs of sample-and hold	-	-	20	μs	-
	Dynamic range		0.25	-	VREFH 0 - 0.25	V	-
sample-and-hold (operation at source imp		Permissible signal source impedance Max. = 1 kΩ	0.48 (0.267)*2	-	-	μs	Sampling in 16 states
(AN000 to AN002)	Offset error Full-scale error Absolute accuracy		-	±1.0	±2.5	LSB	-
			-	±1.0	±2.5	LSB	-
			-	±2.0	±4.5	LSB	-
	DNL differential nonli	nearity error	-	±0.5	±1.5	LSB	-
	INL integral nonlinear	rity error	-	±1.0	±2.5	LSB	-

Table 2.40 A/D conversion characteristics for unit 0 (2 of 2) Conditions: PCLKC = 1 to 60 MHz

Parameter			Min	Тур	Max	Unit	Test conditions
High-precision channels (AN003 to AN007)	Conversion time*1 (operation at PCLKC = 60 MHz) Permissible signal source impedance Max. = 1 kΩ		0.48 (0.267)*2	-	-	μs	Sampling in 16 states
		Max. = 400 Ω	0.40 (0.183)*2	-	-	μs	Sampling in 11 states VCC = AVCC0 = 3.0 to 3.6 V 3.0 V ≤ VREFH0 ≤ AVCC0
	Offset error		-	±1.0	±2.5	LSB	-
	Full-scale error		-	±1.0	±2.5	LSB	-
	Absolute accuracy		-	±2.0	±4.5	LSB	-
	DNL differential nonlinearity error		-	±0.5	±1.5	LSB	-
	INL integral nonlinea	rity error	-	±1.0	±2.5	LSB	-
Normal-precision channels (AN016 to AN020)	Conversion time*1 (Operation at PCLKC = 60 MHz)	Permissible signal source impedance Max. = 1 kΩ	0.88 (0.667)*2	-	-	μs	Sampling in 40 states
	Offset error	1	-	±1.0	±5.5	LSB	-
	Full-scale error		-	±1.0	±5.5	LSB	-
	Absolute accuracy	Absolute accuracy		±2.0	±7.5	LSB	-
	DNL differential nonl	inearity error	-	±0.5	±4.5	LSB	-
	INL integral nonlinea	rity error	-	±1.0	±5.5	LSB	-

Note: These specification values apply when there is no access to the external bus during A/D conversion. If access occurs during A/D conversion, values might not fall within the indicated ranges.

The use of ports 0 as digital outputs is not allowed when the 12-Bit A/D converter is used.

The characteristics apply when AVCC0, AVSS0, VREFH0, VREFH, VREFL0, VREFL, and 12-bit A/D converter input voltage is stable.

The conversion time includes the sampling and comparison times. The number of sampling states is indicated for the test Note 1. conditions.

Note 2. Values in parentheses indicate the sampling time.

Table 2.41 A/D conversion characteristics for unit 1 (1 of 2)

Conditions: PCLKC = 1 to 60 MHz

Parameter			Min	Тур	Max	Unit	Test conditions
Frequency			1	-	60	MHz	-
Analog input capacitance			-	-	30	pF	-
Quantization error			-	±0.5	-	LSB	-
Resolution			-	-	12	Bits	-
		source impedance	1.06 (0.4 + 0.25)*2	-	-	μs	Sampling of channel- dedicated sample-and-hold circuits in 24 states Sampling in 15 states
	Offset error		-	±1.5	±3.5	LSB	AN100 to AN102 = 0.25 V
	Full-scale error		-	±1.5	±3.5	LSB	AN100 to AN102 = VREFH - 0.25 V
	Absolute accuracy		-	±2.5	±5.5	LSB	-
	DNL differential nonli	nearity error	-	±1.0	±2.0	LSB	-
INL integral nonlinearity error Holding characteristics of sample-and hold circuits		rity error	-	±1.5	±3.0	LSB	-
		-	-	20	μs	-	
	Dynamic range		0.25	-	VREFH - 0.25	V	-

Table 2.41 A/D conversion characteristics for unit 1 (2 of 2) Conditions: PCLKC = 1 to 60 MHz

Parameter			Min	Тур	Max	Unit	Test conditions
Channel-dedicated sample-and-hold circuits not in use	Conversion time*1 (Operation at PCLKC = 60 MHz)	Permissible signal source impedance Max. = 1 kΩ	0.48 (0.267)* ²	-	-	μs	Sampling in 16 states
(AN100 to AN102)	Offset error		-	±1.0	±2.5	LSB	-
	Full-scale error		-	±1.0	±2.5	LSB	-
	Absolute accuracy		-	±2.0	±4.5	LSB	-
	DNL differential nonli	nearity error	-	±0.5	±1.5	LSB	-
	INL integral nonlinear	rity error	-	±1.0	±2.5	LSB	-
High-precision channels (AN103, AN105 to AN107)	Conversion time*1 (Operation at PCLKC = 60 MHz)	Permissible signal source impedance Max. = 1 kΩ	0.48 (0.267)* ²	-	-	μs	Sampling in 16 states
		Max. = 400 Ω	0.40 (0.183)*2	-	-	μs	Sampling in 11 states VCC = AVCC0 = 3.0 to 3.6 V 3.0 V ≤ VREFH ≤ AVCC0
	Offset error		-	±1.0	±2.5	LSB	-
	Full-scale error		-	±1.0	±2.5	LSB	-
	Absolute accuracy	Absolute accuracy		±2.0	±4.5	LSB	-
	DNL differential nonli	nearity error	-	±0.5	±1.5	LSB	-
	INL integral nonlinear	rity error	-	±1.0	±2.5	LSB	-
Normal-precision channels (AN116 to AN119)	Conversion time*1 (Operation at PCLKC = 60 MHz)	Permissible signal source impedance Max. = 1 kΩ	0.88 (0.667)* ²	-	-	μs	Sampling in 40 states
	Offset error		-	±1.0	±5.5	LSB	-
	Full-scale error		-	±1.0	±5.5	LSB	-
	Absolute accuracy		-	±2.0	±7.5	LSB	-
	DNL differential nonli	nearity error	-	±0.5	±4.5	LSB	-
	INL integral nonlinear	rity error	-	±1.0	±5.5	LSB	-

Note: These specification values apply when there is no access to the external bus during A/D conversion. If access occurs during A/D conversion, values might not fall within the indicated ranges.

The use of ports 0 as digital outputs is not allowed when the 12-Bit A/D converter is used.

The characteristics apply when AVCC0, AVSS0, VREFH0, VREFH, VREFL0, VREFL, and 12-bit A/D converter input voltage is stable.

Note 1. The conversion time includes the sampling and comparison times. The number of sampling states is indicated for the test conditions.

Note 2. Values in parentheses indicate the sampling time.

A/D conversion characteristics for simultaneous using of channel-dedicated sample-and-hold circuits in unit0 and unit1 **Table 2.42**

Conditions: PCLKC = 30/60 MHz

Parameter		Min	Тур	Max	Test conditions
Channel-dedicated sample-and-hold circuits in use	Offset error	-	±1.5	±5.0	• PCLKC = 60 MHz
with continious sampling function enabled (AN000 to AN002)	Full-scale error	-	±2.5	±5.0	Sampling in 15 states
(144000 10744002)	Absolute accuracy	-	±4.0	±8.0	
Channel-dedicated sample-and-hold circuits in use with continious sampling function enabled (AN100 to AN102)	Offset error	-	±1.5	±5.0]
	Full-scale error	-	±2.5	±5.0]
	Absolute accuracy	-	±4.0	±8.0	
Channel-dedicated sample-and-hold circuits in use	Offset error	-	±1.5	±3.5	• PCLKC = 30 MHz
with continious sampling function enabled (AN000 to AN002)	Full-scale error	-	±1.5	±3.5	Sampling in 7 states
(144000 10744002)	Absolute accuracy	-	±3.0	±5.5]
Channel-dedicated sample-and-hold circuits in use	Offset error	-	±1.5	±3.5	
with continious sampling function enabled (AN100 to AN102)	Full-scale error	-	±1.5	±3.5]
(Absolute accuracy	-	±3.0	±5.5]

Note: When simultaneously using channel-dedicated sample-and-hold circuits in unit0 and unit1, setting the ADSHMSR.SHMD bit to 1 is recommended.

Table 2.43 A/D internal reference voltage characteristics

Parameter	Min	Тур	Max	Unit	Test conditions
A/D internal reference voltage	1.13	1.18	1.23	V	-
Sampling time	4.15	-	-	μs	-

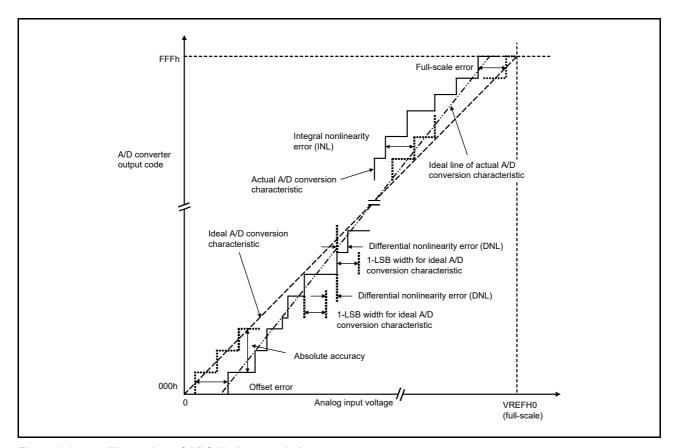


Figure 2.95 Illustration of ADC12 characteristic terms

Absolute accuracy

Absolute accuracy is the difference between output code based on the theoretical A/D conversion characteristics, and the actual A/D conversion result. When measuring absolute accuracy, the voltage at the midpoint of the width of the analog input voltage (1-LSB width), which can meet the expectation of outputting an equal code based on the theoretical A/D conversion characteristics, is used as an analog input voltage. For example, if 12-bit resolution is used and the reference voltage VREFH0 = 3.072 V, then 1-LSB width becomes 0.75 mV, and 0 mV, 0.75 mV, and 1.5 mV are used as the analog input voltages. If the analog input voltage is 6 mV, an absolute accuracy of ± 5 LSB means that the actual A/D conversion result is in the range of 0.03h to 0.00h, though an output code of 0.08h can be expected from the theoretical A/D conversion characteristics.

Integral nonlinearity error (INL)

Integral nonlinearity error is the maximum deviation between the ideal line when the measured offset and full-scale errors are zeroed, and the actual output code.

Differential nonlinearity error (DNL)

Differential nonlinearity error is the difference between the 1-LSB width based on the ideal A/D conversion characteristics and the width of the actual output code.



Offset error

Offset error is the difference between the transition point of the ideal first output code and the actual first output code.

Full-scale error

Full-scale error is the difference between the transition point of the ideal last output code and the actual last output code.

2.6 DAC12 Characteristics

Table 2.44 D/A conversion characteristics

Parameter	Min	Тур	Max	Unit	Test conditions
Resolution	-	-	12	Bits	-
Without output amplifier	•	•			•
Absolute accuracy	-	-	±24	LSB	Resistive load 2 MΩ
INL	-	±2.0	±8.0	LSB	Resistive load 2 MΩ
DNL	-	±1.0	±2.0	LSB	-
Output impedance	-	8.5	-	kΩ	-
Conversion time	-	-	3.0	μs	Resistive load 2 MΩ, Capacitive load 20 pF
Output voltage range	0	-	VREFH	V	-
With output amplifier	•		•		-
INL	-	±2.0	±4.0	LSB	-
DNL	-	±1.0	±2.0	LSB	-
Conversion time	-	-	4.0	μs	-
Resistive load	5	-	-	kΩ	-
Capacitive load	-	-	50	pF	-
Output voltage range	0.2	-	VREFH - 0.2	V	-

2.7 TSN Characteristics

Table 2.45 TSN characteristics

Parameter	Symbol	Min	Тур	Max	Unit	Test conditions
Relative accuracy	-	-	±1.0	-	°C	-
Temperature slope	-	-	4.0	-	mV/°C	-
Output voltage (at 25°C)	-	-	1.24	-	V	-
Temperature sensor start time	t _{START}	-	-	30	μs	-
Sampling time	-	4.15	-	-	μs	-

2.8 OSC Stop Detect Characteristics

Table 2.46 Oscillation stop detection circuit characteristics

Parameter	Symbol	Min	Тур	Max	Unit	Test conditions
Detection time	t _{dr}	-	-	1	ms	Figure 2.96

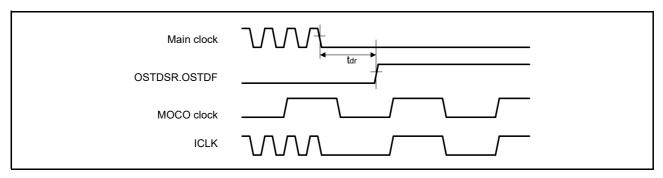


Figure 2.96 Oscillation stop detection timing

2.9 POR and LVD Characteristics

Table 2.47 Power-on reset circuit and voltage detection circuit characteristics

Parameter			Symbol	Min	Тур	Max	Unit	Test conditions
Voltage detection level	Power-on reset (POR)	DPSBYCR.DEEPCUT[1:0] = 00b or 01b	V _{POR}	2.5	2.6	2.7	٧	Figure 2.97
		DPSBYCR.DEEPCUT[1:0] = 11b		1.8	2.25	2.7		
	Voltage detection	circuit (LVD0)	V _{det0_1}	2.84	2.94	3.04		Figure 2.98
			V _{det0_2}	2.77	2.87	2.97		
			V _{det0_3}	2.70	2.80	2.90		
	Voltage detection circuit (LVD1)		V _{det1_1}	2.89	2.99	3.09		Figure 2.99
		V _{det1_2}	2.82	2.92	3.02			
			V _{det1_3}	2.75	2.85	2.95		
	Voltage detection	circuit (LVD2)	V _{det2_1}	2.89	2.99	3.09		Figure 2.100
			V _{det2_2}	2.82	2.92	3.02		
			V _{det2_3}	2.75	2.85	2.95		
Internal reset time	Power-on reset ti	me	t _{POR}	-	4.5	-	ms	Figure 2.97
	LVD0 reset time		t _{LVD0}	-	0.51	-		Figure 2.98
	LVD1 reset time		t _{LVD1}	-	0.38	-		Figure 2.99
	LVD2 reset time		t _{LVD2}	-	0.38	-		Figure 2.100
Minimum VCC dow	n time*1		t _{VOFF}	200	-	-	μs	Figure 2.97, Figure 2.98
Response delay			t _{det}	-	-	200	μs	Figure 2.97 to Figure 2.100
LVD operation stab	ilization time (after	LVD is enabled)	t _{d(E-A)}	-	-	10	μs	Figure 2.99,
Hysteresis width (L	VD1 and LVD2)		V_{LVH}	-	70	-	mV	Figure 2.100

Note 1. The minimum VCC down time indicates the time when VCC is below the minimum value of voltage detection levels V_{POR} , V_{det1} , and V_{det2} for POR and LVD.

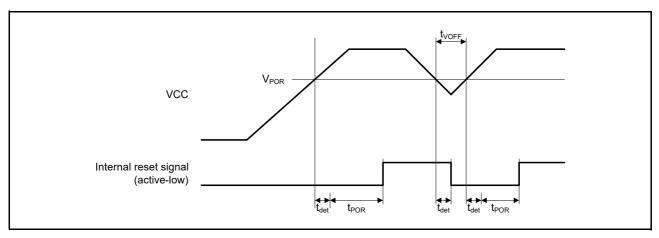


Figure 2.97 Power-on reset timing

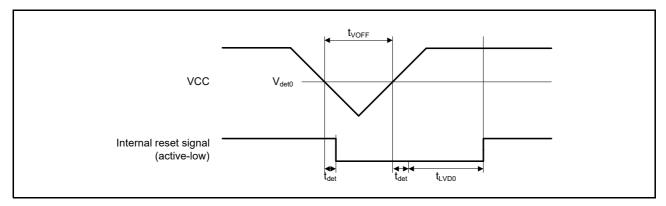


Figure 2.98 Voltage detection circuit timing (V_{det0})

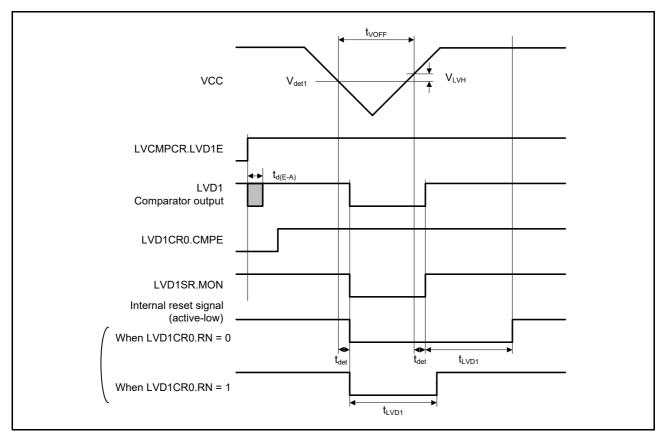


Figure 2.99 Voltage detection circuit timing (V_{det1})

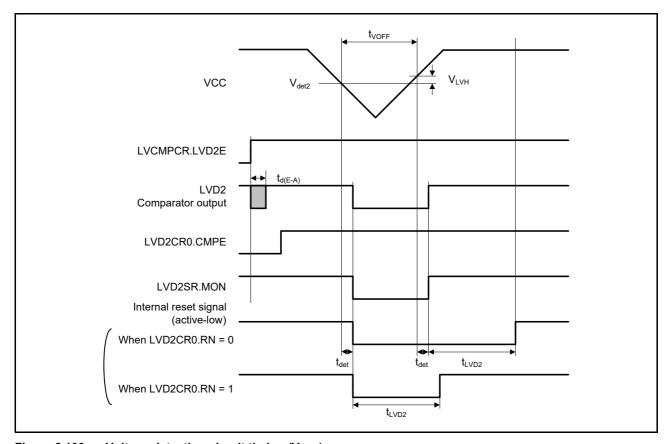


Figure 2.100 Voltage detection circuit timing (V_{det2})

2.10 **VBATT Characteristics**

Table 2.48Battery backup function characteristicsConditions: VCC = AVCC0 = VCC_USB = 2.7 to 3.6 V, 2.7 ≤ VREFH0/VREFH ≤ AVCC0, VBATT = 1.65 to 3.6 V*1

Parameter	Symbol	Min	Тур	Max	Unit	Test conditions
Voltage level for switching to battery backup	$V_{DETBATT}$	2.50	2.60	2.70	V	Figure 2.101
Lower-limit VBATT voltage for power supply switching caused by VCC voltage drop	V _{BATTSW}	2.70	-	-	V	
VCC-off period for starting power supply switching	t _{VOFFBATT}	200	-	-	μs	

Note: The VCC-off period for starting power supply switching indicates the period in which VCC is below the minimum value of the voltage level for switching to battery backup ($V_{\mbox{\scriptsize DETBATT}}$).

Low CL crystal cannot be used below VBATT = 1.8 V. Note 1.

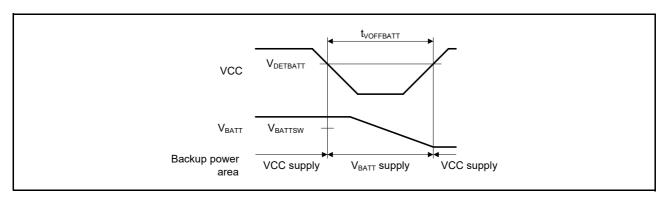


Figure 2.101 Battery backup function characteristics

2.11 **CTSU Characteristics**

Table 2.49 CTSU characteristics

Parameter	Symbol	Min	Тур	Max	Unit	Test conditions
External capacitance connected to TSCAP pin	C _{tscap}	9	10	11	nF	-
TS pin capacitive load	C _{base}	-	-	50	pF	-
Permissible output high current	Σ _{ΙοΗ}	-	-	-40	mA	When the mutual capacitance method is applied

2.12 **ACMPHS Characteristics**

Table 2.50 ACMPHS characteristics

Parameter	Symbol	Min	Тур	Max	Unit	Test conditions
Reference voltage range	VREF	0	-	AVCC0	V	-
Input voltage range	VI	0	-	AVCC0	V	-
Output delay*1	Td	-	50	100	ns	VI = VREF ± 100 mV
Internal reference voltage	Vref	1.13	1.18	1.23	V	-

Note 1. This value is the internal propagation delay.

2.13 PGA Characteristics

Table 2.51 PGA characteristics in single mode

Parameter	Symbol	Min	Тур	Max	Unit
PGAVSS input voltage range	PGAVSS	0	-	0	V
	AIN0 (G = 2.000)	0.050 × AVCC0	-	0.45 × AVCC0	V
	AIN1 (G = 2.500)	0.047 × AVCC0	-	0.360 × AVCC0	V
	AIN2 (G = 2.667)	0.046 × AVCC0	-	0.337 × AVCC0	V
	AIN3 (G = 2.857)	0.046 × AVCC0	-	0.32 × AVCC0	V
	AIN4 (G = 3.077)	0.045 × AVCC0	-	0.292 × AVCC0	V
	AIN5 (G = 3.333)	0.044 × AVCC0	-	0.265 × AVCC0	V
	AIN6 (G = 3.636)	0.042 × AVCC0	-	0.247 × AVCC0	V
	AIN7 (G = 4.000)	0.040 × AVCC0	-	0.212 × AVCC0	V
	AIN8 (G = 4.444)	0.036 × AVCC0	-	0.191 × AVCC0	V
	AIN9 (G = 5.000)	0.033 × AVCC0	-	0.17 × AVCC0	V
	AIN10 (G = 5.714)	0.031 × AVCC0	-	0.148 × AVCC0	V
	AIN11 (G = 6.667)	0.029 × AVCC0	-	0.127 × AVCC0	V
	AIN12 (G = 8.000)	0.027 × AVCC0	-	0.09 × AVCC0	V
	AIN13 (G = 10.000)	0.025 × AVCC0	-	0.08 × AVCC0	V
	AIN14 (G = 13.333)	0.023 × AVCC0	-	0.06 × AVCC0	V
Gain error	Gerr0 (G = 2.000)	-1.0	-	1.0	%
	Gerr1 (G = 2.500)	-1.0	-	1.0	%
	Gerr2 (G = 2.667)	-1.0	-	1.0	%
	Gerr3 (G = 2.857)	-1.0	-	1.0	%
	Gerr4 (G = 3.077)	-1.0	-	1.0	%
	Gerr5 (G = 3.333)	-1.5	-	1.5	%
	Gerr6 (G = 3.636)	-1.5	-	1.5	%
	Gerr7 (G = 4.000)	-1.5	-	1.5	%
	Gerr8 (G = 4.444)	-2.0	-	2.0	%
	Gerr9 (G = 5.000)	-2.0	-	2.0	%
	Gerr10 (G = 5.714)	-2.0	-	2.0	%
	Gerr11 (G = 6.667)	-2.0	-	2.0	%
	Gerr12 (G = 8.000)	-2.0	-	2.0	%
	Gerr13 (G = 10.000)	-2.0	-	2.0	%
	Gerr14 (G = 13.333)	-2.0	-	2.0	%
Offset error	Voff	-8	-	8	mV

Table 2.52 PGA characteristics in differential mode (1 of 2)

Parameter		Symbol	Min	Тур	Max	Unit
PGAVSS input voltag	ge range	PGAVSS	-0.5	-	0.3	V
Differential input	G = 1.500	AIN-PGAVSS	-0.5	-	0.5	V
voltage range	G = 2.333]	-0.4	-	0.4	V
	G = 4.000]	-0.2	-	0.2	V
	G = 5.667]	-0.15	-	0.15	V

Table 2.52 PGA characteristics in differential mode (2 of 2)

Parameter		Symbol	Min	Тур	Max	Unit
Gain error	G = 1.500	Gerr	-1.0	-	1.0	%
	G = 2.333		-1.0	-	1.0	
	G = 4.000		-1.0	-	1.0	
	G = 5.667		-1.0	-	1.0	

2.14 Flash Memory Characteristics

2.14.1 Code Flash Memory Characteristics

Table 2.53 Code flash memory characteristics Conditions: Program or erase: FCLK = 4 to 60 MHz

Read: FCLK ≤ 60 MHz

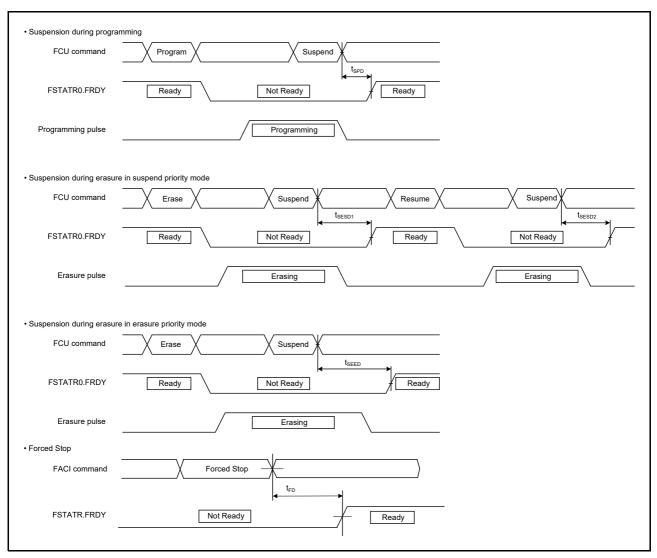
			F	CLK = 4 N	ИHz	20 MHz	z ≤ FCLK	≤ 60 MHz		Test
Parameter		Symbol	Min	Тур	Max	Min	Тур	Max	Unit	conditions
Programming time	128-byte	t _{P128}	-	0.75	13.2	-	0.34	6.0	ms	
N _{PEC} ≤ 100 times	8-KB	t _{P8K}	-	49	176	-	22	80	ms	
	32-KB	t _{P32K}	-	194	704	-	88	320	ms	
Programming time	128-byte	t _{P128}	-	0.91	15.8	-	0.41	7.2	ms	
N _{PEC} > 100 times	8-KB	t _{P8K}	-	60	212	-	27	96	ms	
	32-KB	t _{P32K}	-	234	848	-	106	384	ms	
Erasure time	8-KB	t _{E8K}	-	78	216	-	43	120	ms	
N _{PEC} ≤ 100 times	32-KB	t _{E32K}	-	283	864	-	157	480	ms	
Erasure time	8-KB	t _{E8K}	-	94	260	-	52	144	ms	
N _{PEC} > 100 times	32-KB	t _{E32K}	-	341	1040	-	189	576	ms	
Reprogramming/eras	ure cycle*Note:	N _{PEC}	10000*1	-	-	10000*1	-	-	Times	
Suspend delay during	g programming	t _{SPD}	-	-	264	-	-	120	μs	
First suspend delay d suspend priority mod		t _{SESD1}	-	-	216	-	-	120	μs	
Second suspend dela erasure in suspend p	, ,	t _{SESD2}	-	-	1.7	-	-	1.7	ms	
Suspend delay during erasure priority mode	,	t _{SEED}	-	-	1.7	-	-	1.7	ms	
Forced stop comman	ıd	t _{FD}	-	-	32	-	-	20	μs	
Data hold time*2		t _{DRP}	10*2, *3	-	-	10*2, *3	-	-	Years	
			30*2, *3	-	-	30*2, *3	-	-		Ta = +85°C

The reprogram/erase cycle is the number of erasures for each block. When the reprogram/erase cycle is n times (n = 10,000), Note: erasing can be performed n times for each block. For example, when 128-byte programming is performed 64 times for different addresses in 8-KB blocks, and then the entire block is erased, the reprogram/erase cycle is counted as one. However, programming the same address several times as one erasure is not enabled. (Overwriting is prohibited.)

Note 1. This is the minimum number of times to guarantee all the characteristics after reprogramming. The guaranteed range is from 1 to the minimum value.

Note 2. This indicates the minimum value of the characteristic when reprogramming is performed within the specified range.

Note 3. This result is obtained from reliability testing.



Suspension and forced stop timing for flash memory programming and erasure Figure 2.102

2.14.2 **Data Flash Memory Characteristics**

Table 2.54 Data flash memory characteristics (1 of 2) Conditions: Program or erase: FCLK = 4 to 60 MHz

Read: FCLK ≤ 60 MHz

			FC	FCLK = 4 MHz 20 MHz			≤ FCLK	≤ 60 MHz		Test
Parameter		Symbol	Min	Тур	Max	Min	Тур	Max	Unit	conditions
Programming time	4-byte	t _{DP4}	-	0.36	3.8	-	0.16	1.7	ms	
	8-byte	t _{DP8}	-	0.38	4.0	-	0.17	1.8		
	16-byte	t _{DP16}	-	0.42	4.5	-	0.19	2.0		
Erasure time	64-byte	t _{DE64}	-	3.1	18	-	1.7	10	ms	
	128-byte	t _{DE128}	-	4.7	27	-	2.6	15		
	256-byte	t _{DE256}	-	8.9	50	-	4.9	28		
Blank check time	4-byte	t _{DBC4}	-	-	84	-	-	30	μs	
Reprogramming/erasu	ure cycle*1	N _{DPEC}	125000 *2	-	-	125000 *2	-	-	-	

Table 2.54 Data flash memory characteristics (2 of 2) Conditions: Program or erase: FCLK = 4 to 60 MHz

Read: FCLK ≤ 60 MHz

			F	CLK = 4	MHz	20 MHz	≤ FCLK	≤ 60 MHz		Test
Parameter		Symbol	Min	Тур	Max	Min	Тур	Max	Unit	conditions
Suspend delay during	4-byte	t _{DSPD}	-	-	264	-	-	120	μs	
programming	8-byte		-	-	264	-	-	120		
	16-byte		-	-	264	-	-	120		
First suspend delay	64-byte	t _{DSESD1}	-	-	216	-	-	120	μs	
during erasure in suspend priority mode	128-byte		-	-	216	-	-	120		
Suspend priority mode	256-byte		-	-	216	-	-	120		
Second suspend delay	64-byte	t _{DSESD2}	-	-	300	-	-	300	μs	
during erasure in suspend priority mode	128-byte		-	-	390	-	-	390		
Suspend priority mode	256-byte		-	-	570	-	-	570		
Suspend delay during	64-byte	t _{DSEED}	-	-	300	-	-	300	μs	
erasing in erasure priority mode	128-byte		-	-	390	-	-	390		
phonty mode	256-byte		-	-	570	-	-	570		
Forced stop command	1	t _{FD}	-	-	32	-	-	20	μs	
Data hold time*3		t _{DRP}	10*3,*4	-	-	10*3,*4	-	-	Year	
			30*3,*4	-	-	30*3,*4	-	-		Ta = +85°C

- Note 1. The reprogram/erase cycle is the number of erasures for each block. When the reprogram/erase cycle is n times (n = 125,000), erasing can be performed n times for each block. For example, when 4-byte programming is performed 16 times for different addresses in 64-byte blocks, and then the entire block is erased, the reprogram/erase cycle is counted as one. However, programming the same address several times as one erasure is not enabled. (Overwriting is prohibited.)
- This is the minimum number of times to guarantee all the characteristics after reprogramming. The guaranteed range is from 1 Note 2. to the minimum value.
- Note 3. This indicates the minimum value of the characteristic when reprogramming is performed within the specified range.
- This result is obtained from reliability testing. Note 4.

2.15 **Boundary Scan**

Table 2.55 Boundary scan characteristics

Parameter	Symbol	Min	Тур	Max	Unit	Test conditions
TCK clock cycle time	t _{TCKcyc}	100	-	-	ns	Figure 2.103
TCK clock high pulse width	t _{TCKH}	45	-	-	ns	
TCK clock low pulse width	t _{TCKL}	45	-	-	ns	
TCK clock rise time	t _{TCKr}	-	-	5	ns	
TCK clock fall time	t _{TCKf}	-	-	5	ns	
TMS setup time	t _{TMSS}	20	-	-	ns	Figure 2.104
TMS hold time	t _{TMSH}	20	-	-	ns	
TDI setup time	t _{TDIS}	20	-	-	ns	
TDI hold time	t _{TDIH}	20	-	-	ns	
TDO data delay	t _{TDOD}	-	-	40	ns	
Boundary scan circuit startup time*1	T _{BSSTUP}	t _{RESWP}	-	-	-	Figure 2.105

Note 1. Boundary scan does not function until the power-on reset becomes negative.

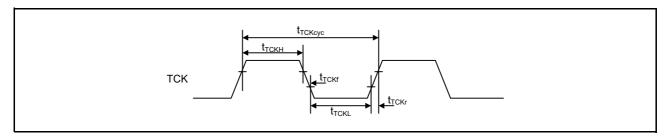


Figure 2.103 Boundary scan TCK timing

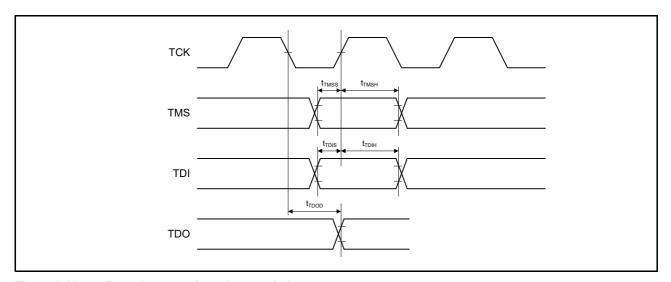


Figure 2.104 Boundary scan input/output timing

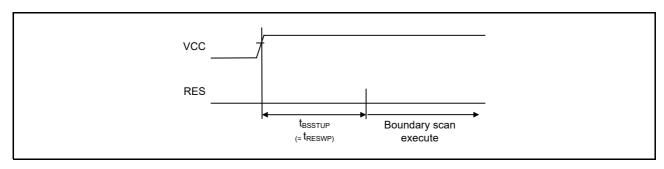


Figure 2.105 Boundary scan circuit startup timing

2.16 Joint Test Action Group (JTAG)

Table 2.56 JTAG

Parameter	Symbol	Min	Тур	Max	Unit	Test conditions
TCK clock cycle time	t _{TCKcyc}	40	-	-	ns	Figure 2.103
TCK clock high pulse width	t _{TCKH}	15	-	-	ns	
TCK clock low pulse width	t _{TCKL}	15	-	-	ns	
TCK clock rise time	t _{TCKr}	-	-	5	ns	
TCK clock fall time	t _{TCKf}	-	-	5	ns	

Table 2.56 JTAG

Parameter	Symbol	Min	Тур	Max	Unit	Test conditions
TMS setup time	t _{TMSS}	8	-	-	ns	Figure 2.104
TMS hold time	t _{TMSH}	8	-	-	ns	
TDI setup time	t _{TDIS}	8	-	-	ns	
TDI hold time	t _{TDIH}	8	-	-	ns	
TDO data delay time	t _{TDOD}	-	-	20	ns	

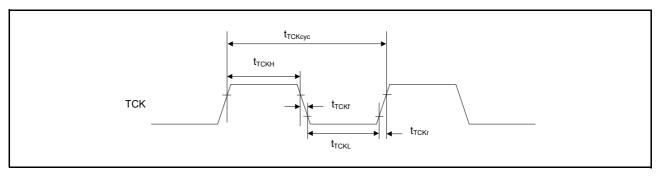


Figure 2.106 JTAG TCK timing

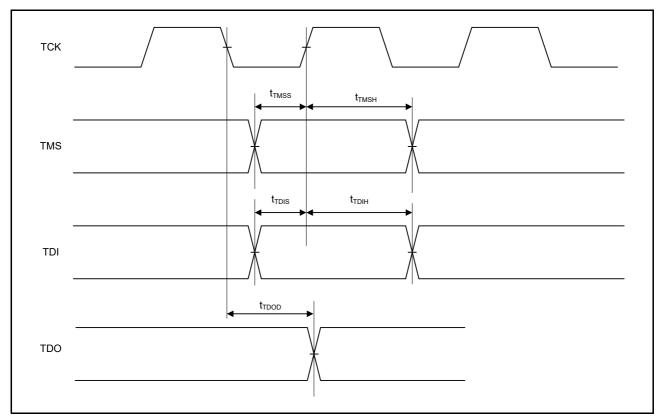


Figure 2.107 JTAG input/output timing

2.17 Serial Wire Debug (SWD)

Table 2.57 SWD

Parameter	Symbol	Min	Тур	Max	Unit	Test conditions
SWCLK clock cycle time	t _{SWCKcyc}	40	-	-	ns	Figure 2.108
SWCLK clock high pulse width	tswckh	15	-	-	ns	
SWCLK clock low pulse width	tswckl	15	-	-	ns	
SWCLK clock rise time	t _{SWCKr}	-	-	5	ns	
SWCLK clock fall time	t _{SWCKf}	-	-	5	ns	
SWDIO setup time	t _{SWDS}	8	-	-	ns	Figure 2.109
SWDIO hold time	t _{SWDH}	8	-	-	ns	
SWDIO data delay time t _{SWDD}		2	-	28	ns	

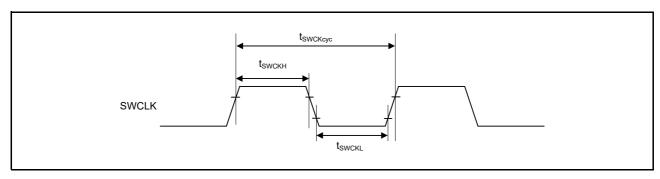


Figure 2.108 SWD SWCLK timing

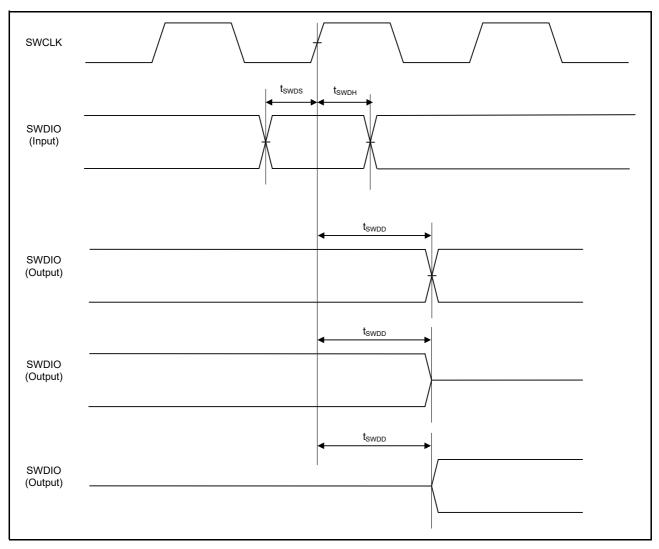


Figure 2.109 SWD input/output timing

2.18 Embedded Trace Macro Interface (ETM)

Table 2.58 ETMConditions: High drive output is selected in the port drive capability bit in the PmnPFS register.

Parameter	Symbol	Min	Тур	Max	Unit	Test conditions
TCLK clock cycle time	t _{TCLKcyc}	33.3	-	-	ns	Figure 2.110
TCLK clock high pulse width	t _{TCLKH}	13.6	-	-	ns	
TCLK clock low pulse width	t _{TCLKL}	13.6	-	-	ns	
TCLK clock rise time	t _{TCLKr}	-	-	3	ns	
TCLK clock fall time	t _{TCLKf}	-	-	3	ns	
TDATA[3:0] output setup time	t _{TRDS}	3.5	-	-	ns	Figure 2.111
TDATA[3:0] output hold time	t _{TRDH}	2.5	-	-	ns	

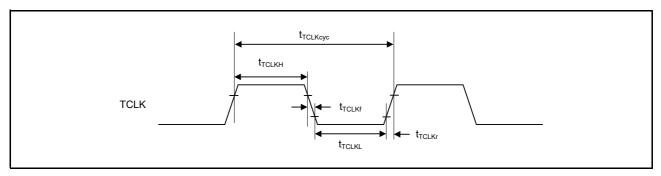


Figure 2.110 ETM TCLK timing

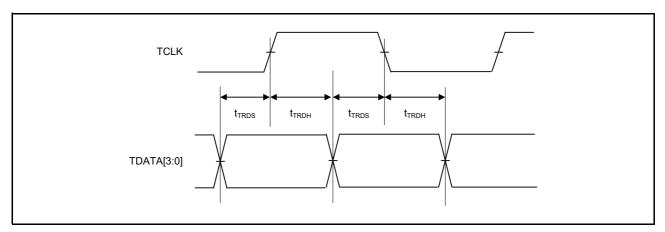


Figure 2.111 ETM output timing

Appendix 1.Package Dimensions

For information on the latest version of the package dimensions or mountings, go to "Packages" on the Renesas Electronics Corporation website.

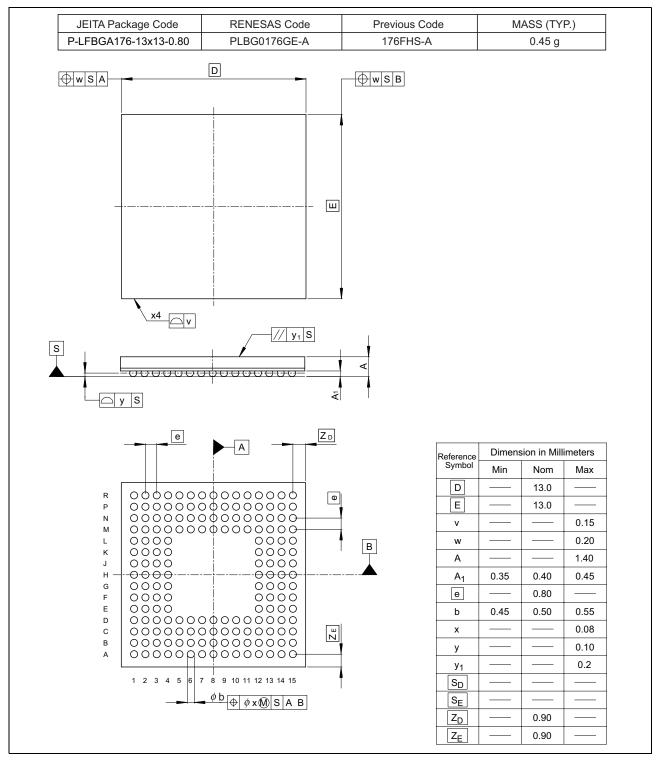


Figure 1.1 176-pin BGA

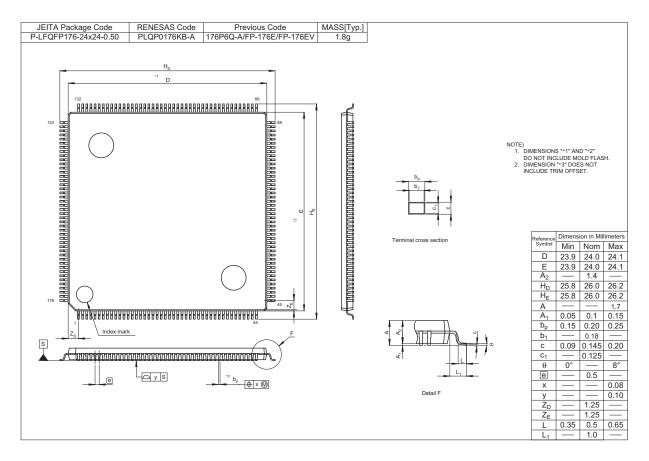


Figure 1.2 176-pin LQFP

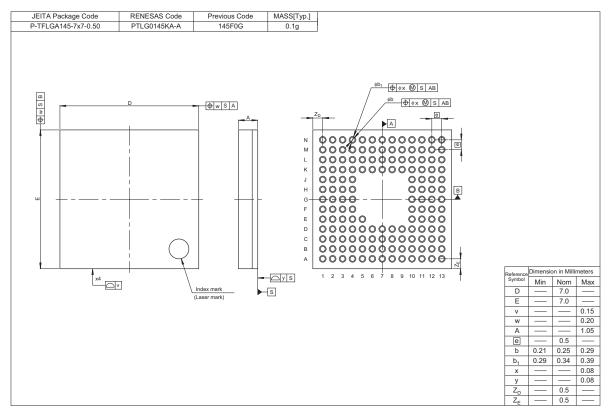


Figure 1.3 145-pin LGA

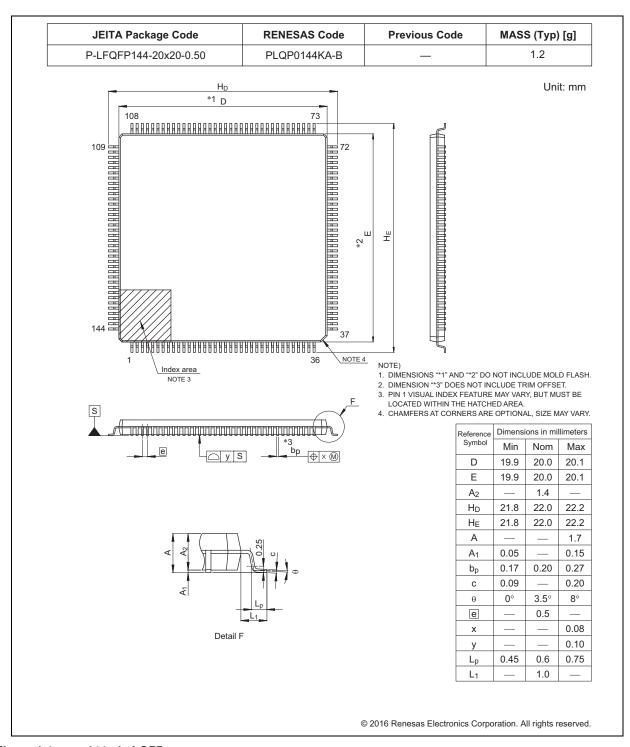


Figure 1.4 144-pin LQFP

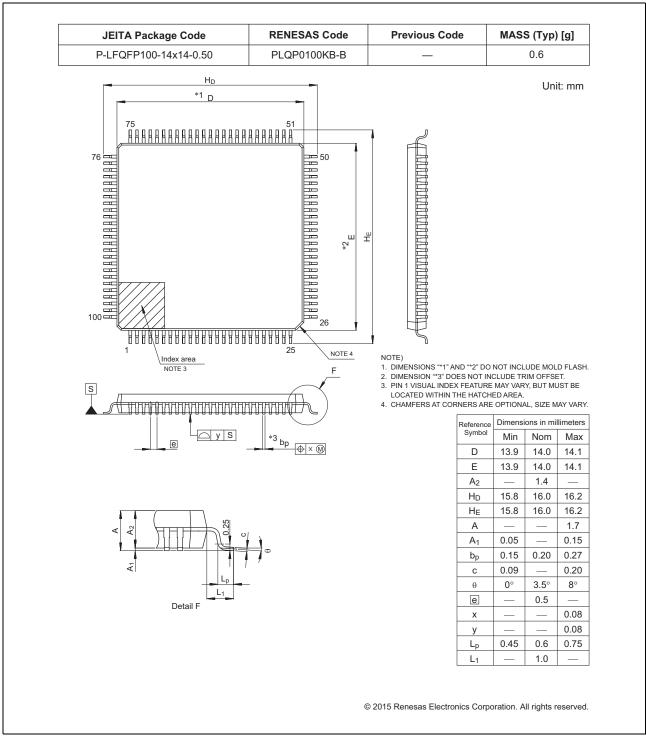


Figure 1.5 100-pin LQFP

RA6M3 Group Revision History

Revision History	RA6M3 Group Datasheet
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Rev.	Date	Chapter	Summary
1.00	Oct 8, 2019	-	First Edition issued
1.10	Dec 25, 2020	-	Second Edition issued
1.20	Feb 3, 2023	_	Third Edition issued

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1. Precaution against Electrostatic Discharge (ESD)

A strong electrical field, when exposed to a CMOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop the generation of static electricity as much as possible, and quickly dissipate it when it occurs. Environmental control must be adequate. When it is dry, a humidifier should be used. This is recommended to avoid using insulators that can easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors must be grounded. The operator must also be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions must be taken for printed circuit boards with mounted semiconductor devices.

2. Processing at power-on

The state of the product is undefined at the time when power is supplied. The states of internal circuits in the LSI are indeterminate and the states of register settings and pins are undefined at the time when power is supplied. In a finished product where the reset signal is applied to the external reset pin, the states of pins are not guaranteed from the time when power is supplied until the reset process is completed. In a similar way, the states of pins in a product that is reset by an on-chip power-on reset function are not guaranteed from the time when power is supplied until the power reaches the level at which resetting is specified.

3. Input of signal during power-off state

Do not input signals or an I/O pull-up power supply while the device is powered off. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Follow the guideline for input signal during power-off state as described in your product documentation.

4. Handling of unused pins

Handle unused pins in accordance with the directions given under handling of unused pins in the manual. The input pins of CMOS products are generally in the high-impedance state. In operation with an unused pin in the open-circuit state, extra electromagnetic noise is induced in the vicinity of the LSI, an associated shoot-through current flows internally, and malfunctions occur due to the false recognition of the pin state as an input signal become possible.

5. Clock signals

After applying a reset, only release the reset line after the operating clock signal becomes stable. When switching the clock signal during program execution, wait until the target clock signal is stabilized. When the clock signal is generated with an external resonator or from an external oscillator during a reset, ensure that the reset line is only released after full stabilization of the clock signal. Additionally, when switching to a clock signal produced with an external resonator or by an external oscillator while program execution is in progress, wait until the target clock signal is stable.

6. Voltage application waveform at input pin

Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between V_{IL} (Max.) and V_{IH} (Min.) due to noise, for example, the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between V_{IL} (Max.) and V_{IH} (Min.).

7. Prohibition of access to reserved addresses

Access to reserved addresses is prohibited. The reserved addresses are provided for possible future expansion of functions. Do not access these addresses as the correct operation of the LSI is not guaranteed.

8. Differences between products

Before changing from one product to another, for example to a product with a different part number, confirm that the change will not lead to problems. The characteristics of a microprocessing unit or microcontroller unit products in the same group but having a different part number might differ in terms of internal memory capacity, layout pattern, and other factors, which can affect the ranges of electrical characteristics, such as characteristic values, operating margins, immunity to noise, and amount of radiated noise. When changing to a product with a different part number, implement a system-evaluation test for the given product.

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